

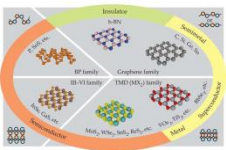
Optical spectroscopy as a probe of charge and energy transfer in two-dimensional materials

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`berciaud@unistra.fr`

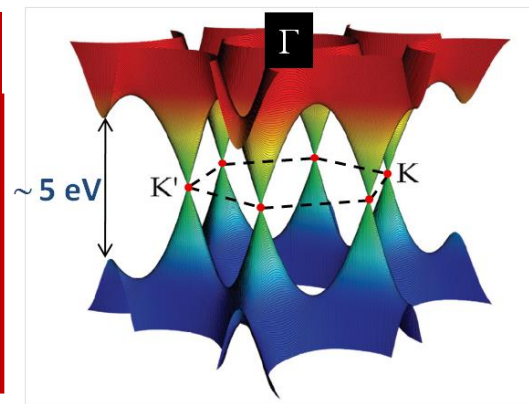
New Frontiers in 2D materials Winterschool/Workshop
Villard de Lans, January 16, 2017



Graphene and 2D materials at IPCMS



- *Cross-disciplinary work on graphene and 2DM since 2012*
- 6 Permanent staff, 5 Postdocs + 9 PhD (currently, 1 + 4)
- Nanofabrication facility (StNano, 180 m²)
- Optical spectroscopy, optoelectronics, optomechanics, electron transport, spintronics, chemtronics, straintronics...



Fundamental properties

- **Suspended graphene**

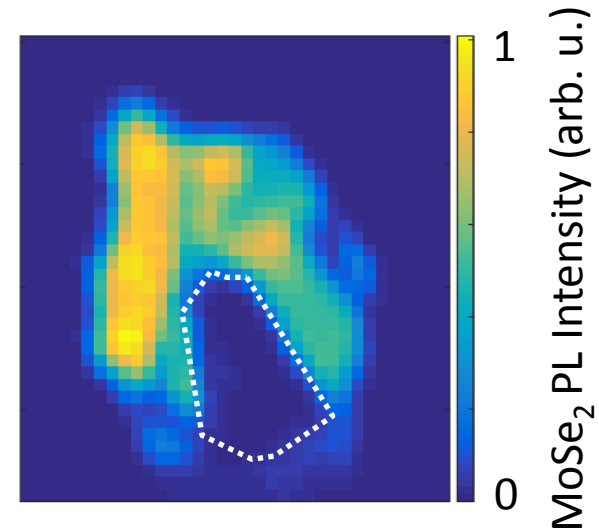
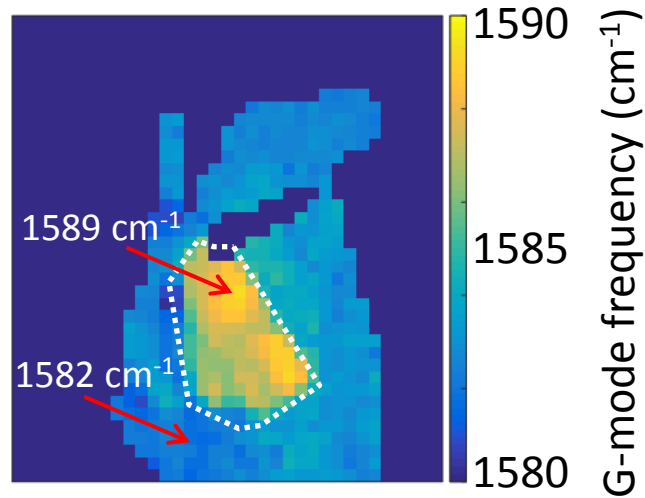
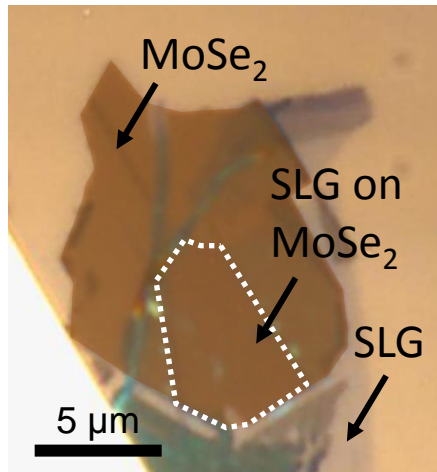
- **Transition metal dichalcogenides**

Devices, Hybrid Systems, Heterostructures

- Field-effect transistors, memories, sensors
- 2DM-nanoemitter hybrids
- van der Waals heterostructures
- Gr-based tunnel junctions

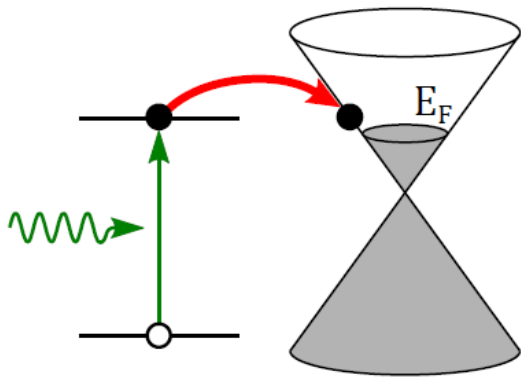
Advanced Mat. DOI: 10.1002/adma.201604837

Let us try to understand this...

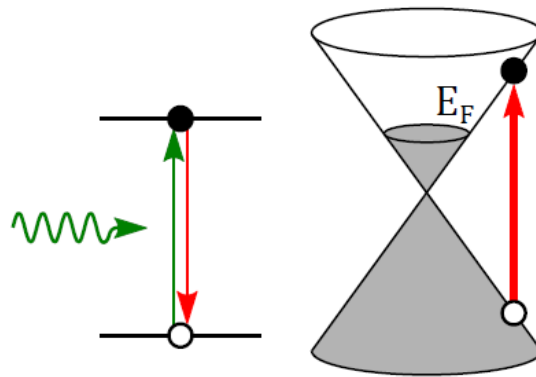


Data : G. Froehlicher, E. Lorchat, SB (in preparation)

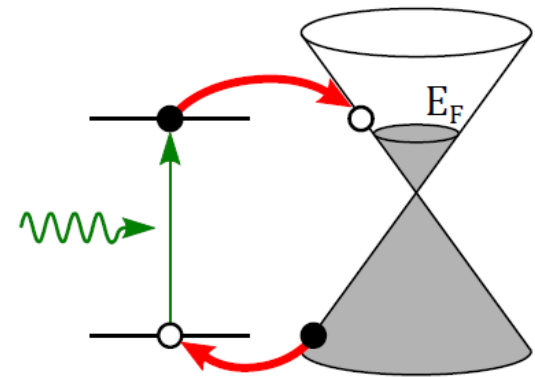
(a) Charge transfer



(b) Foerster energy transfer

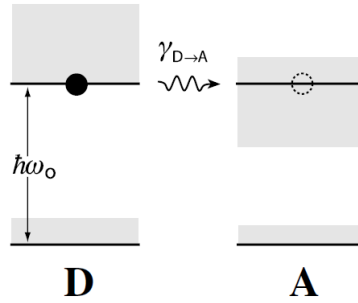
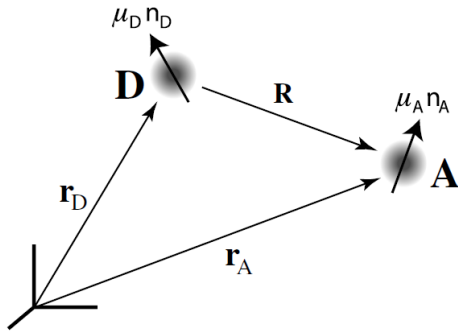


(c) Dexter energy transfer



...and discuss what this can be useful for.

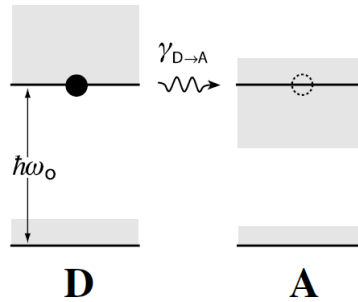
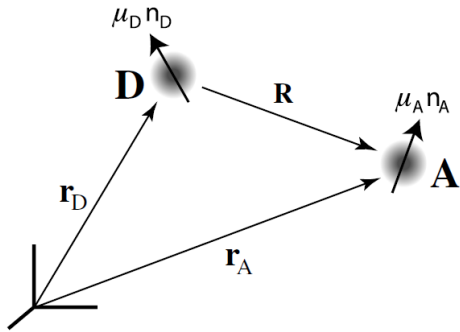
Förster energy transfer: near field dipole-dipole interaction



$$\frac{\gamma_{D \rightarrow A}}{\gamma_0} = \frac{P_{D \rightarrow A}}{P_0}$$

$$\mathbf{E}_D = \frac{1}{4\pi\epsilon_0} \left[k^2 (\mathbf{r} \wedge \boldsymbol{\mu}_D) \wedge \boldsymbol{\mu}_D \frac{e^{ikr}}{r^2} + \left(\frac{3\mathbf{r}(\mathbf{r} \cdot \boldsymbol{\mu}_D)}{r^2} - \boldsymbol{\mu}_D \right) \left(\frac{1}{r^3} - \frac{ik}{r^2} \right) e^{ikr} \right]$$

Förster energy transfer: near field dipole-dipole interaction



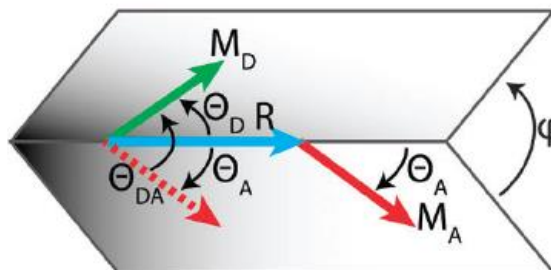
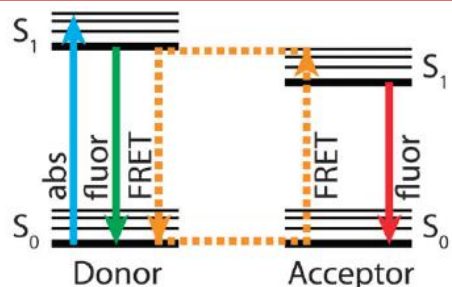
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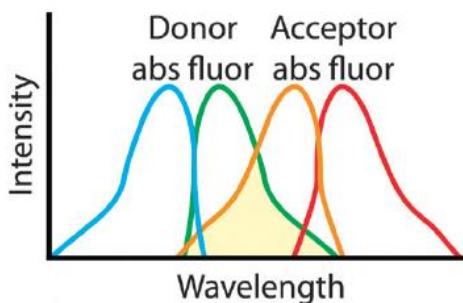
$$P_{D \rightarrow A} = -\frac{1}{2} \int_{V_A} \text{Re}\{\mathbf{j}_A^* \cdot \mathbf{E}_D\} dV \approx \frac{\omega_0}{2} \text{Im}\{\alpha_A\} |\mathbf{n}_A \cdot \mathbf{E}_D(\mathbf{r}_A)|^2$$

$$\frac{\gamma_{D \rightarrow A}}{\gamma_0} = \left[\frac{R_0}{R} \right]^6 \quad R_0^6 = \frac{9c^4 \kappa^2}{8\pi} \int_0^\infty \frac{f_D(\omega) \sigma_A(\omega)}{n^4(\omega) \omega^4} d\omega$$

FRET: Distance sensing at the single molecule level

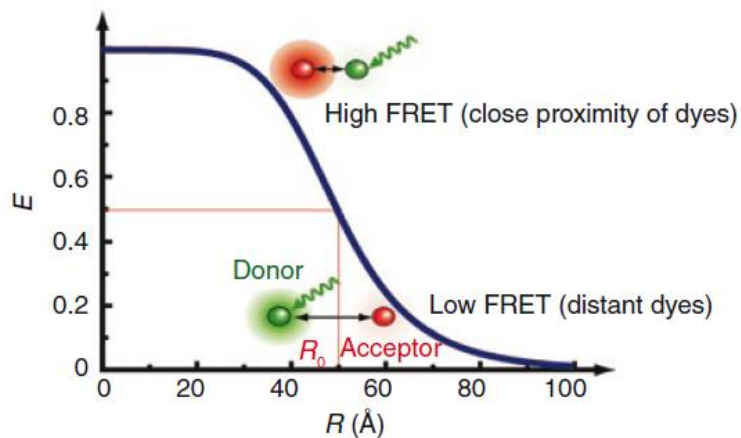
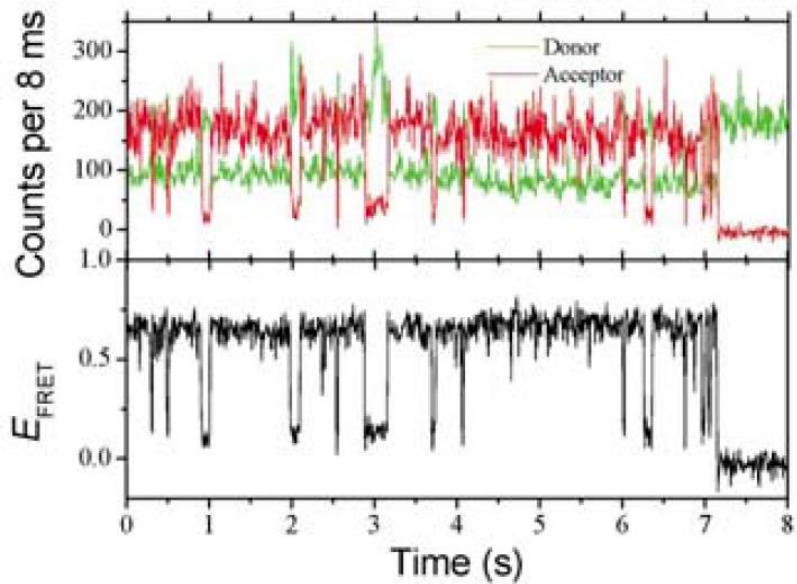


$$R_0^6 = \frac{9c^4 \kappa^2}{8\pi} \int_0^\infty \frac{f_D(\omega) \sigma_A(\omega)}{n^4(\omega) \omega^4} d\omega$$



$$\eta = \frac{\gamma_0}{\gamma_0 + \gamma_{D \rightarrow A}} = \left[1 + \left(\frac{R_0}{R} \right)^6 \right]^{-1}$$

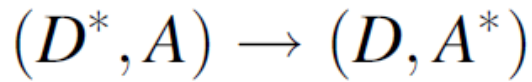
Chem.Soc.Rev., **43**, 1144 (2014)



Nature Methods, **5**, 507 (2008)

Nature structural biology **10**, 93 (2003)

Förster and Dexter energy transfer



$$U = \langle \Psi_i | \hat{V} | \Psi_f \rangle$$

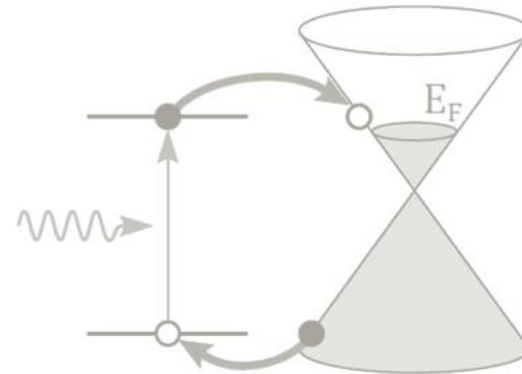
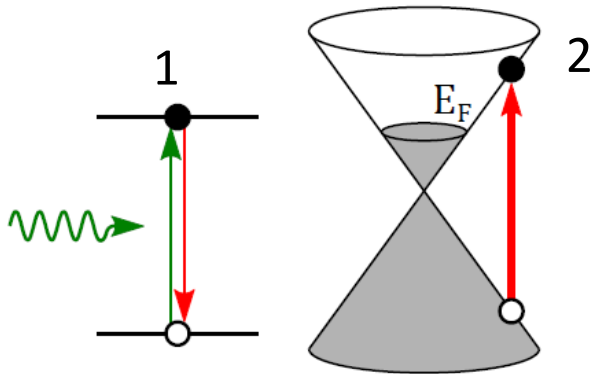
$$U = \langle \Psi_{D^*}(1) \Psi_A(2) | \hat{V} | \Psi_D(1) \Psi_{A^*}(2) \rangle - \langle \Psi_{D^*}(1) \Psi_A(2) | \hat{V} | \Psi_D(2) \Psi_{A^*}(1) \rangle$$

Coulomb (FRET) term

- ✓ 'Long' range (power law)
- ✓ Implies spectral overlap

Exchange (Dexter) term

- ✓ Short range (exponential, idem CT)
- ✓ Implies overlap of molecular orbitals



Photoinduced Charge Transfer and Energy Transfer

Key near-field phenomena in nano-optoelectronic devices

Affect:

- (photo)excited states dynamics
- Fermi energies/doping levels

Sensitive to:

- donor-acceptor distance
- dimensionality
- band alignment
- excitonic effects
- Fermi energies/doping levels

How to probe charge and energy transfer ?

Experimental techniques:

- Raman spectroscopy (CT)
- Photoluminescence spectroscopy (CT & ET)
- Non-linear (pump-probe) spectroscopy (CT & ET)

Devices:

- Nanofabrication
- Custom devices
- Electrical control

Today's menu

I. Introduction

- Two-dimensional materials (2DM)
- Semiconductor nanostructures
- Hybrid and van der Waals heterostructures
- Optoelectronic devices
- Optical spectroscopies

II. Near-field coupling in hybrid heterostructures

- Energy transfer: distance scaling, dimensionality, screening
- Electrical control of near-field coupling

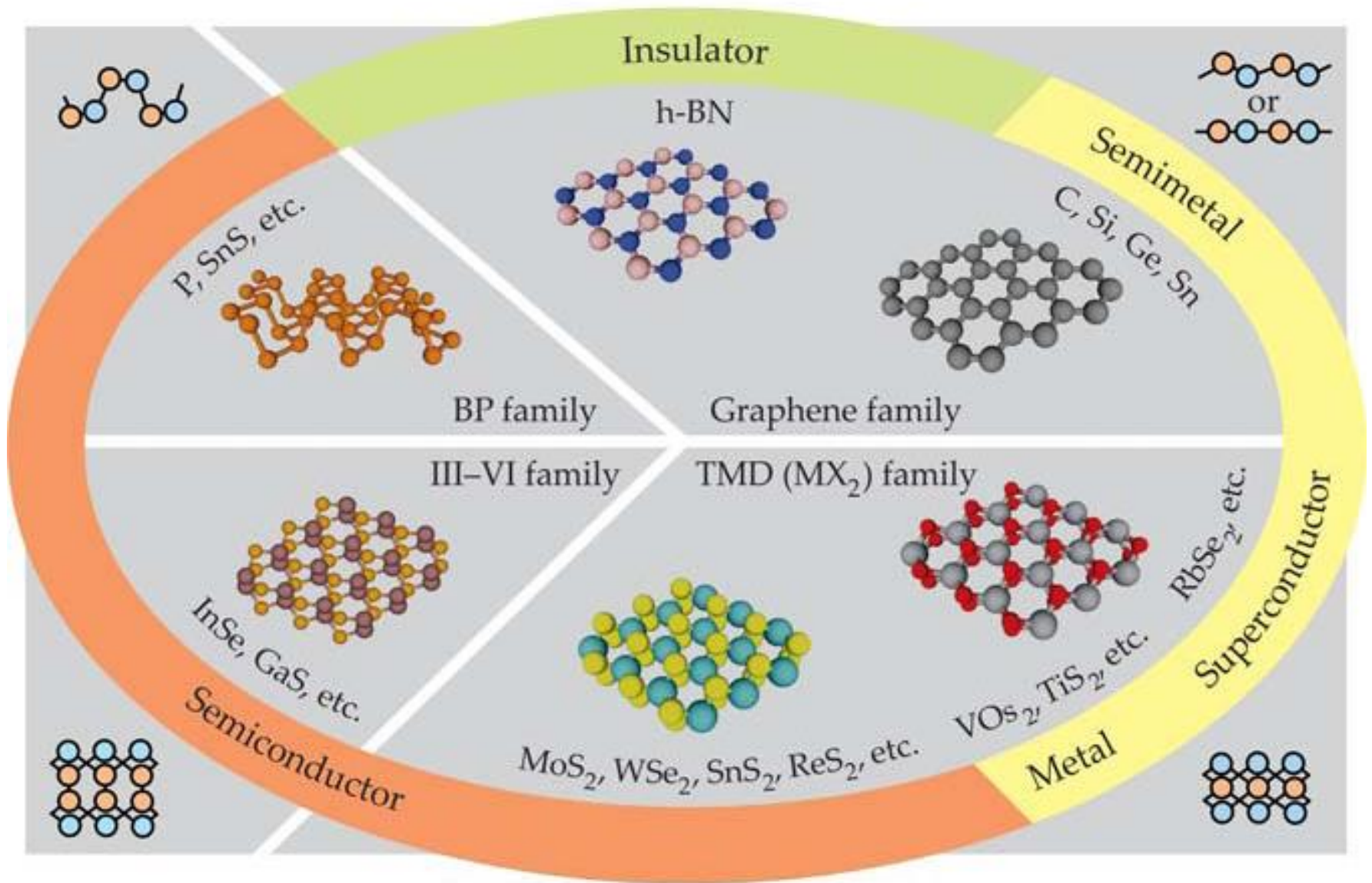
III. Near-field coupling in van der Waals Heterostructures

- TMD-TMD heterostructures
- Charge vs energy transfer in graphene-TMD heterostructures

IV. Conclusion and outlook

- Novel optoelectronic devices
- Towards opto-electro-mechanics

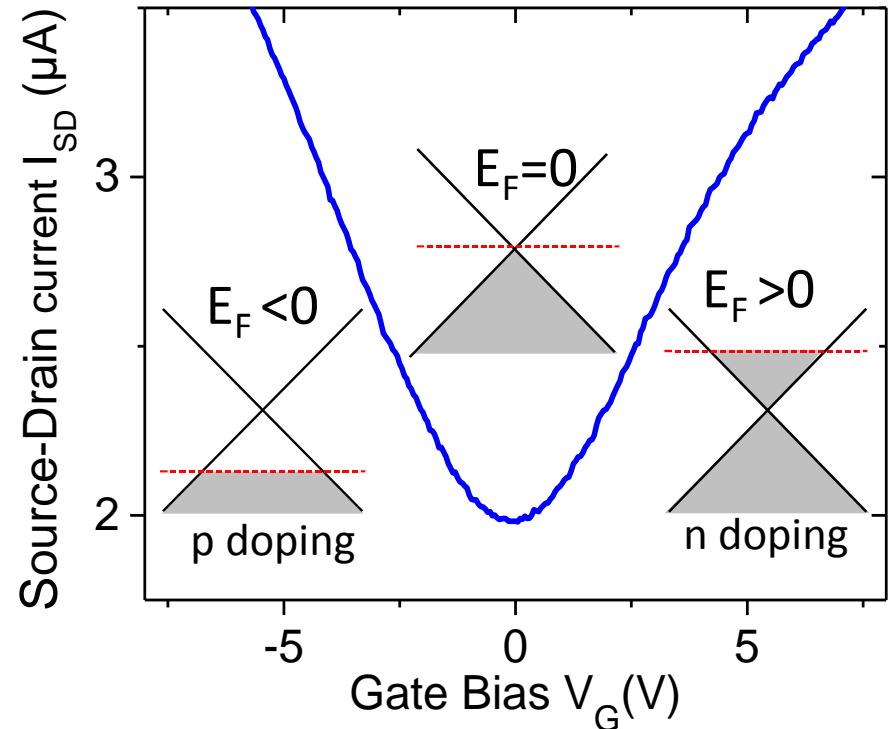
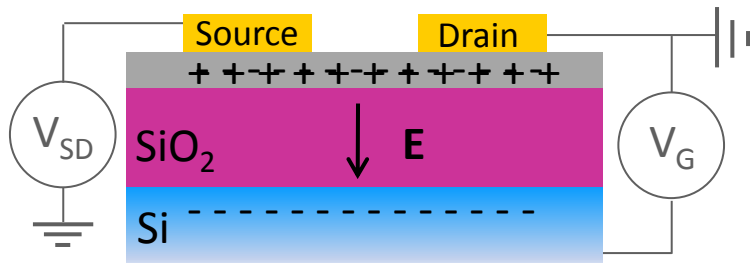
Introducing 2D materials



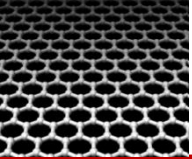
Graphene: a unique, tunable 2D electron gas

- ✓ quantum electron transport (QHE)
- ✓ electron-phonon coupling
- ✓ electromechanics
- ✓ optoelectronics

Electric field effect



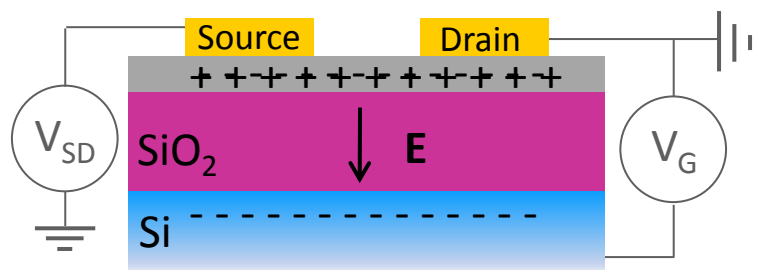
1st observation: Novoselov *et al.*, Science (2004)



Graphene: a unique, tunable 2D electron gas

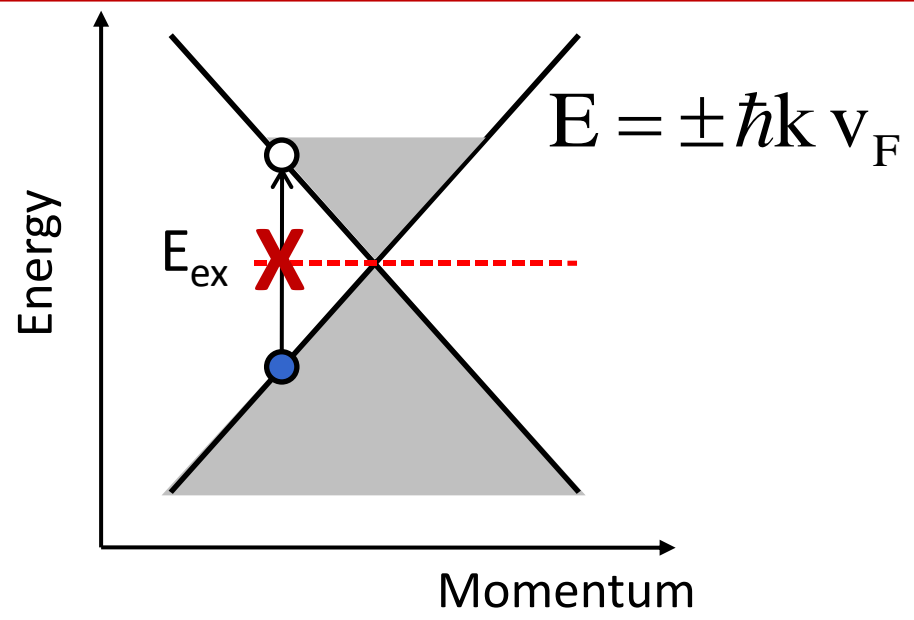
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Electric field effect

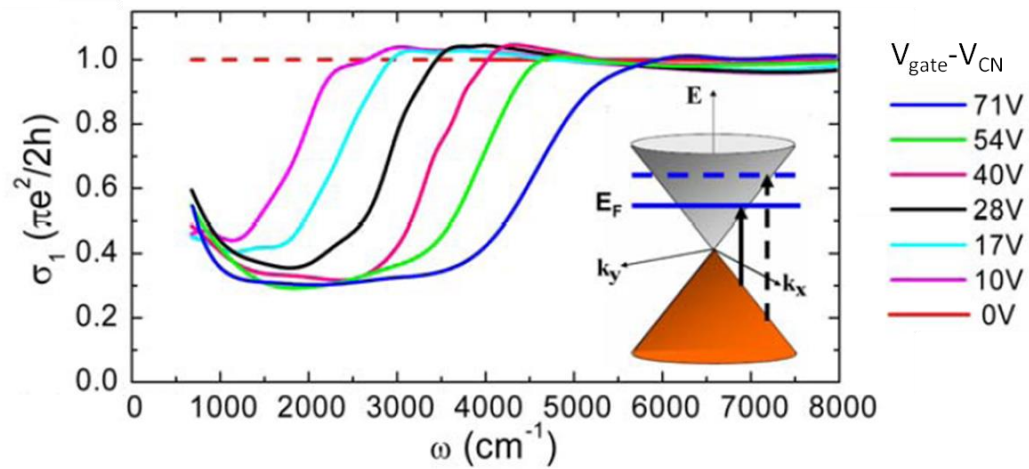


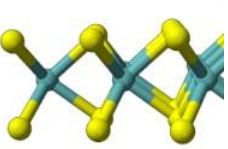
1st observation: Novoselov *et al.*, Science (2004)

Z.Q. Li *et al.* Nature Physics (2008)
 F. Wang *et al.* Science (2008)



→ Absorption edge at $E \sim 2E_F$





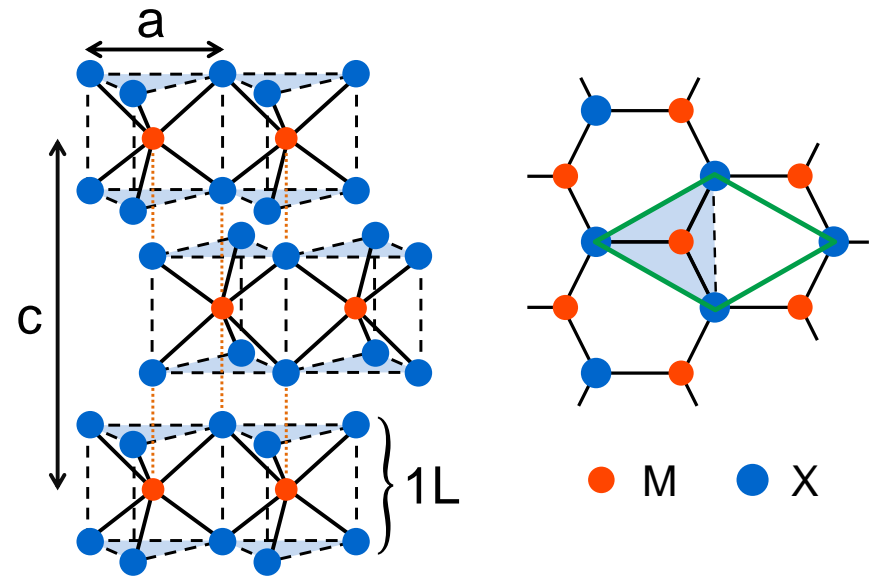
Introducing Transition Metal Dichalcogenides

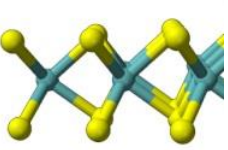
- MX_2 with $\text{M} = \text{Mo}, \text{W}, \text{Re}, \dots$
 $\text{X} = \text{S}, \text{Se}, \text{Te}$
- Well documented in the bulk
Wilson and Yoffe *Adv. Phys.* 1969
- In this talk:
Semiconducting MX_2 only

| | | | | | | | | | | | | | | | | | | X | | | | | | | | | | | | | | | | | | | | | | | |
|----|----|-------|----|----|----|----|----|----|----|----|----|-----|----|-----|----|-----|-----|---|---|---|---|---|----|----|--|--|--|--|--|--|--|--|--|--|--|--|--|--|--|--|--|
| | | | | | | | | | | | | | | | | | | M | | | | | | | | | | | | | | | | | | | | | | | |
| H | | | | | | | | | | | | | | | | | | | | | | | | He | | | | | | | | | | | | | | | | | |
| Li | Be | | | | | | | | | | | | | | | | | B | C | N | O | F | Ne | | | | | | | | | | | | | | | | | | |
| Na | Mg | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 | 12 | Al | Si | P | S | Cl | Ar | | | | | | | | | | | | | | | | | | | | | | | | |
| K | Ca | Sc | Ti | V | Cr | Mn | Fe | Co | Ni | Cu | Zn | Ga | Ge | As | Se | Br | Kr | | | | | | | | | | | | | | | | | | | | | | | | |
| Rb | Sr | Y | Zr | Nb | Mo | Tc | Ru | Rh | Pd | Ag | Cd | In | Sn | Sb | Te | I | Xe | | | | | | | | | | | | | | | | | | | | | | | | |
| Cs | Ba | La-Lu | Hf | Ta | W | Re | Os | Ir | Pt | Au | Hg | Tl | Pb | Bi | Po | At | Rn | | | | | | | | | | | | | | | | | | | | | | | | |
| Fr | Ra | Ac-Lr | Rf | Db | Sg | Bh | Hs | Mt | Ds | Rg | Cn | Uut | Fl | Uup | Lv | Uus | Uuo | | | | | | | | | | | | | | | | | | | | | | | | |

M. Chhowalla *et al.*, *Nat. Chem.* **5**, 263 (2013)

- Trigonal prismatic phase
- $2Hc\text{-MX}_2$ (AbA, BaB stacking)
→ $\text{MoS}_2, \text{MoSe}_2, \text{WS}_2, \text{WSe}_2, \text{MoTe}_2$

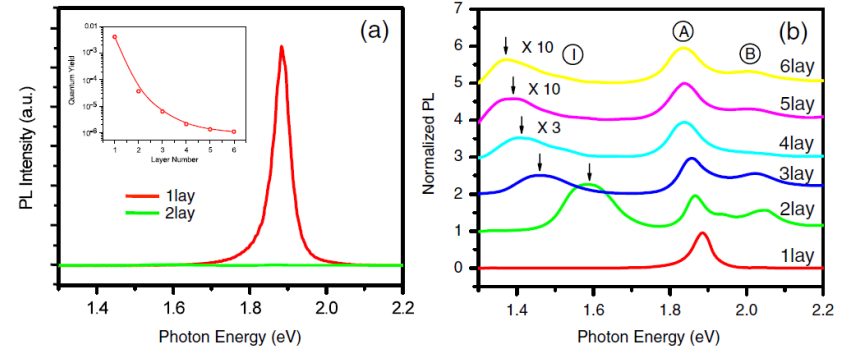




Some remarkable properties of 2Hc-TMD

Photonics

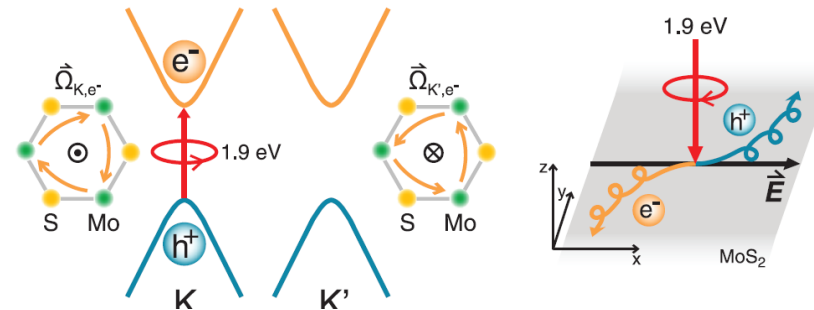
- Indirect (bulk) to direct (1L) bandgap \blacklozenge
- Tightly bound excitons (trions, biexcitons) \clubsuit
- Single photon emitters*
- Towards large PL quantum yields \spadesuit



K. F. Mak, PRL **105**, 136805 (2010)

Valleytronics

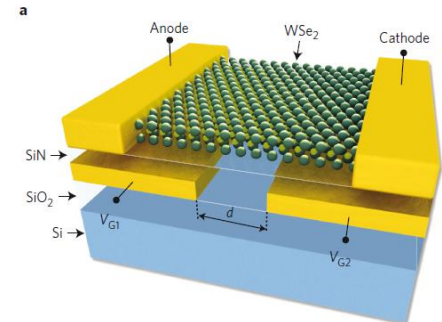
- All optical valley polarization
Mak *et al.* + Zeng *et al.*, Nat. Nano 2012
- Valley-Hall effect



Mak *et al.* Science 2014

Optoelectronics

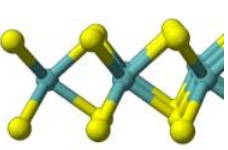
- Photodetection, electroluminescence, photovoltaics
- Type II van der Waals heterostructures
(Seattle, ICFO, Columbia, Berkeley, Manchester, MIT, Vienna, EPFL, U. Kansas,...)



Nat. Nano 2014 (TU Vienna, MIT, Seattle)

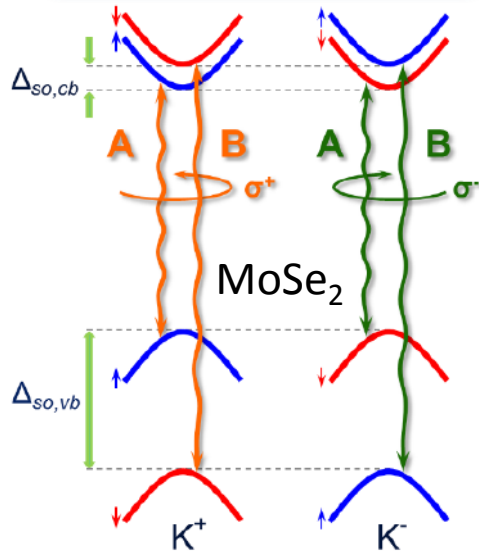
\blacklozenge \clubsuit Columbia, Berkeley, Case Western, Hong Kong, INSA Toulouse, Vanderbilt, LNCMI, Geneva...

*Nat Nano 2015 (ETH, Rochester, LNCMI, Hefei/Seattle) \spadesuit Amani *et al.* Science 2015



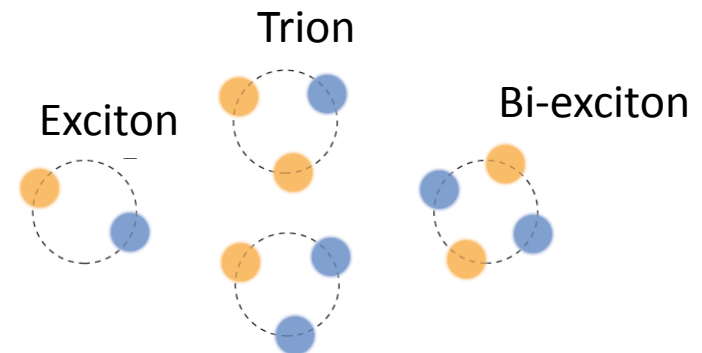
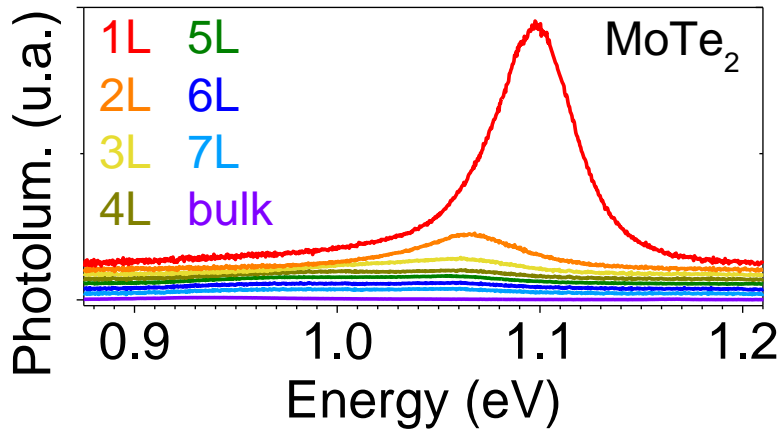
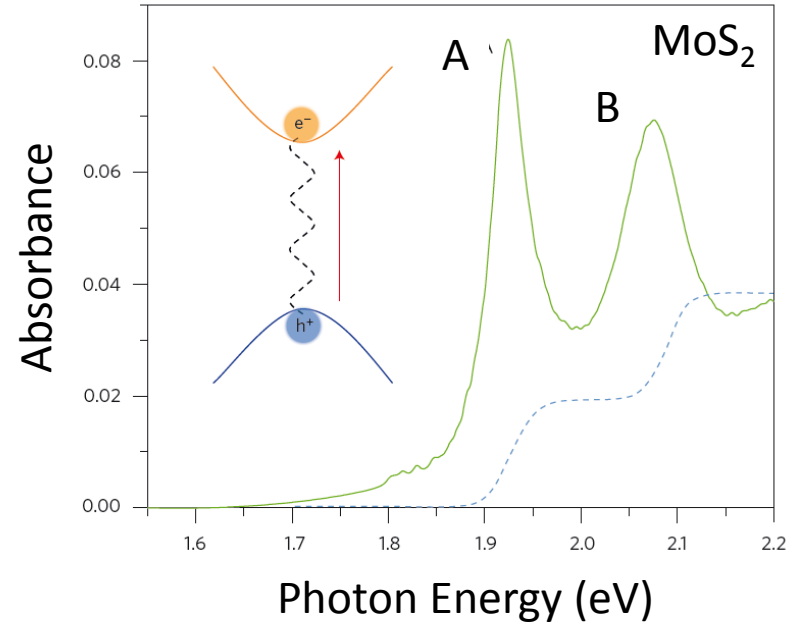
Basic optical properties of TMD

Spin-valley locking



Koperski *et al.* arXiv:1612.05879 (review)

Excitonic Effects

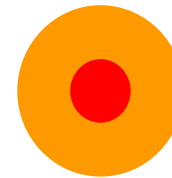
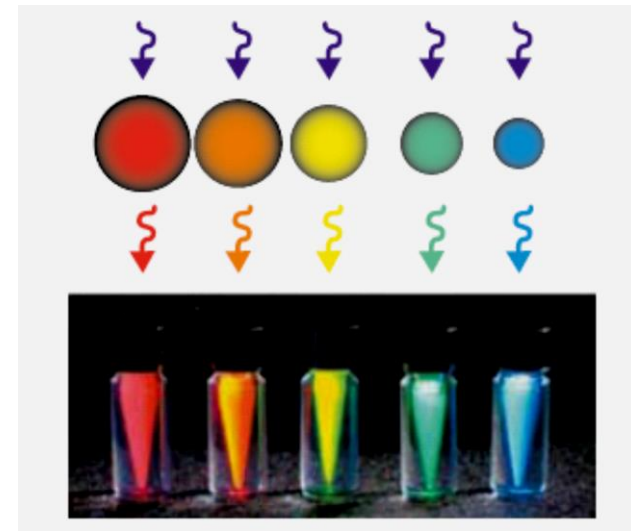
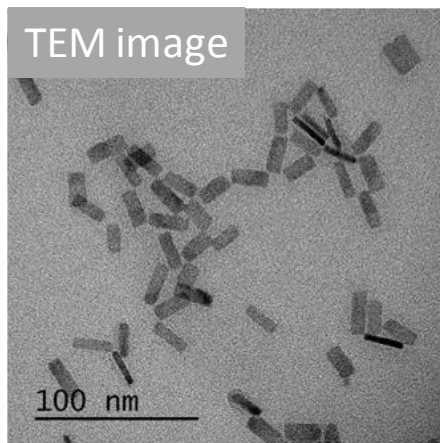
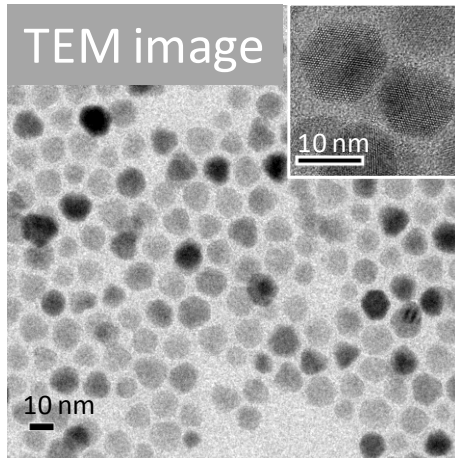


Mak & Shan, Nat. Photon. 2016 (review)

Froehlicher *et al.*, PRB 2016 (also Ruppert NL 2014, Lezama NL 2015)

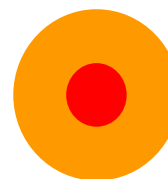
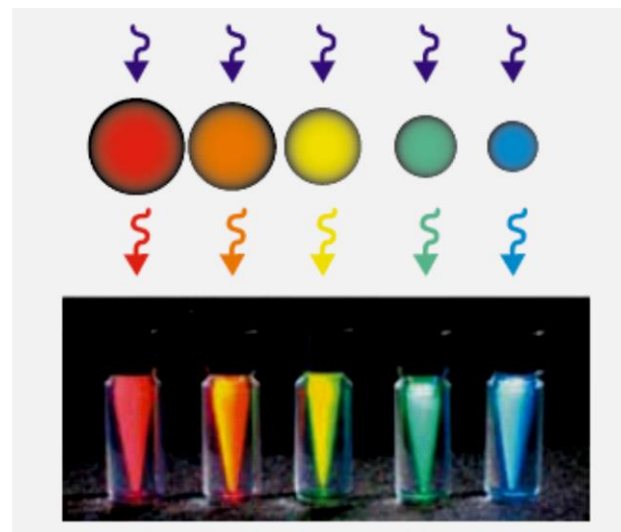
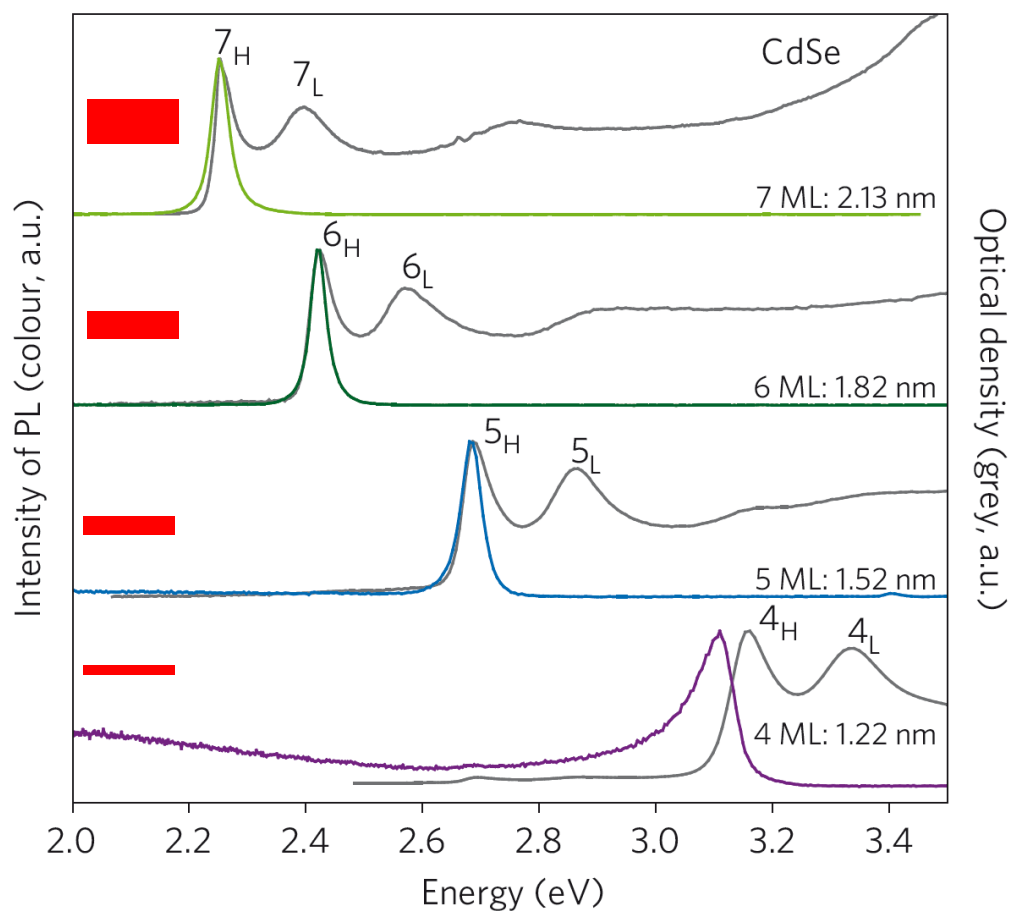
30+ years of colloidal semiconductor nanostructures

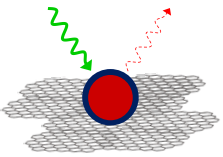
- Quantum dots (0D), rods (~1D), wells (2D)
- Size and shape tunable properties
- Broadband absorption / narrow emission



30+ years of colloidal semiconductor nanostructures

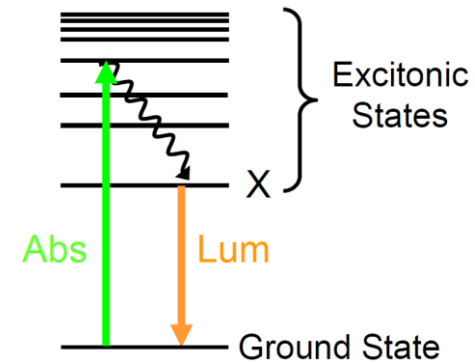
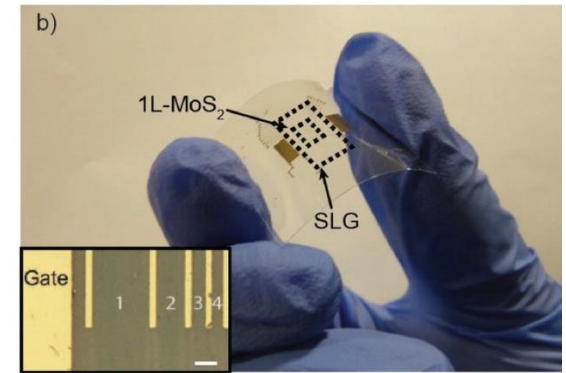
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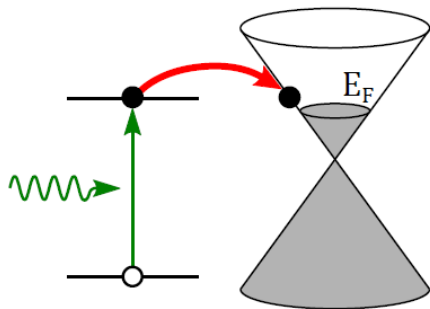


Hybrid systems and heterostructures: why the interest?

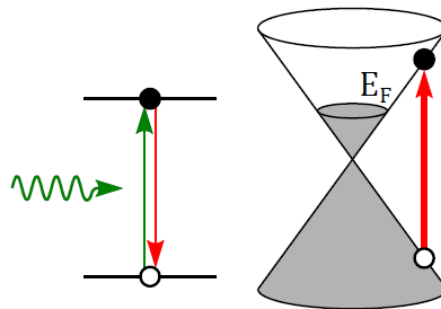
- **Graphene: 2D semi-metallic channel**
 - ✓ Quasi-transparent ($\sim 2\%$ absorption per layer)
 - ✓ High carrier mobility and large carrier density
- **TMD: atomically thin semiconducting channel**
 - ✓ Strong light matter interaction
 - ✓ Tunable properties
- **Semiconductor nanostructures: 0D, 1D, 2D**
 - ✓ Broadband absorption & size tunable emission
 - ✓ Highly photostable



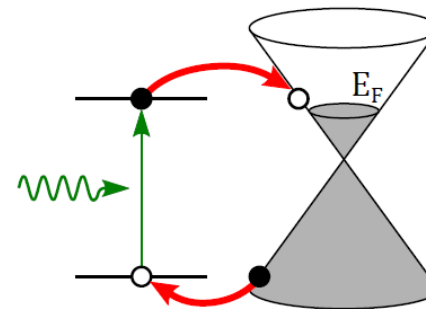
(a) Charge transfer



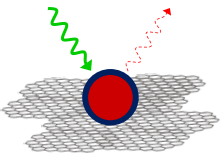
(b) Foerster energy transfer



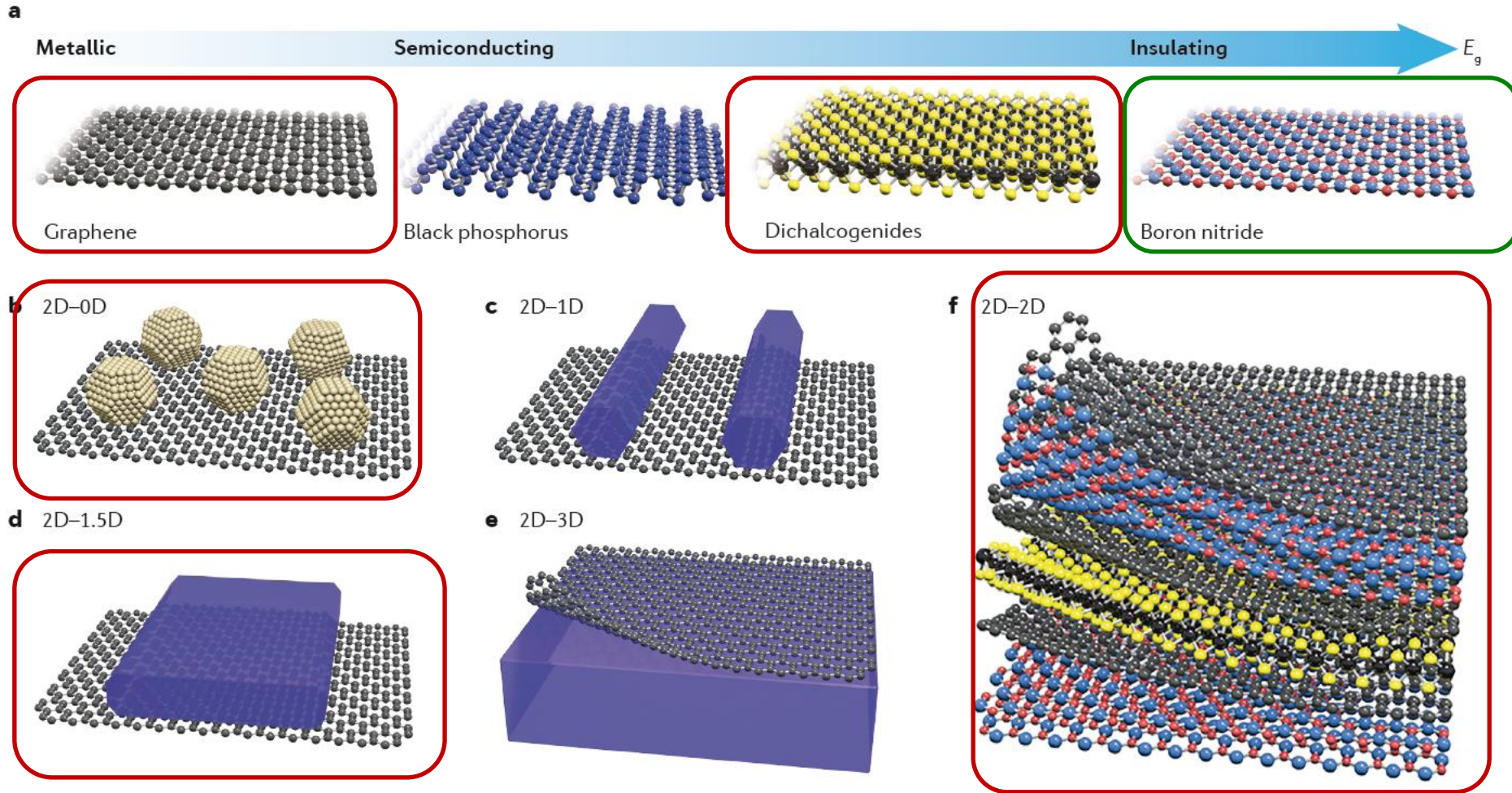
(c) Dexter energy transfer



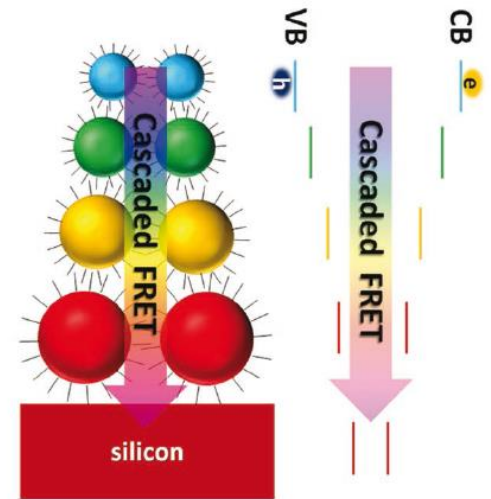
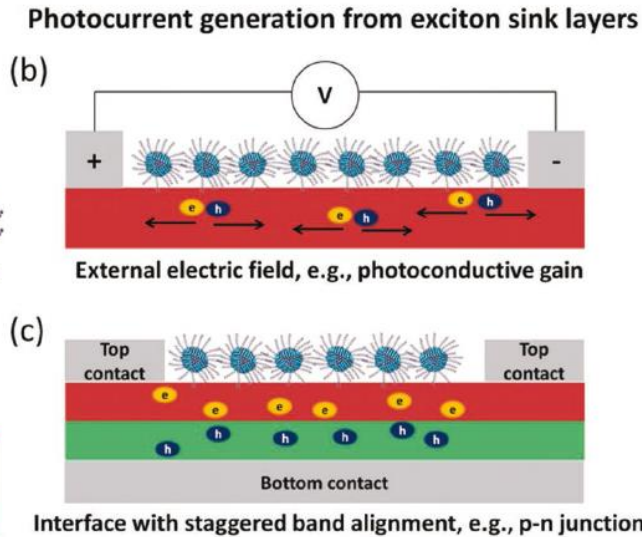
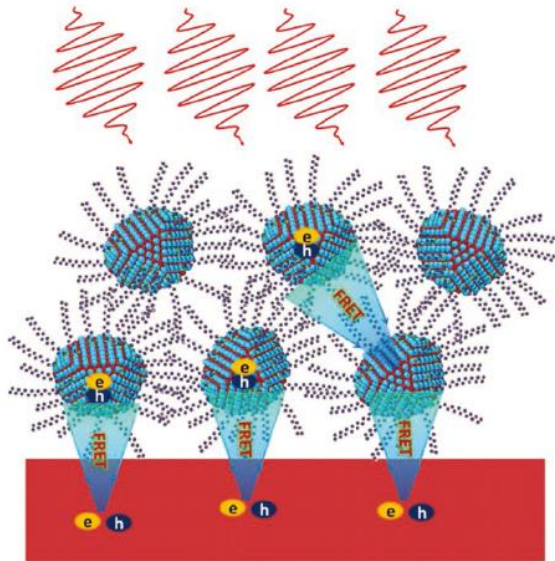
➤ *Harnessing near-field interactions in new optoelectronic devices*



Hybrid systems and heterostructures



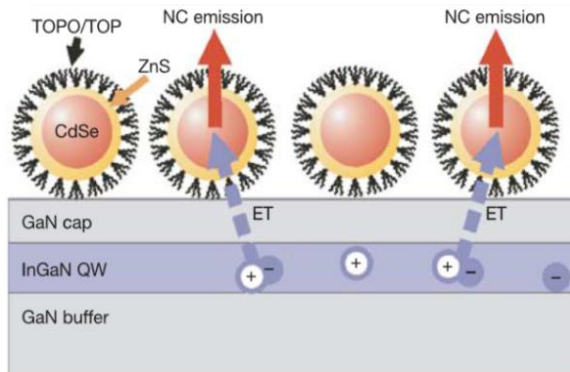
FRET in hybrid optoelectronic devices



B. Guzelturk & HV Demir *Advanced Functional Materials* 10.1002/adfm.201603311

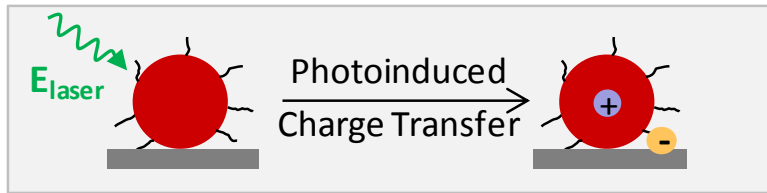
Energy Transfer Pumping

Achermann *et al.*
Nature (2004)
(Los Alamos)



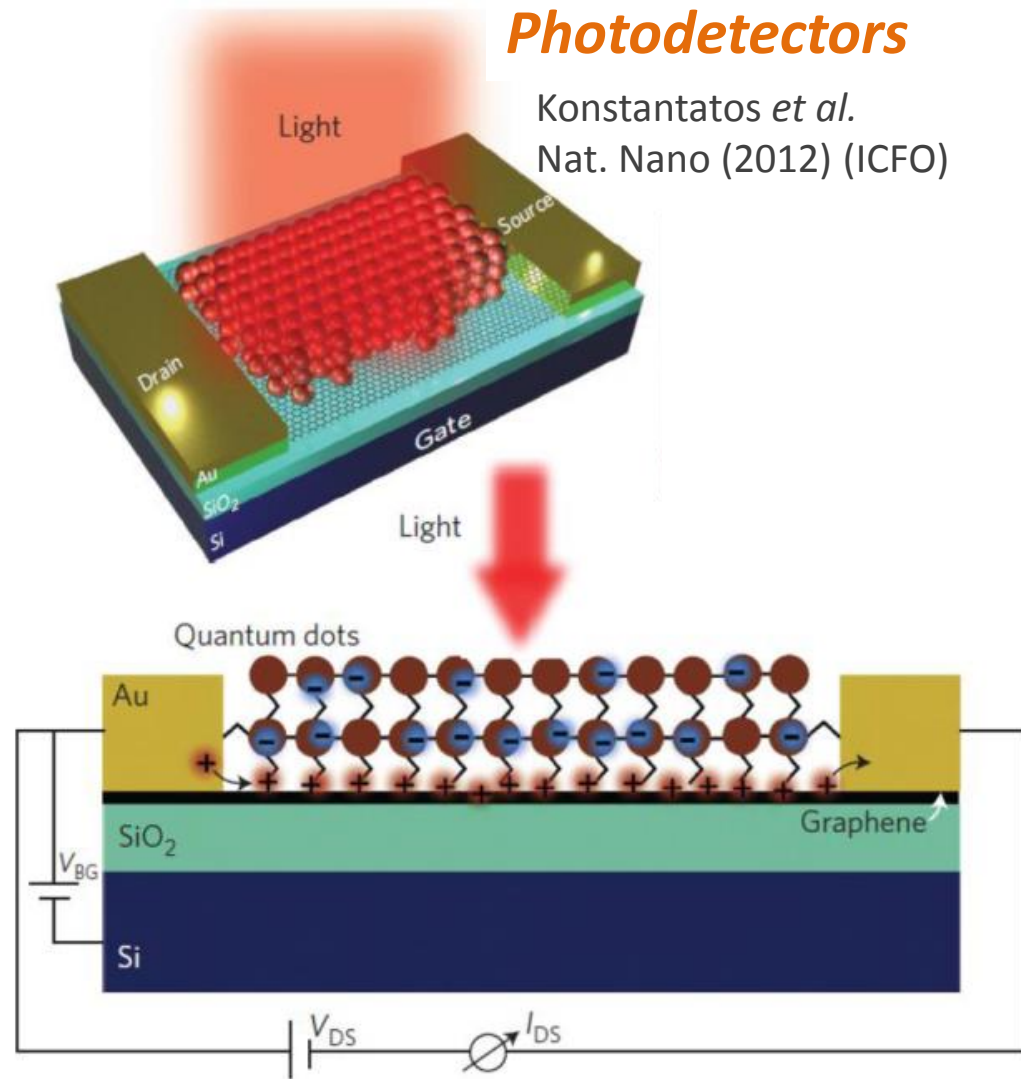
- + Energy/exciton funnelling
- Substrate sensitization
- Color conversion
- Long Range ($\gg 1$ nm)
- How to separate the transferred excitons?

Charge Transfer in hybrid photodetectors



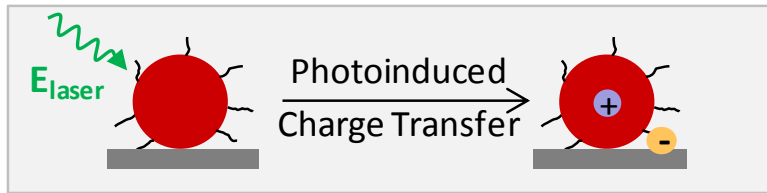
High gain Photodetectors

Konstantatos *et al.*
Nat. Nano (2012) (ICFO)



- + Photodetection
- + Short range (< 1 nm)
→ Selectivity/Sensitivity
Processability
- Short range...
- Highly sensitive to:
 - ✓ Surface states
 - ✓ Adsorbates
 - ✓ Interfaces/ligands

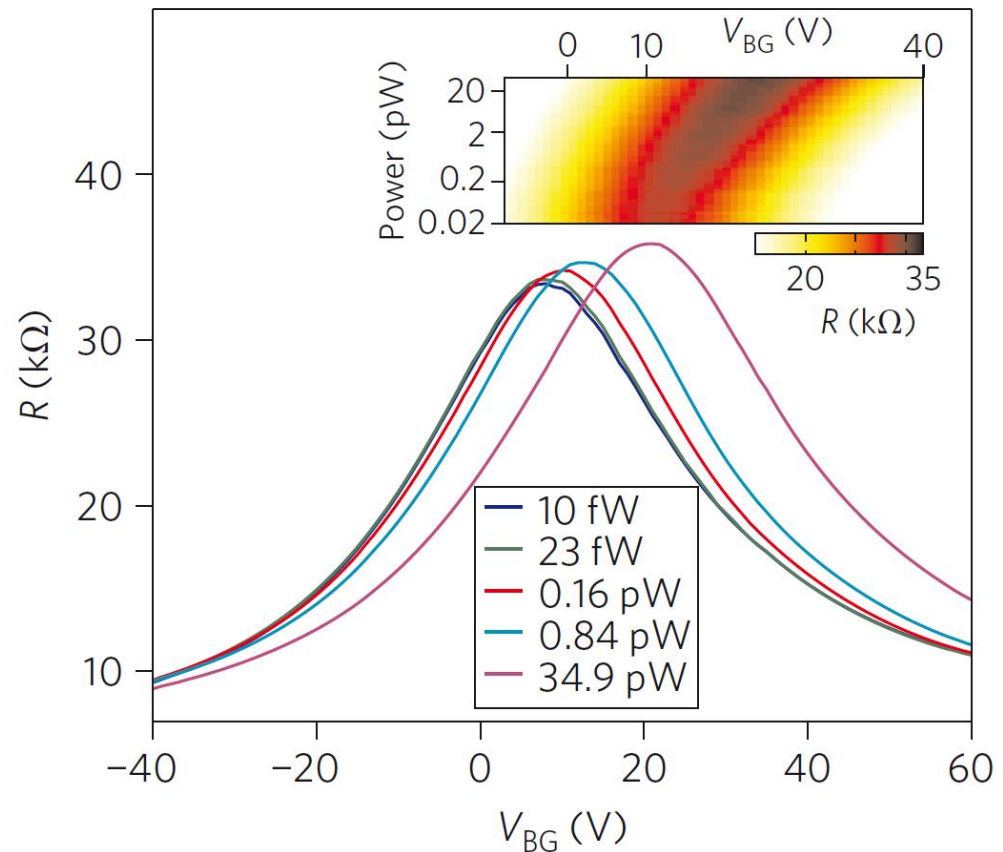
Charge Transfer in hybrid photodetectors



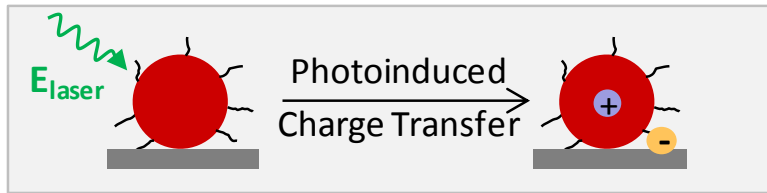
High gain Photodetectors

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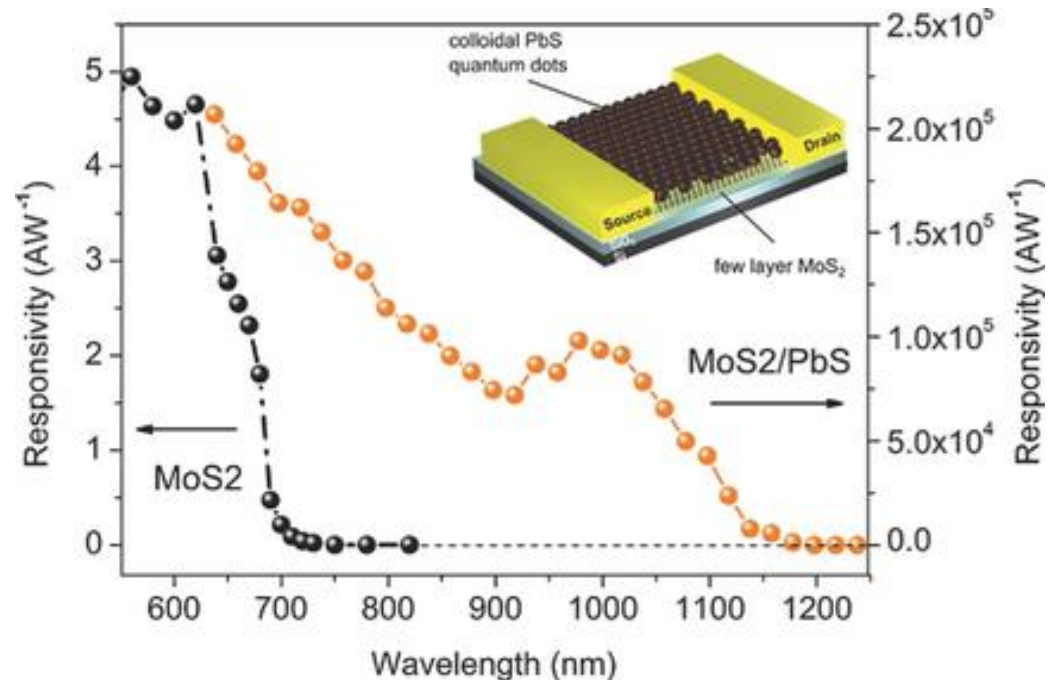
Charge Transfer in hybrid photodetectors



High gain Photodetectors

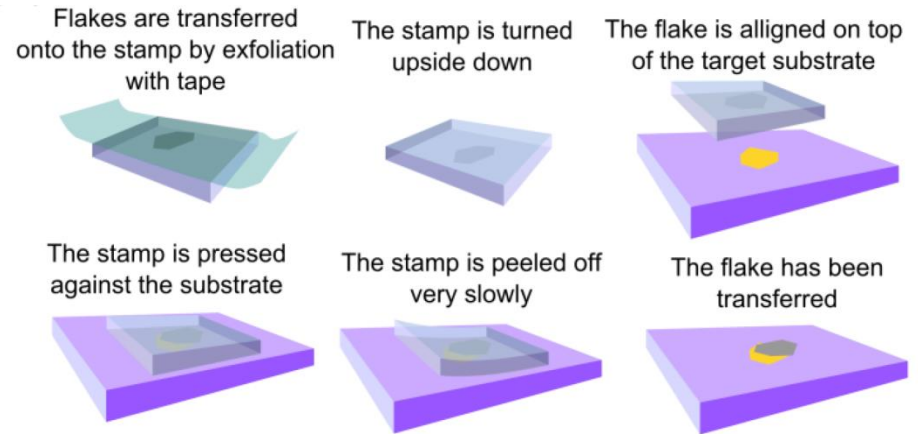
Kufer *et al.*
Advanced Mat. (2015)

- + Photodetection
- Short range (< 1 nm)
→ Selectivity/Sensitivity
Processability
- Short range...
- Highly sensitive to:
 - ✓ Surface states
 - ✓ Adsorbates
 - ✓ Interfaces/ligands

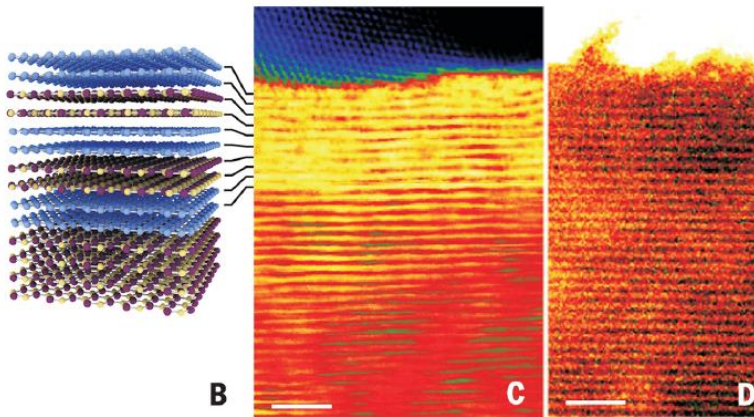


van der Waals Heterostructures

- ✓ No dangling bounds
 - ✓ No lattice mismatch issues
 - ✓ Rotational degree of freedom
- 2010 : Graphene on hBN
 - 2017 : wet or dry transfer, pick up and lift,...
 - Numerous possibilities!



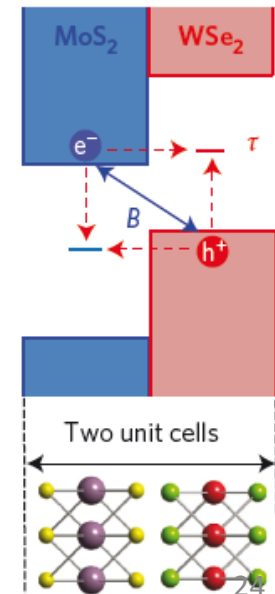
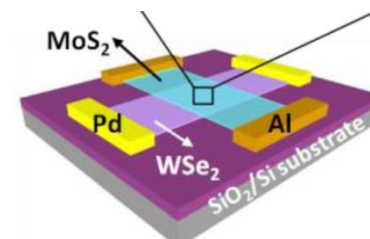
Castellanos-Gomez *et al.* 2D Materials **1** 011002 (2014)



Haigh, Gorbachev *et al.*, Nature Materials 2012
Manchester Group

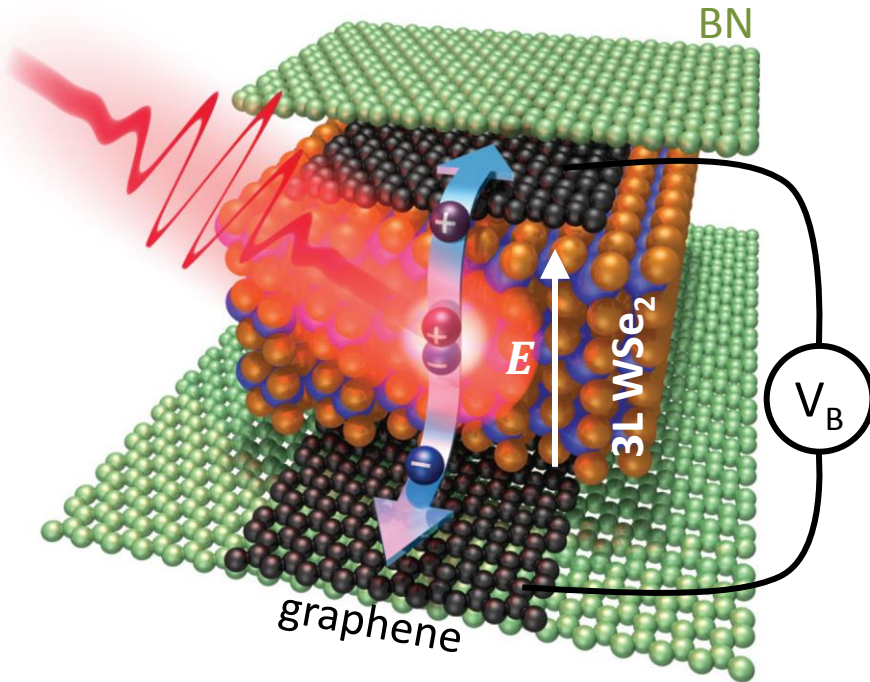
Atomically thin *p-n* junctions

C-H Lee *et al.*
Nat. Nano (2014)
(Columbia)



Optoelectronic devices based on vdWH: key mechanisms

BN/Gr/WSe₂/Gr/BN



Atomic dimensions \neq conventional heterostructures

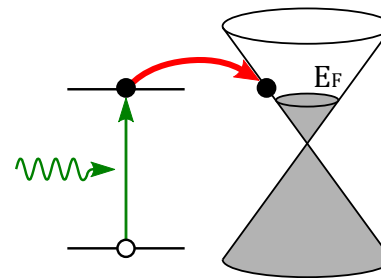
- 1 Exciton formation
- 2 Exciton dissociation
- 3 Charge transport
- 4 Interfacial transfer

+ losses: exciton recombination

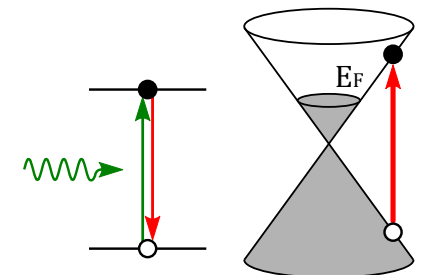
M. Massicotte *et al.*, Nat. Nano. 11, 42 (2016)

- ✓ Photoactive material: **WSe₂**
- ✓ Electrical contacts: **graphene**
- ✓ Electric field: **V_B**

Charge transfer

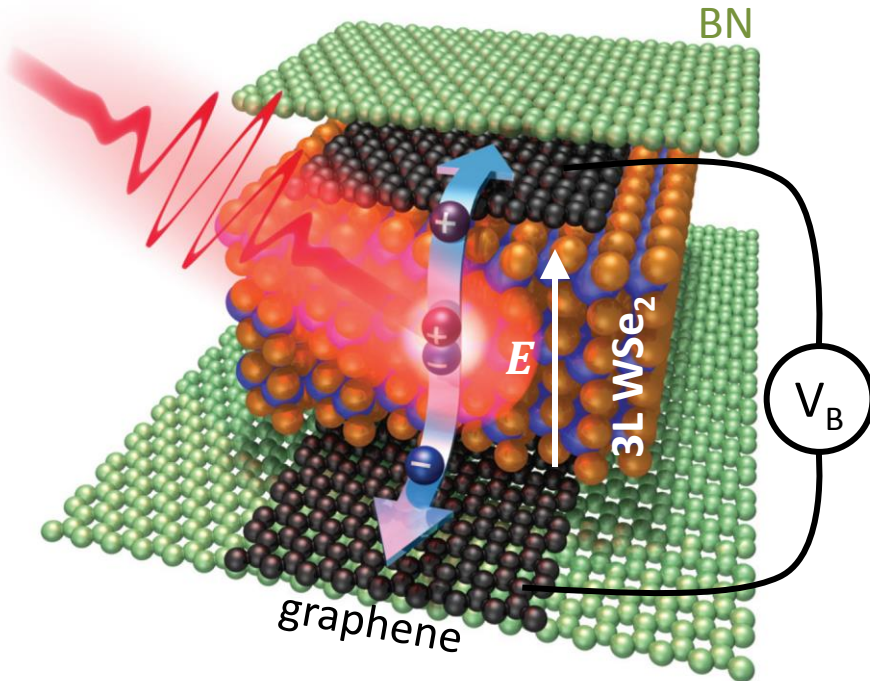


Energy transfer



Optoelectronic devices based on vdWHs: key mechanisms

BN/Gr/WSe₂/Gr/BN

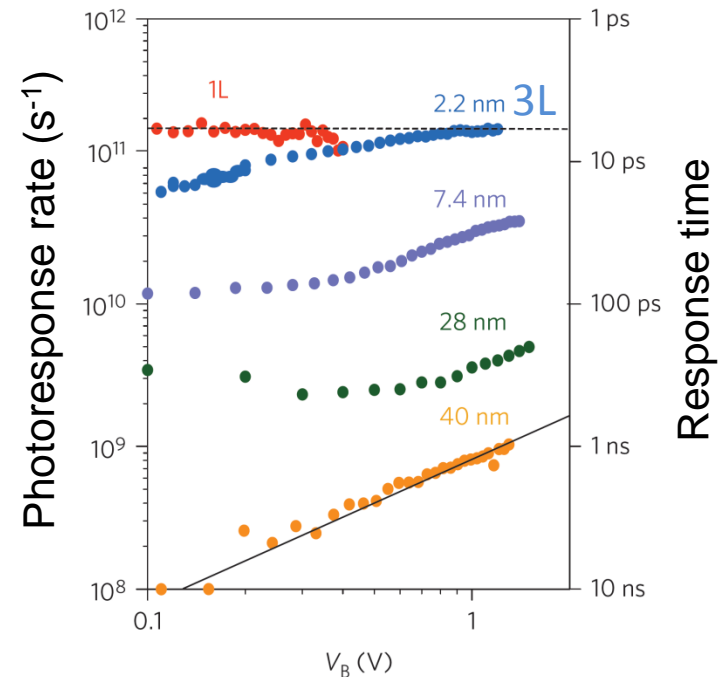


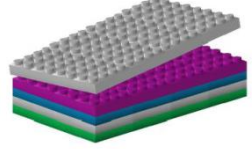
- 1 Exciton formation
- 2 Exciton dissociation
- 3 Charge transport
- 4 Interfacial transfer

+ losses: exciton recombination

M. Massicotte *et al.*, Nat. Nano. 11, 42 (2016)

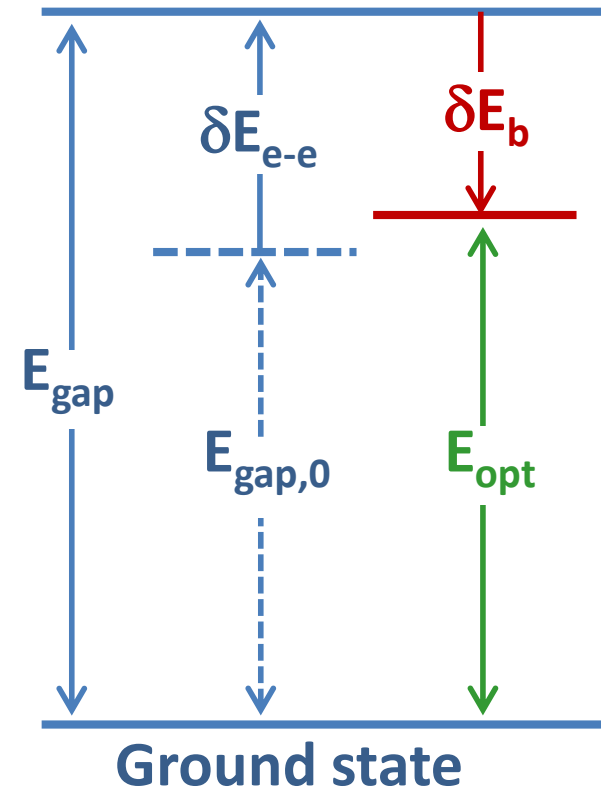
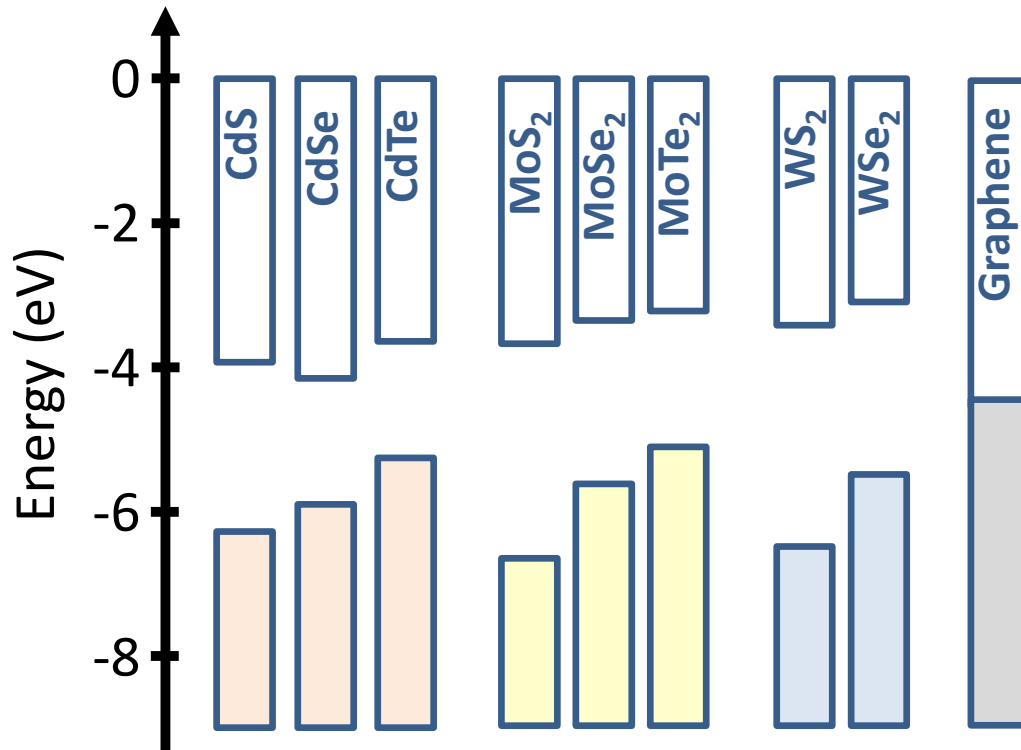
- ✓ Photoactive material: **WSe₂**
- ✓ Electrical contacts: **graphene**
- ✓ Electric field: **V_B**





Band alignment and excitonic effects

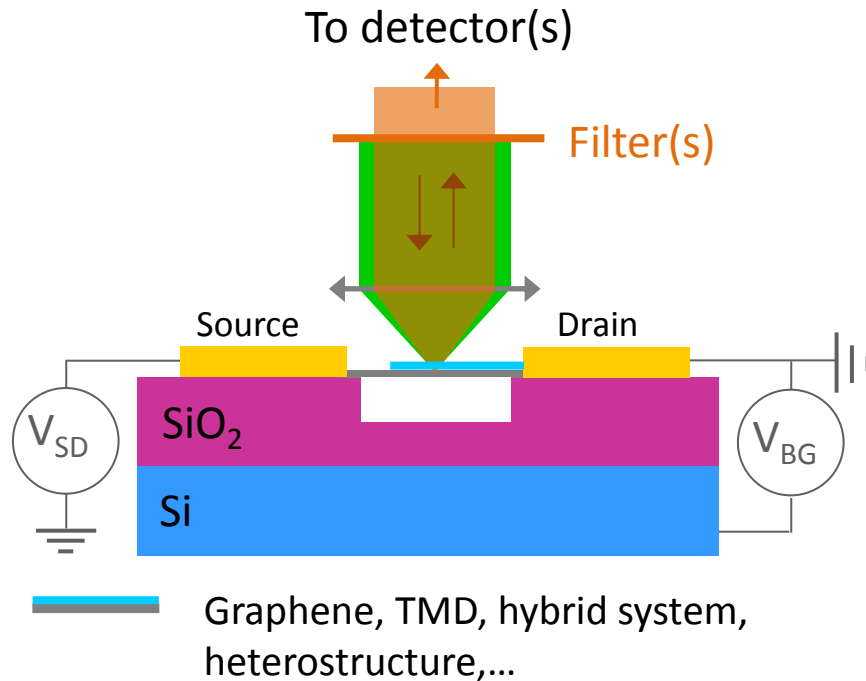
Type I (CdSe/ZnS) or II (CdSe/CdTe) Heterojunctions Optical Gap < Transport Gap



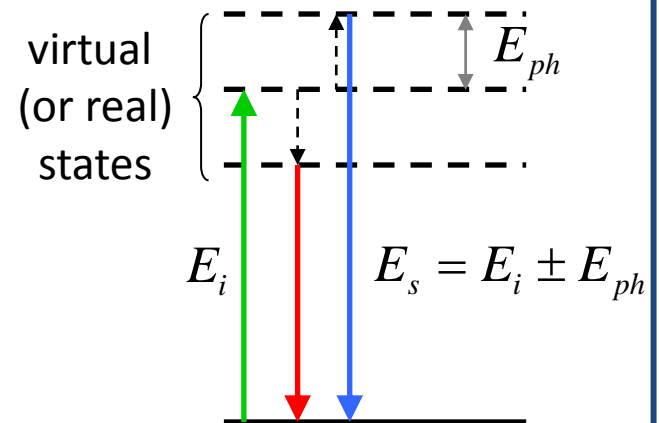
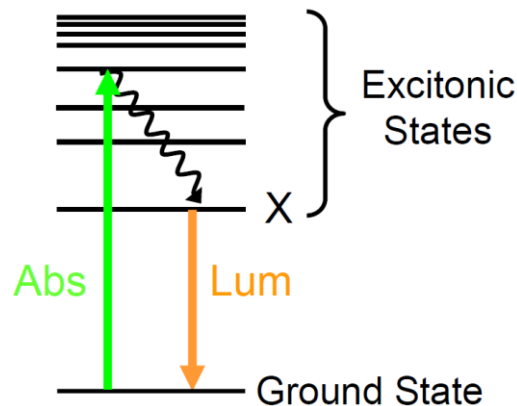
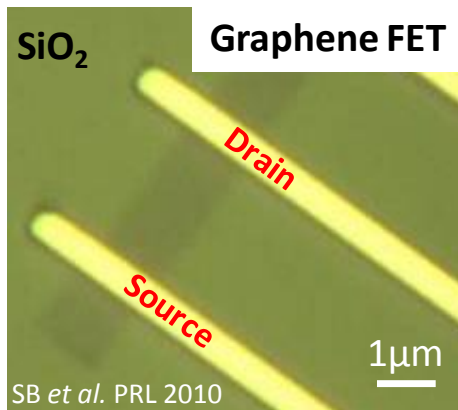
TMD: Y. Liang et al., APL **103**, 42106 (2013), M. Ugeda *et al.*, Nat. Mater. **5**, 1091 (2014)

Graphene: Y.-J. Yu *et al.*, Nano Lett. **9**, 3430 (2008), II-VI semicond : Norris et al. Science 2008

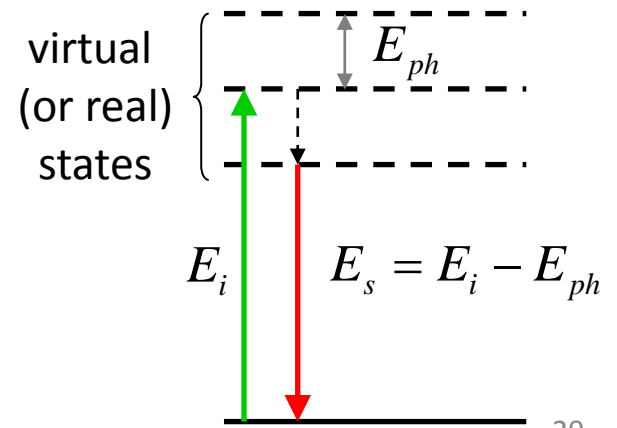
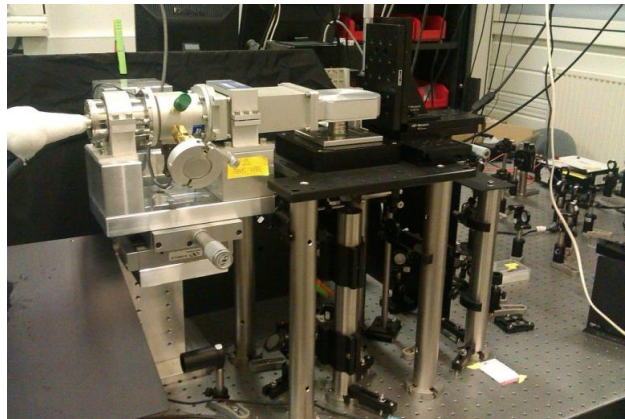
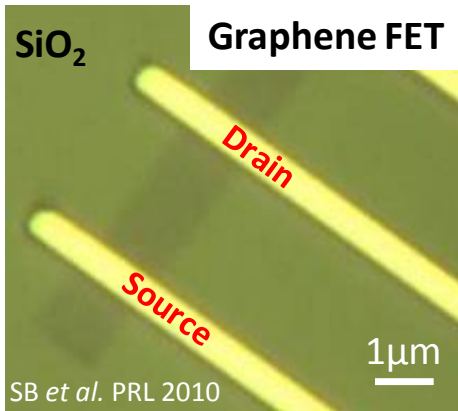
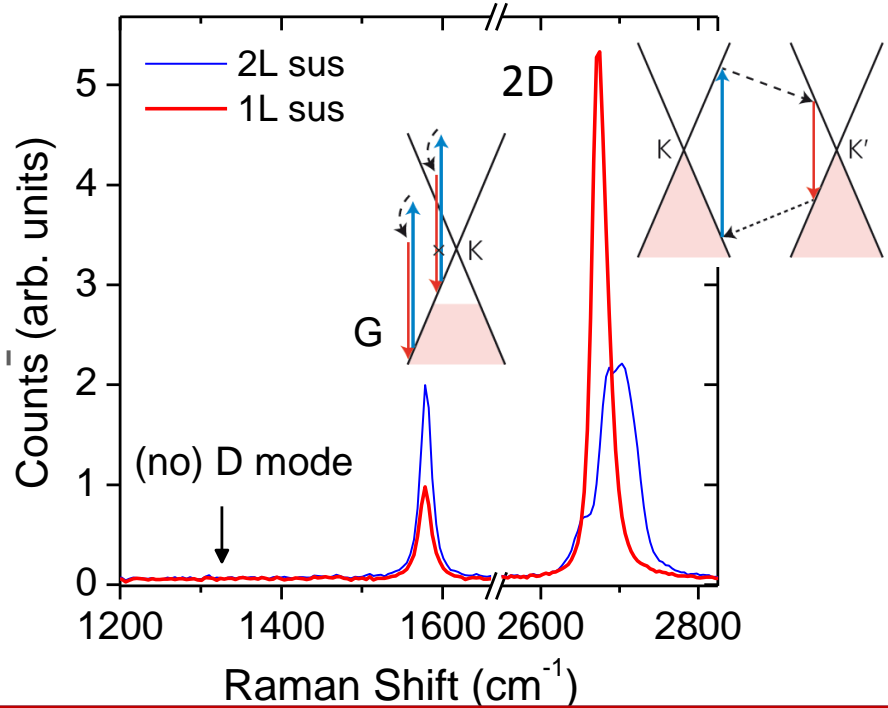
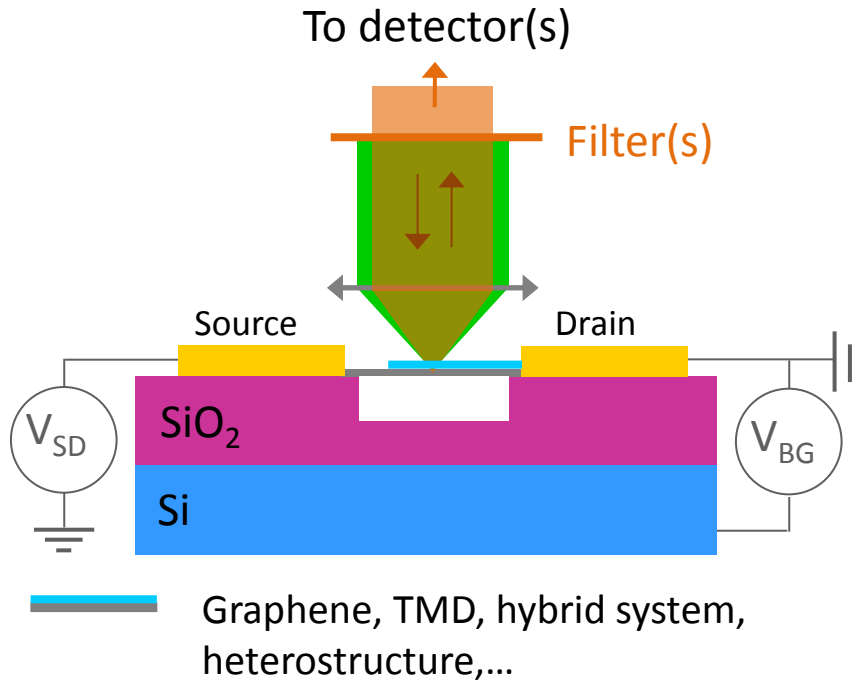
Our experimental approach



- **(micro)-optical spectroscopy**
 - Photoluminescence, Raman,...
- **Exciton dynamics**
 - Time correlated photon counting
- **Nanofabrication**
 - Optoelectronics
 - (electro-)optomechanics

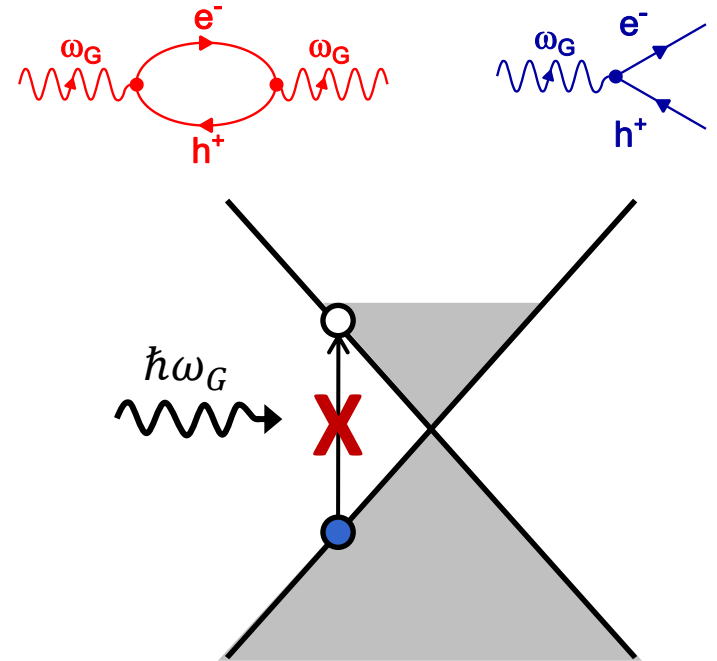
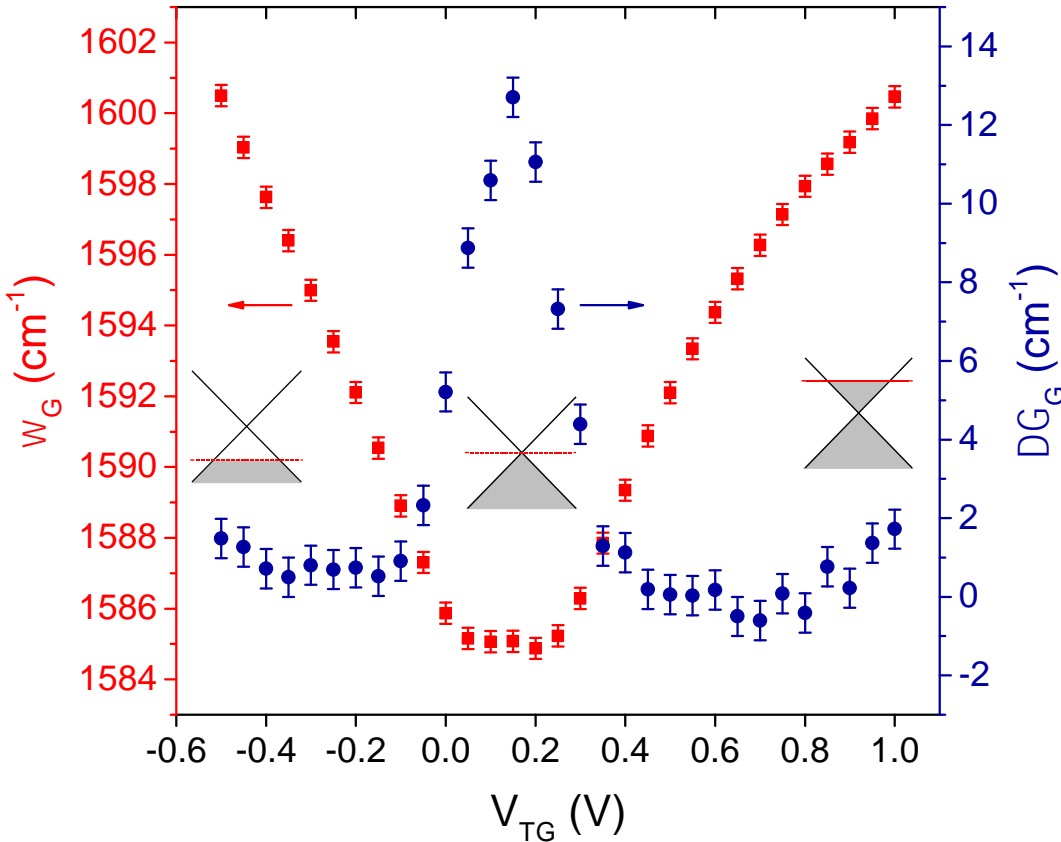


Our experimental approach



Electron-phonon coupling and Raman spectroscopy

G phonon renormalization



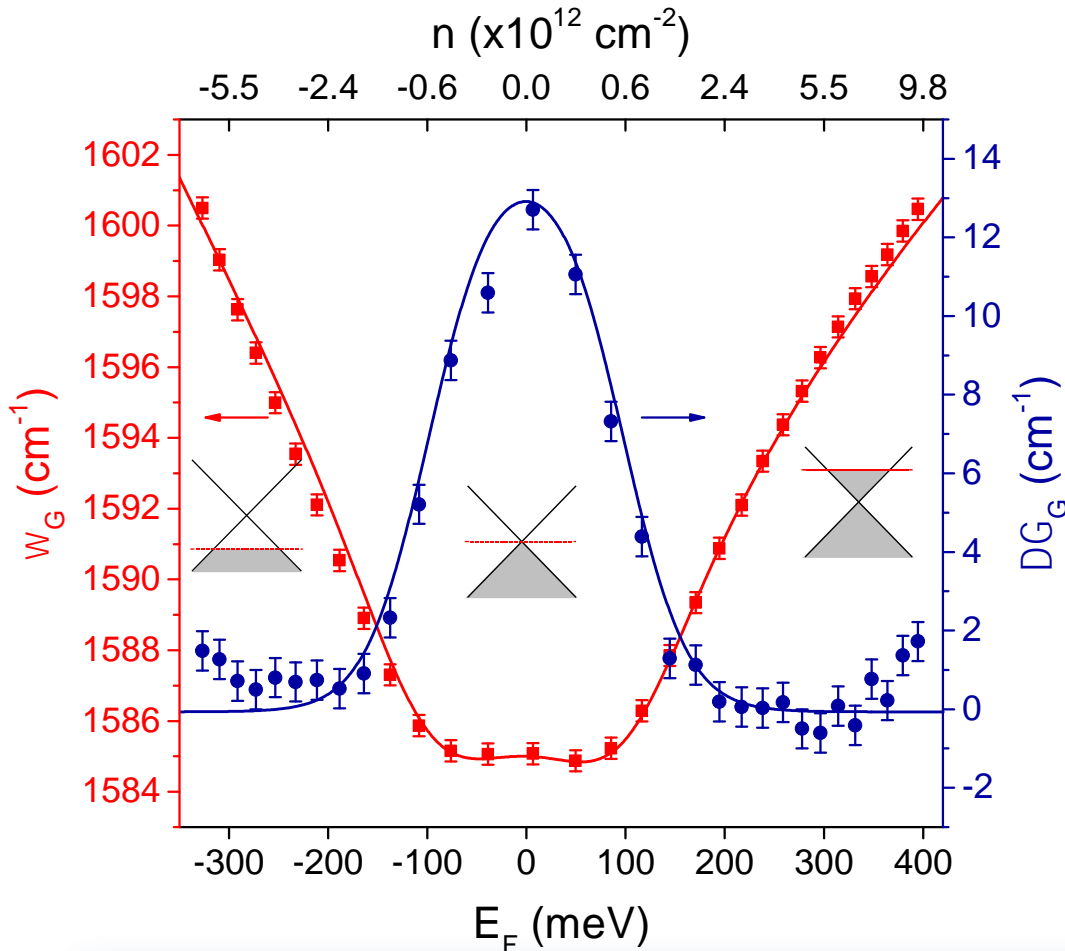
→ $\lambda_\Gamma = 0.031$

$$\Delta\omega_G = \omega_G - \omega_G^0 = \frac{\lambda_\Gamma}{2\pi\hbar} P \int_{-\infty}^{+\infty} \frac{[f(E - E_F) - f(E)]E^2 \text{sgn}(E)}{E^2 - (\hbar\omega_G^0)^2/4} dE + \Delta\omega_G^A$$

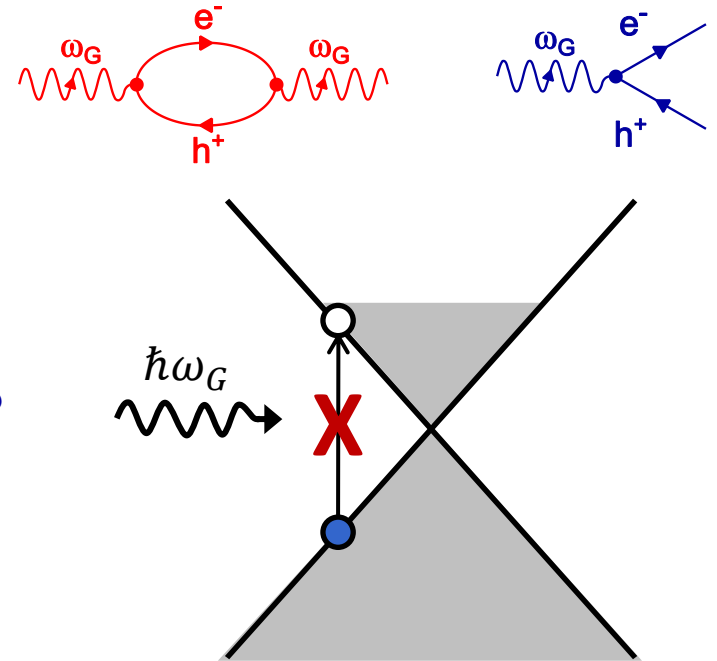
$$\Delta\Gamma_G = \Gamma_G - \Gamma_0 = \frac{\lambda_\Gamma}{4} \left[f\left(\frac{-\hbar\omega_G^0}{2} - E_F\right) - f\left(\frac{\hbar\omega_G^0}{2} - E_F\right) \right]$$

Data: G. Froehlicher & SB PRB 2015
 See also: M. Lazzeri & F. Mauri, PRL **97**, 266407 (2006)
 S. Pisana *et al.*, Nat. Mat. **6**, 198 (2007)
 J. Yan *et al.*, PRL **98**, 166802 (2007)

Electron-phonon coupling and Raman spectroscopy



G phonon renormalization



→ $\lambda_{\Gamma} = 0.031$

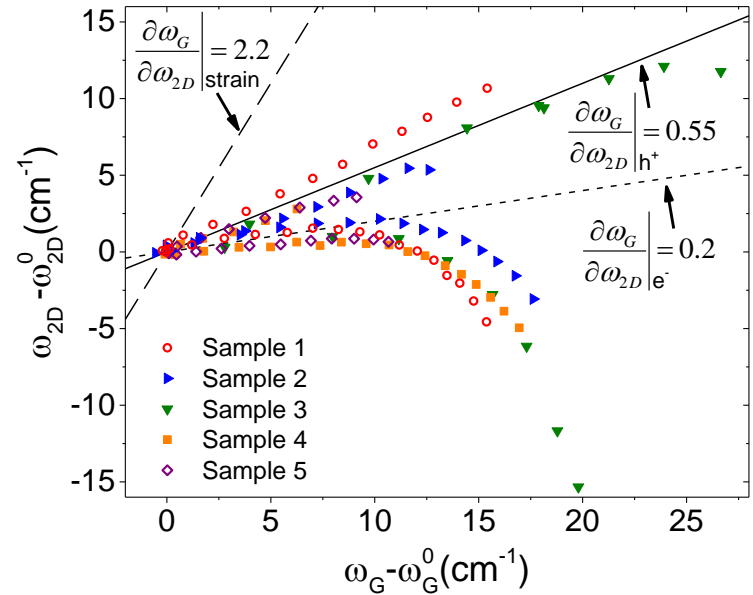
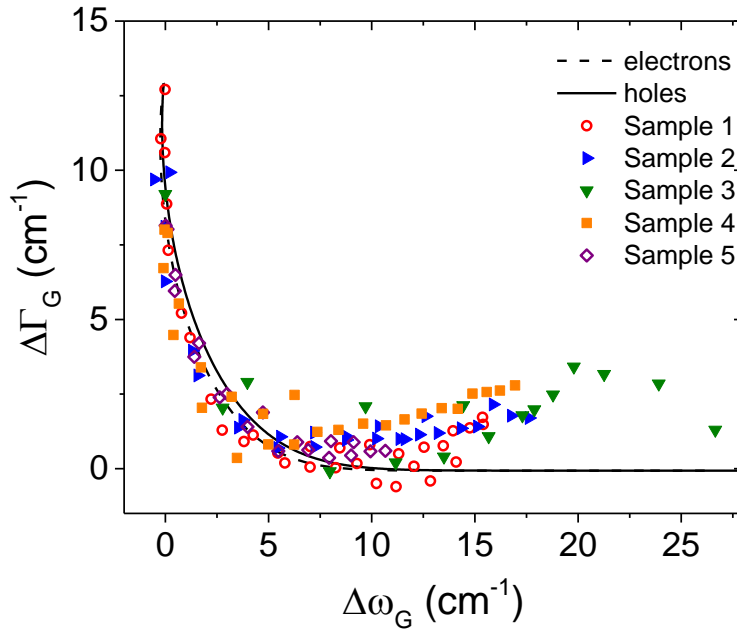
$$\Delta\omega_G = \omega_G - \omega_G^0 = \frac{\lambda_{\Gamma}}{2\pi\hbar} P \int_{-\infty}^{+\infty} \frac{[f(E - E_F) - f(E)]E^2 \text{sgn}(E)}{E^2 - (\hbar\omega_G^0)^2/4} dE + \Delta\omega_G^A$$

$$\Delta\Gamma_G = \Gamma_G - \Gamma_0 = \frac{\lambda_{\Gamma}}{4} \left[f\left(\frac{-\hbar\omega_G^0}{2} - E_F\right) - f\left(\frac{\hbar\omega_G^0}{2} - E_F\right) \right]$$

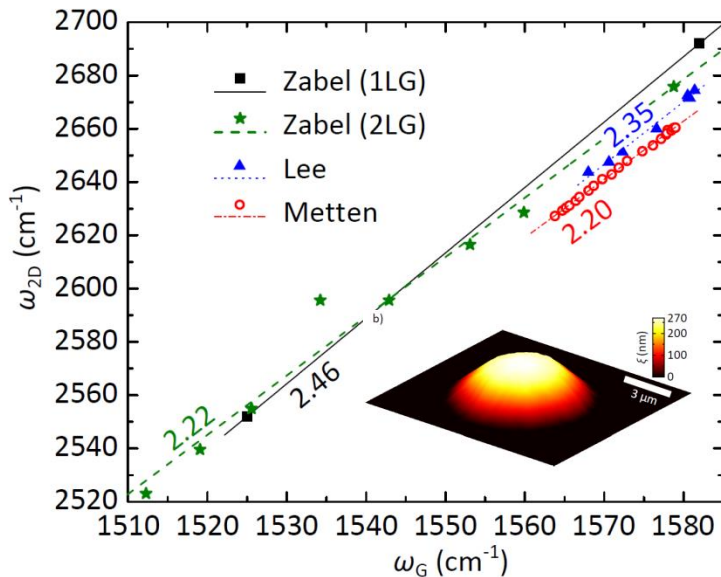
Data: G. Froehlicher & SB PRB 2015
 See also: M. Lazzeri & F. Mauri, PRL **97**, 266407 (2006)
 S. Pisana *et al.*, Nat. Mat. **6**, 198 (2007)
 J. Yan *et al.*, PRL **98**, 166802 (2007)

Separating doping and strain

Doping



Strain



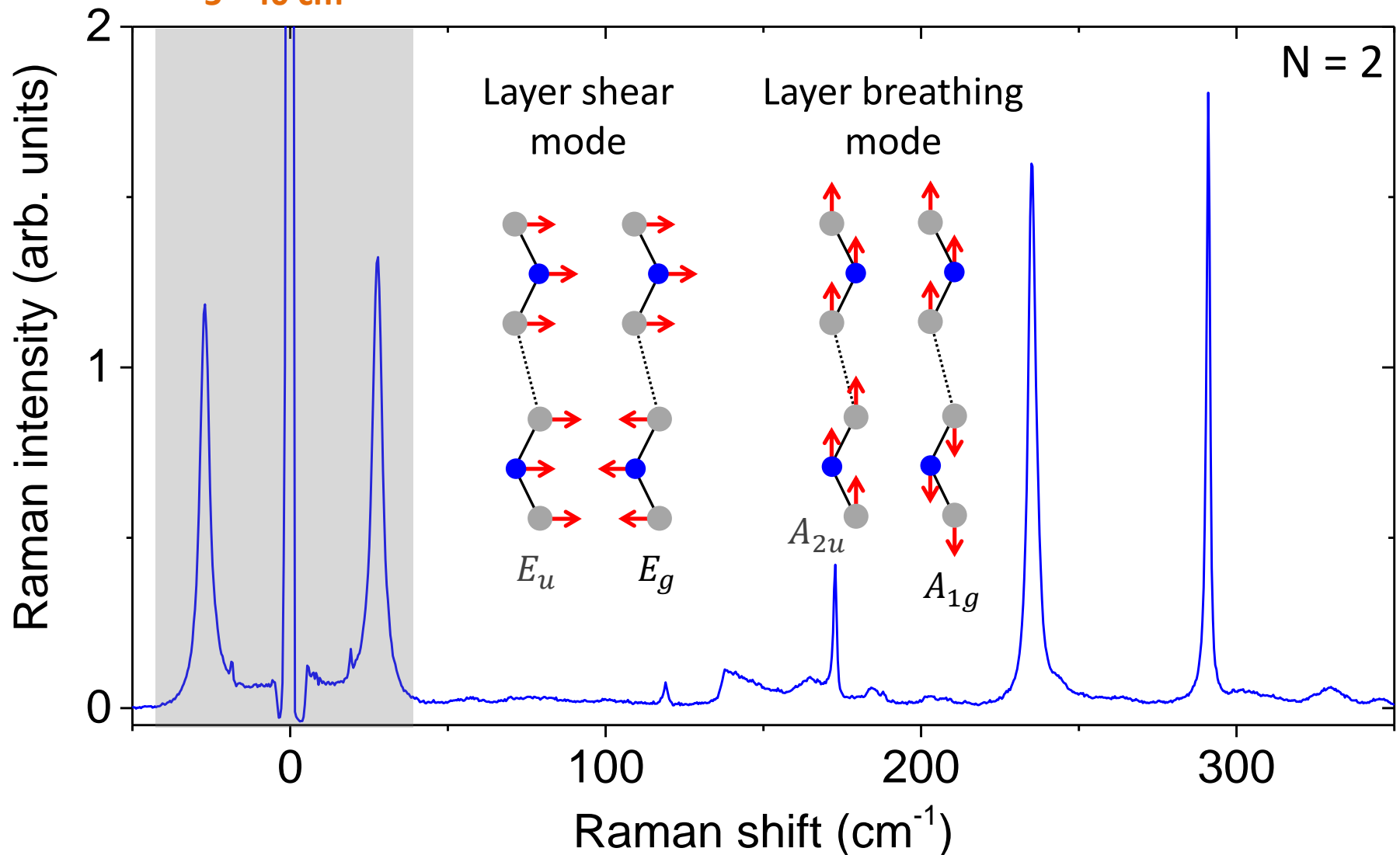
Well-defined and useful correlations between Raman parameters

Data : Froehlicher & Berciaud, PRB 2015
 Metten *et al.*, PRApplied 2014
 Zabel *et al.*, Nano Lett 2012
 Lee *et al.*, Nano Lett 2012
 See also : A. Das *et al.*, Nat Nano 2008
 Lee *et al.*, Nat Comm 2012

Raman Spectrum of bilayer MoTe_2

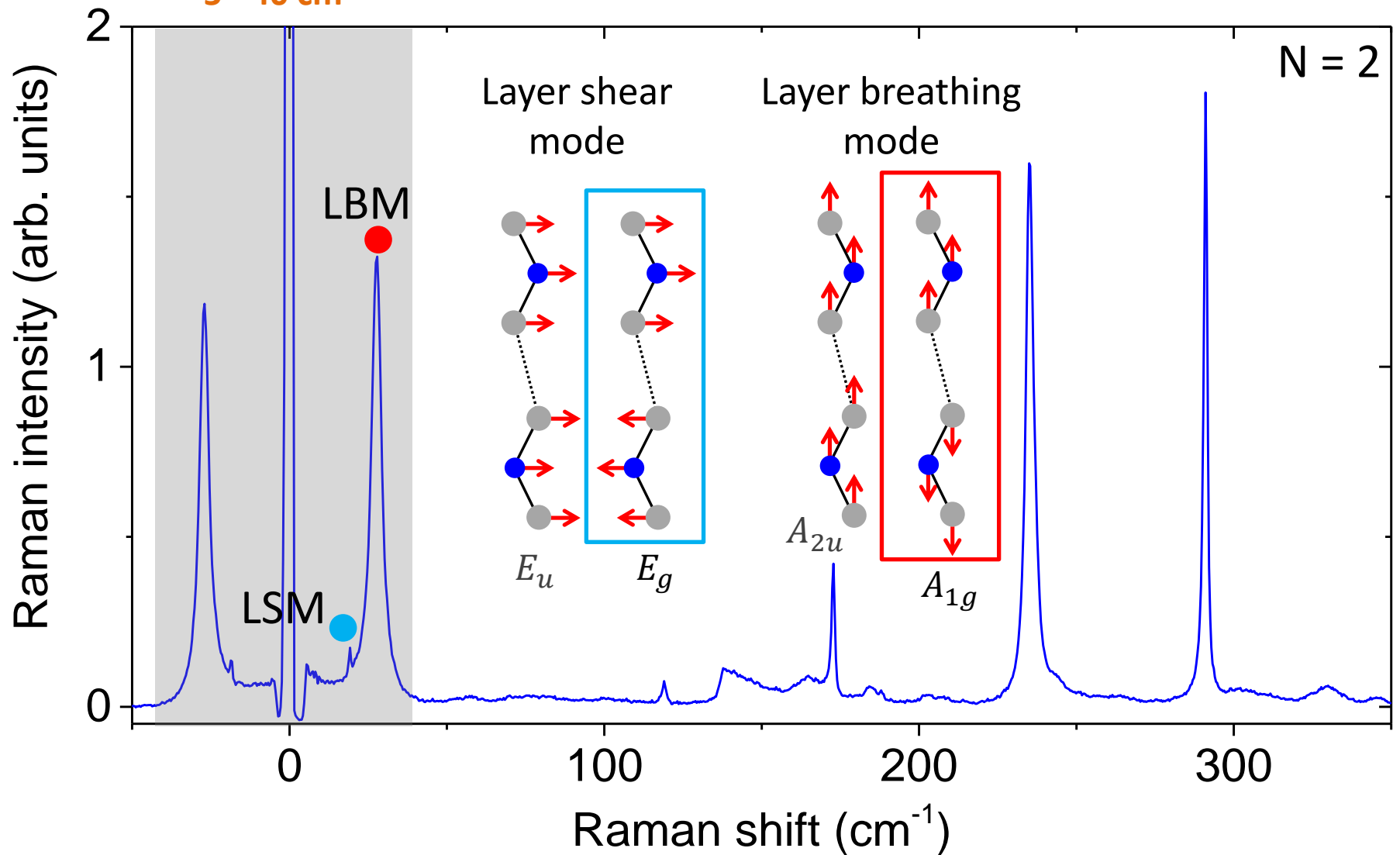
Low frequency
5 - 40 cm^{-1}

$E_L = 2.33 \text{ eV}$

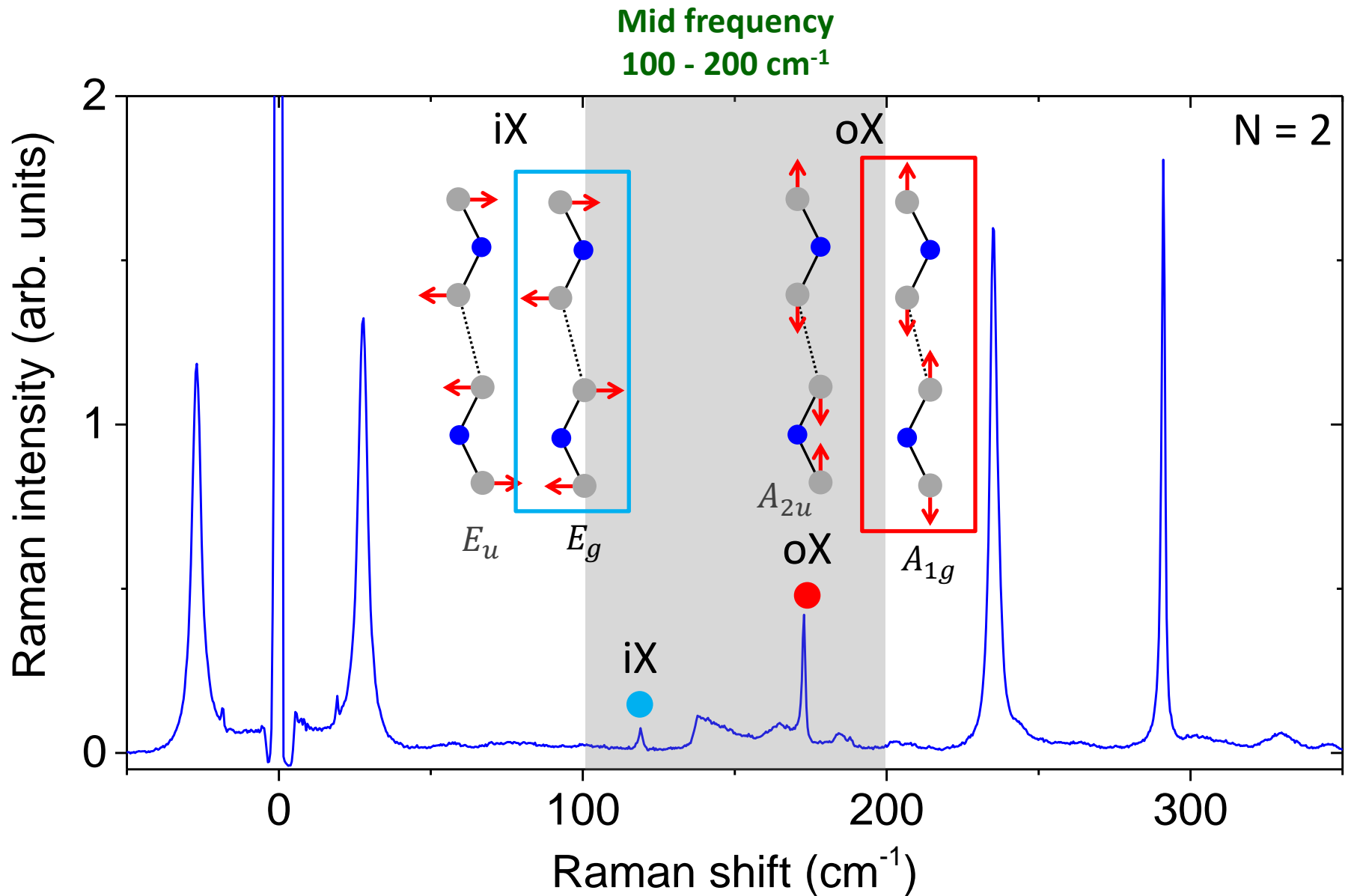


Raman Spectrum of bilayer MoTe_2

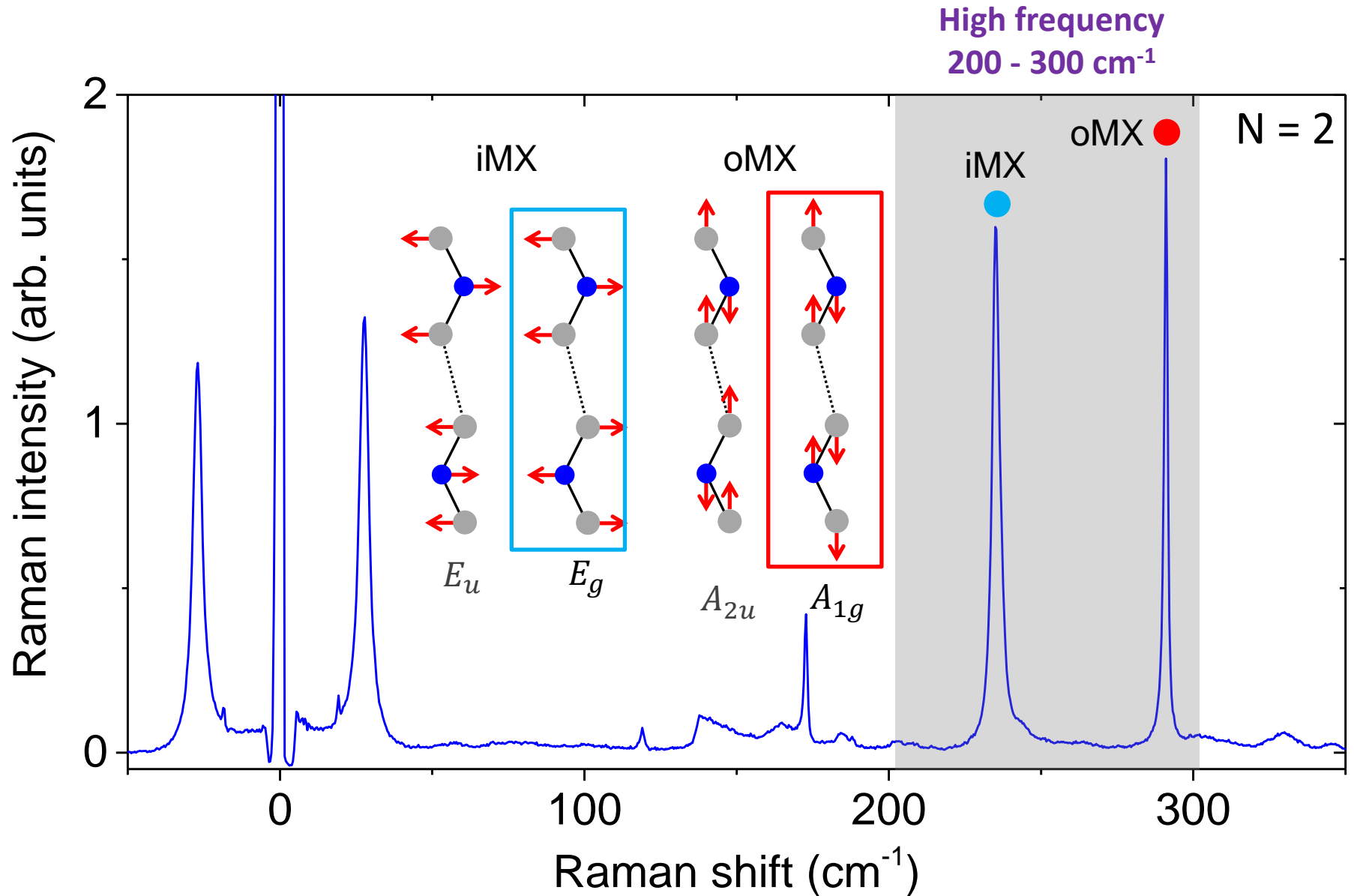
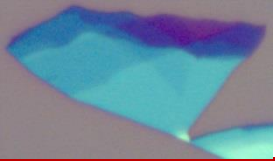
Low frequency
5 - 40 cm^{-1}



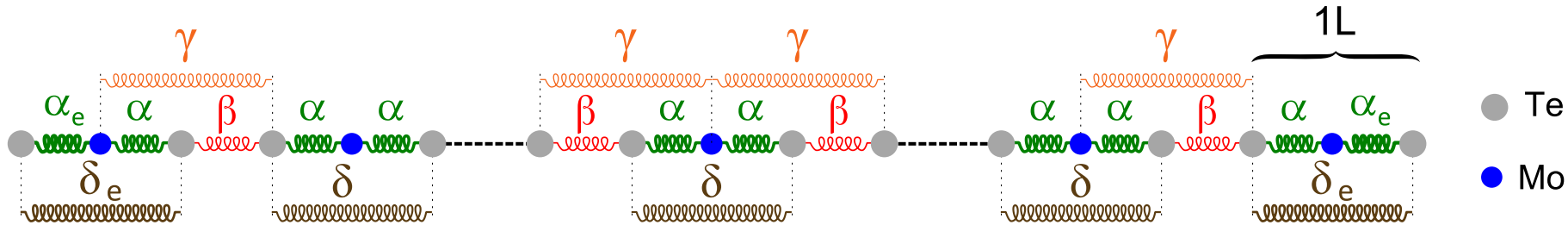
Raman Spectrum of bilayer MoTe_2



Raman Spectrum of bilayer MoTe₂

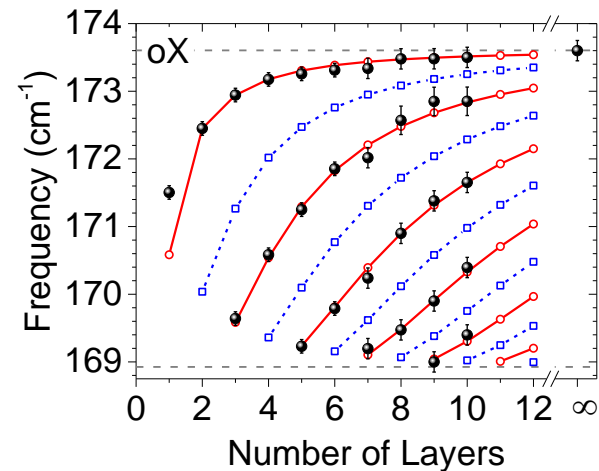
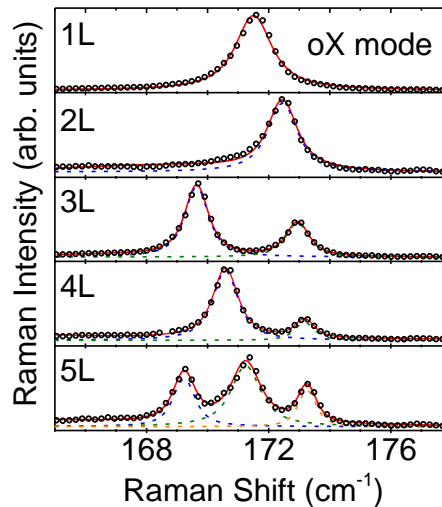
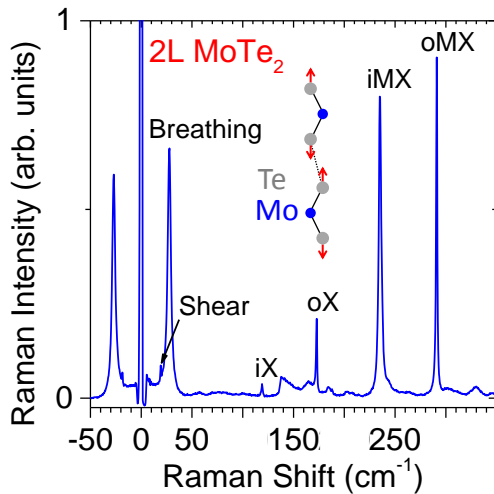


Raman Spectrum of bilayer MoTe₂



Luo *et al.*, PRB **88**, 075320 (2013)

✓ Interlayer interactions: Davydov splitting and unified description of the phonon modes



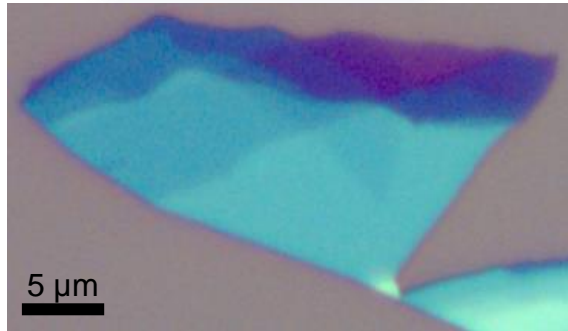
Froehlicher *et al.*, Nano Lett. **15**, 6481 2015 (MoTe₂), Lorchat *et al.* ACS Nano 2016 (ReS₂ and ReSe₂)

Related works:

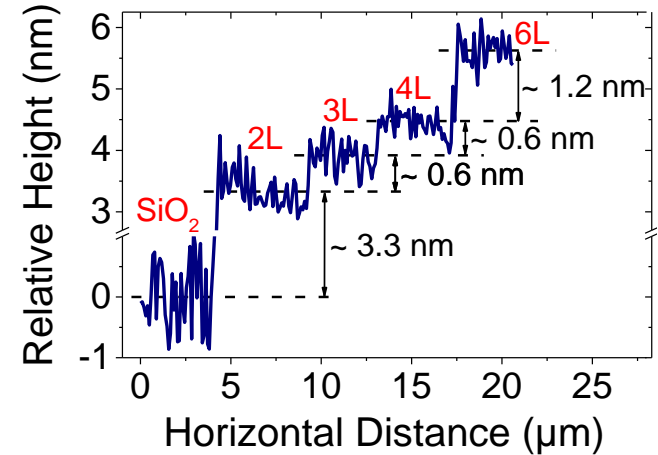
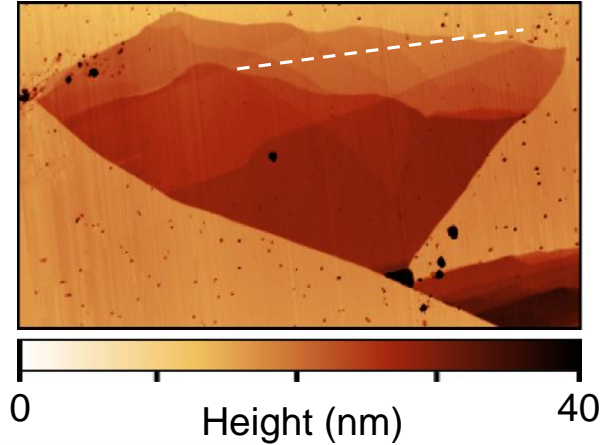
- M. Grzeszczyk *et al.*, 2D Materials **3**, 25010 (2016) (MoTe₂)
- Q. J. Song *et al.*, PRB **93**, 115409 (2016) (MoTe₂)
- K. Kim *et al.*, ACS Nano **10**, 8113 (2016) (MoSe₂)

Hyperspectral Imaging of N -layer MoTe_2

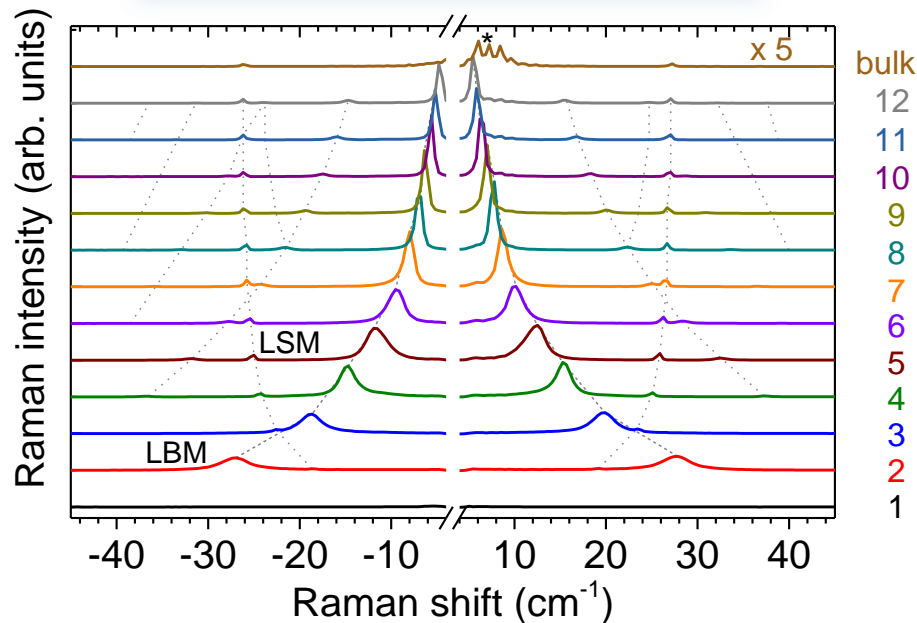
Optical image



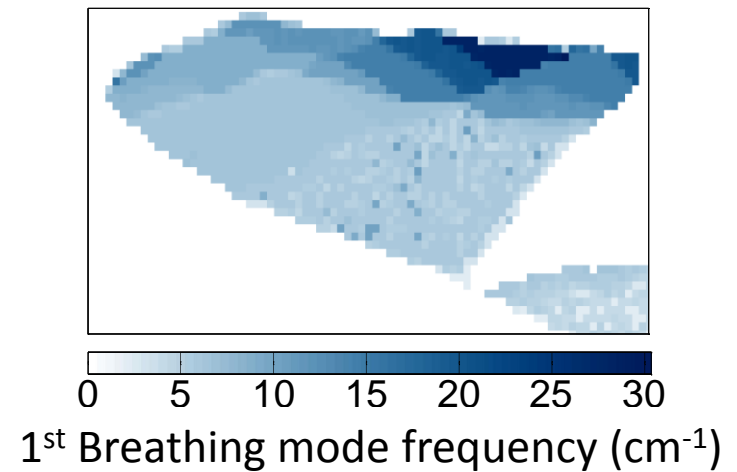
AFM image



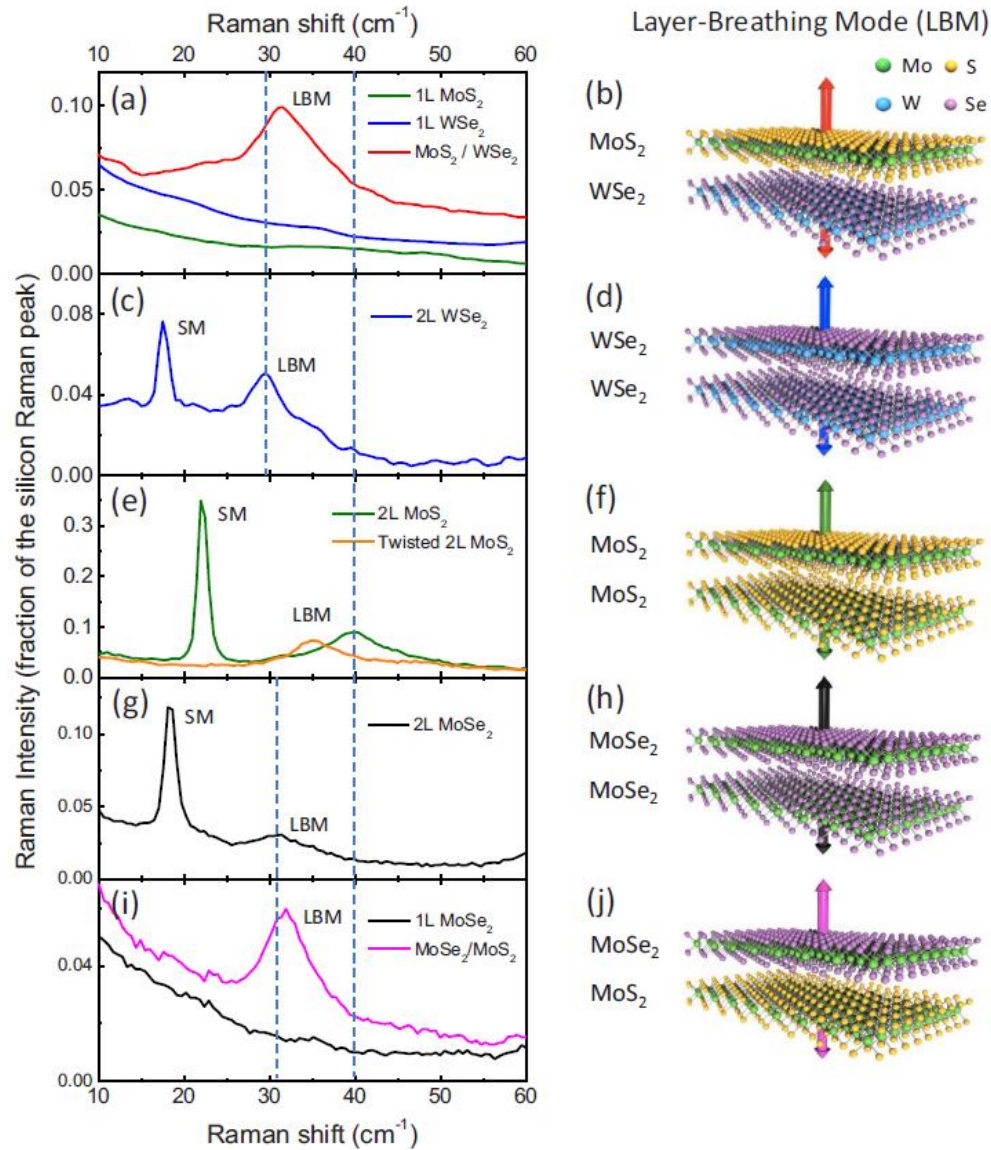
Low Frequency Interlayer Modes



Hyperspectral Raman map

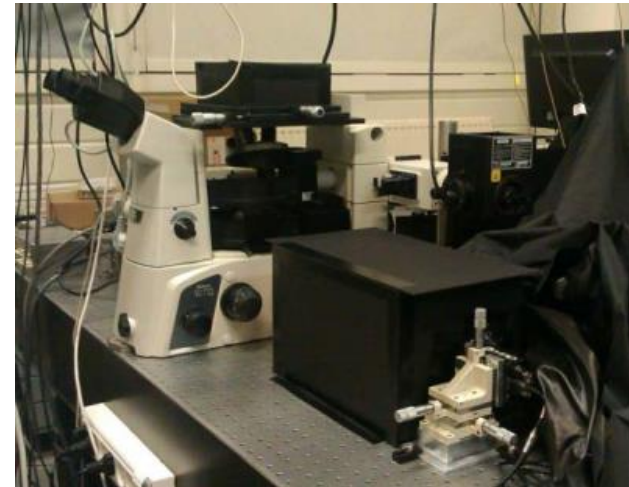
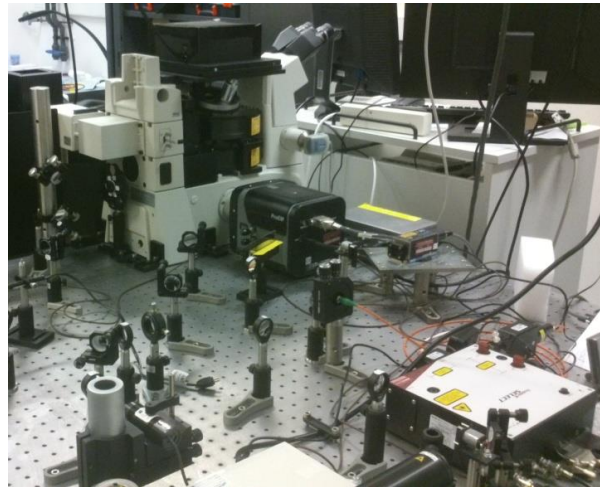
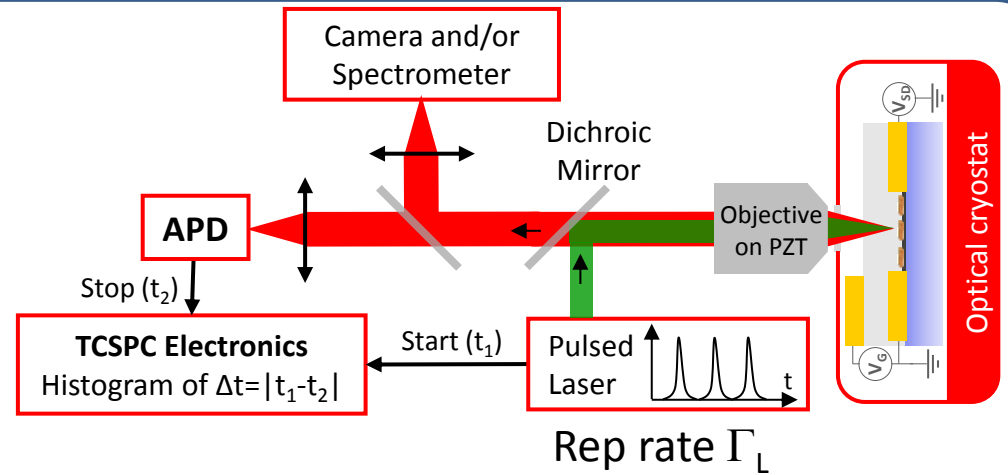


Interlayer modes in van der Waals Heterostructures



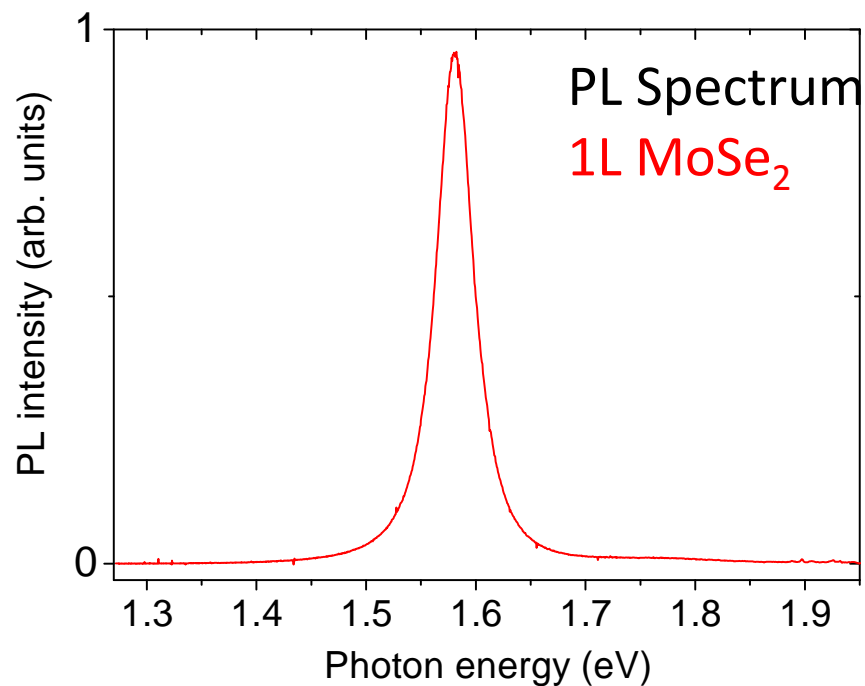
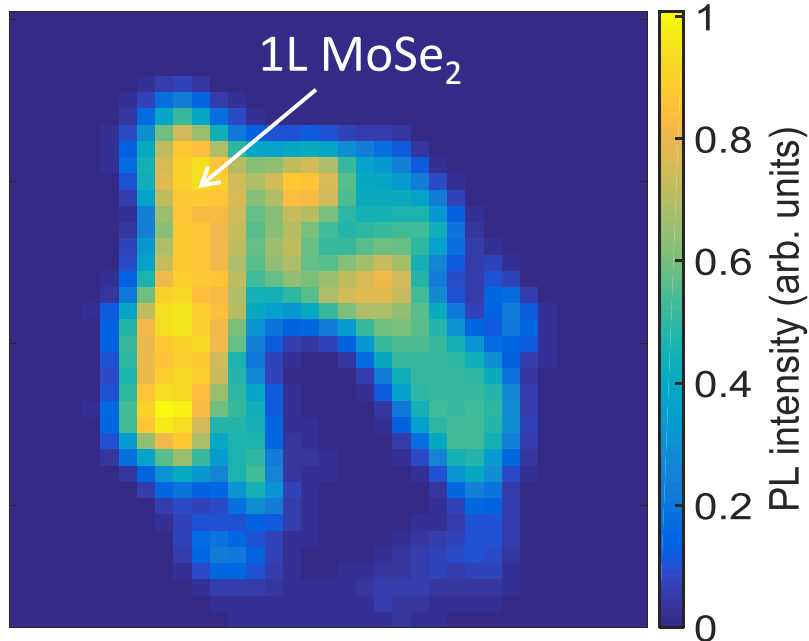
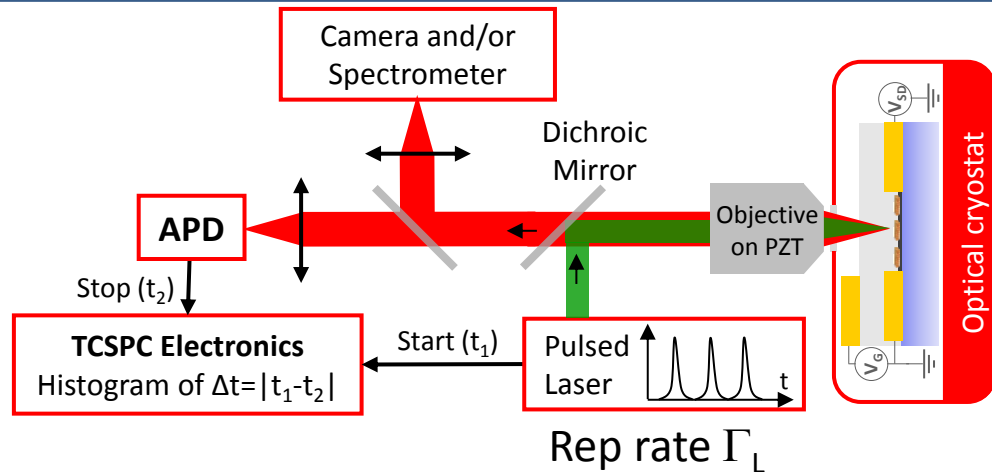
(Time resolved) photoluminescence

- Tunable pulsed laser
pulse width : 100 fs \rightarrow 70 ps
rep.rate 100 kHz \rightarrow 80 MHz)
- Fast avalanche photodiode
(resolution \approx 50 ps)
- Photon counting board



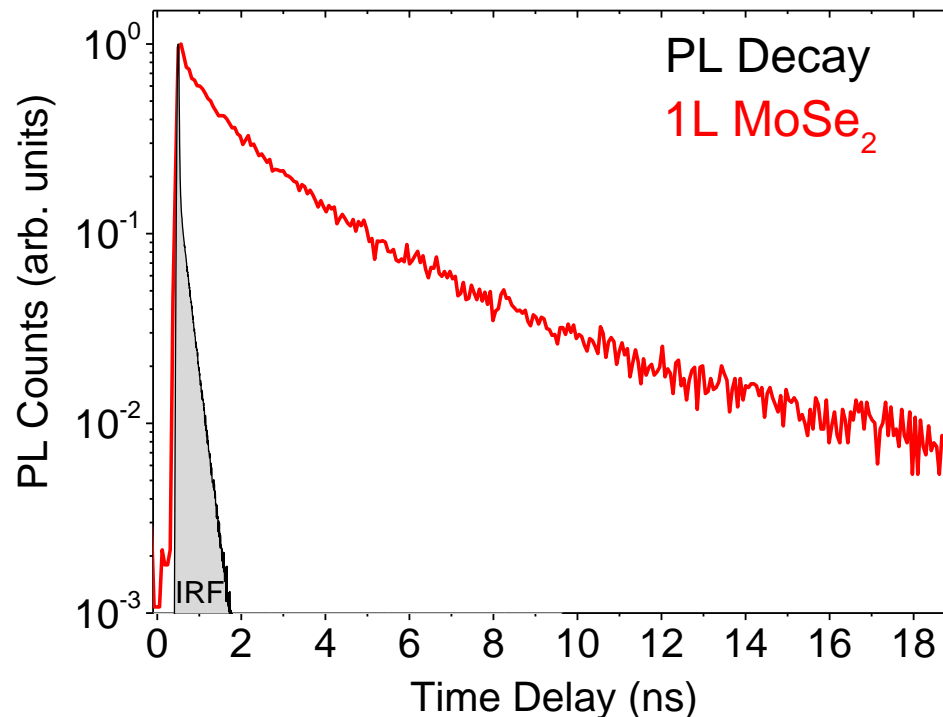
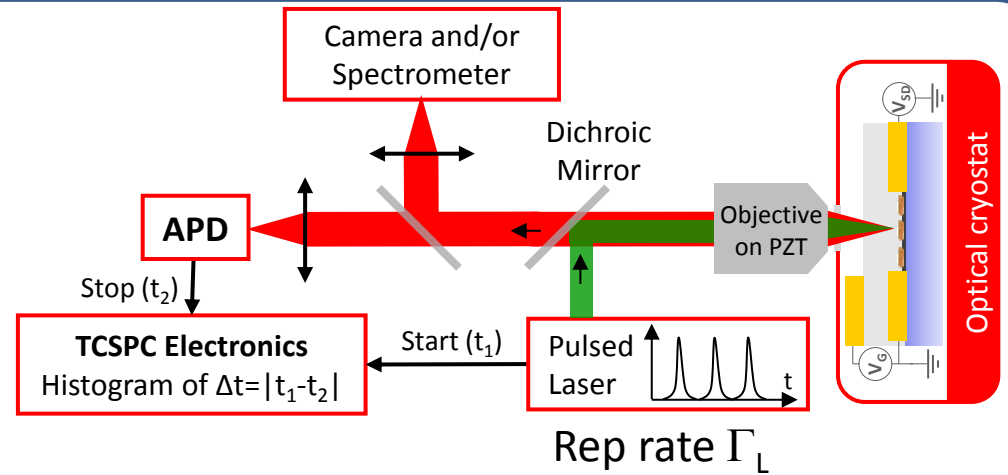
(Time resolved) photoluminescence

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(Time resolved) photoluminescence

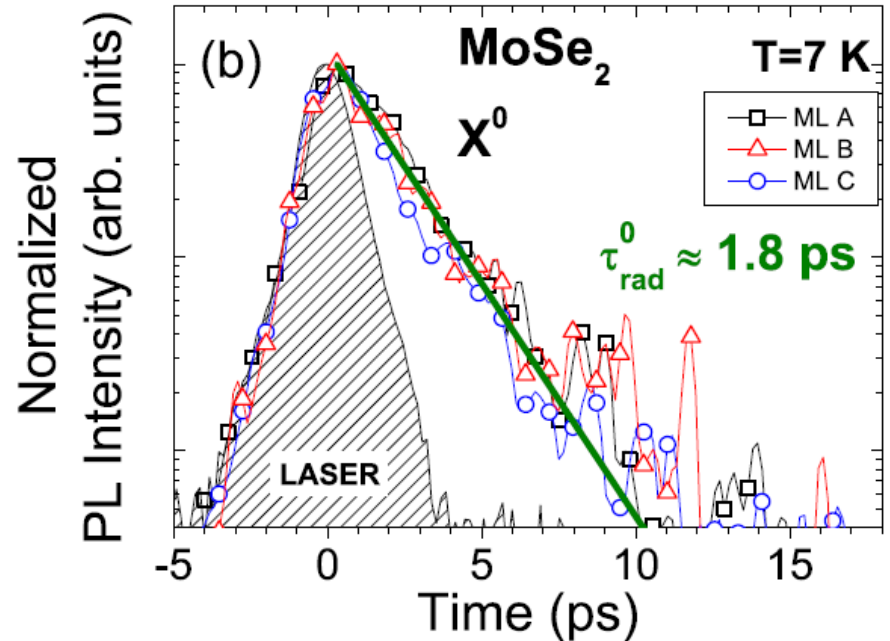
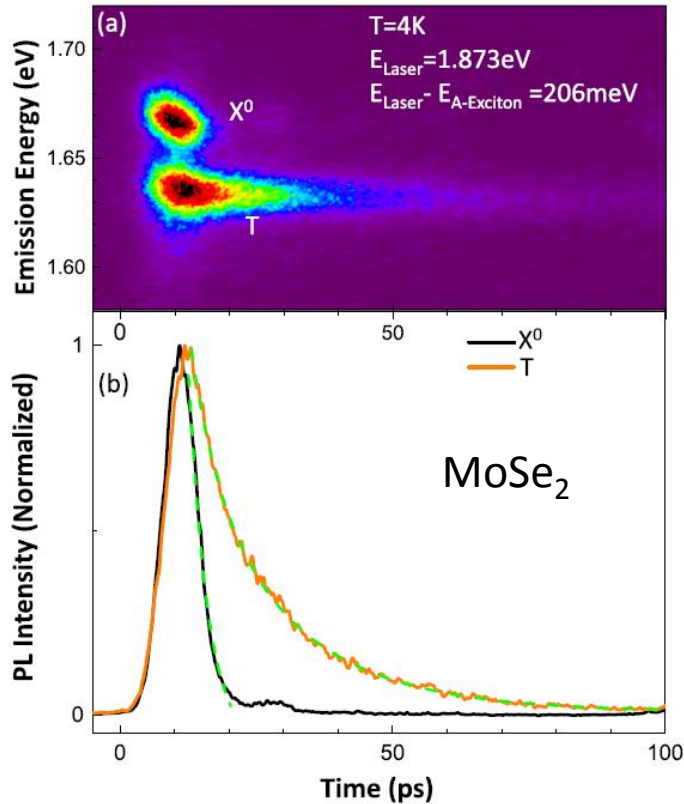
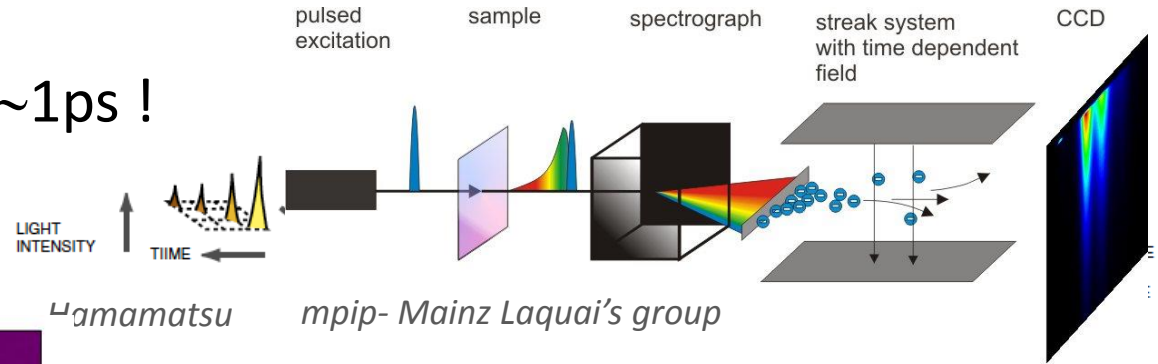
- Tunable pulsed laser
pulse width : 100 fs \rightarrow 70 ps
rep.rate 100 kHz \rightarrow 80 MHz)
- Fast avalanche photodiode
(resolution \approx 50 ps)
- Photon counting board



Streak Camera: an optical oscilloscope

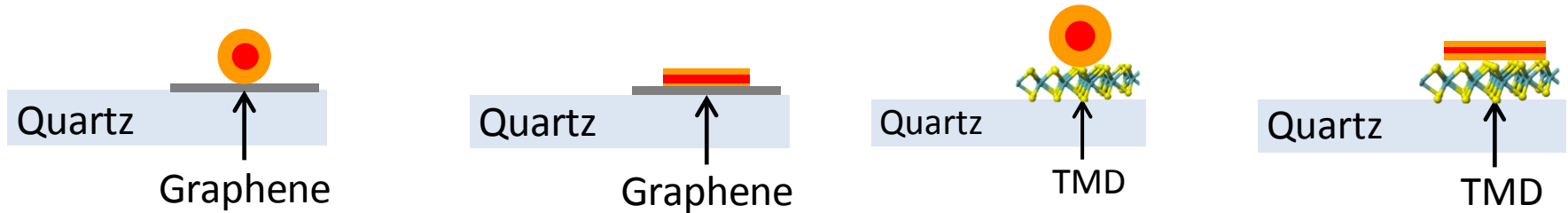
Spectroscopy + TRPL

Time resolution down to ~ 1 ps !



Outline

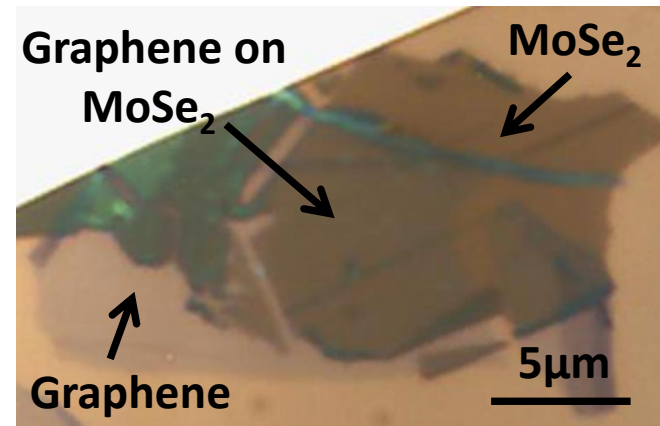
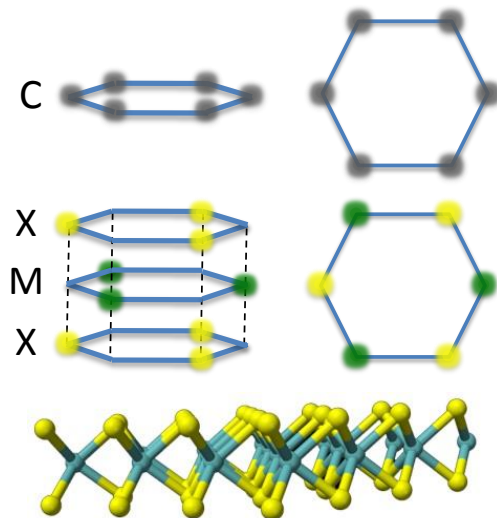
- *Near-field coupling in hybrid heterostructures*



- ✓ Distance dependence
- ✓ Dimensionality effects

- ✓ Dielectric screening
- ✓ Electrical control

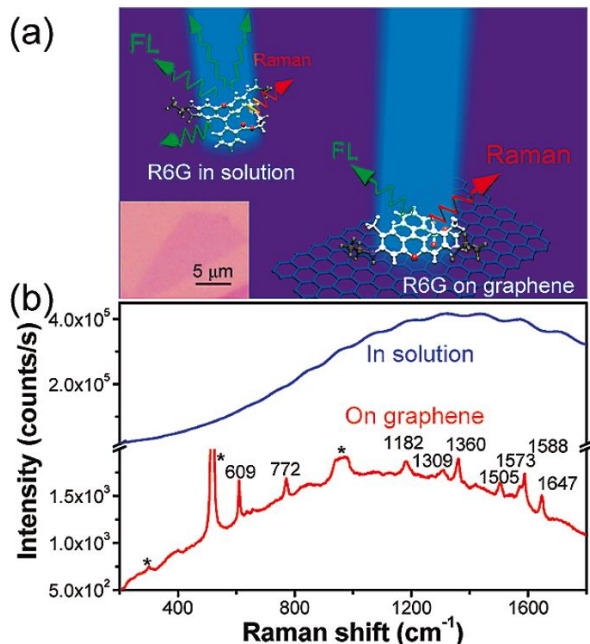
- *Charge and energy transfer in van der Waals heterostructures*



Nano-emitter graphene FRET

Useful for Raman studies

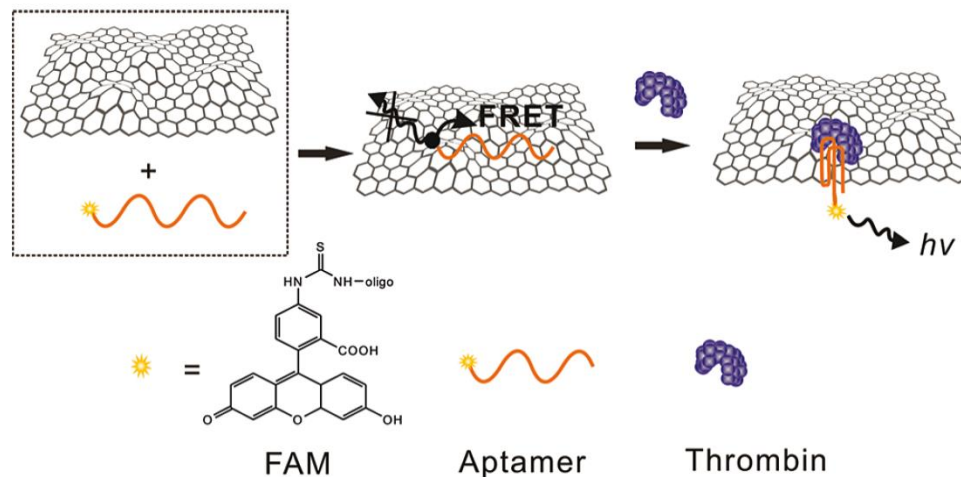
Xie *et al.*, JACS 2009



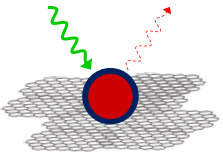
Aptasensors

Chang *et al.* Anal Chem 2010

Scheme 1. Schematic Demonstration of Graphene FRET Aptasensor and the Detection Mechanism for Thrombin^a

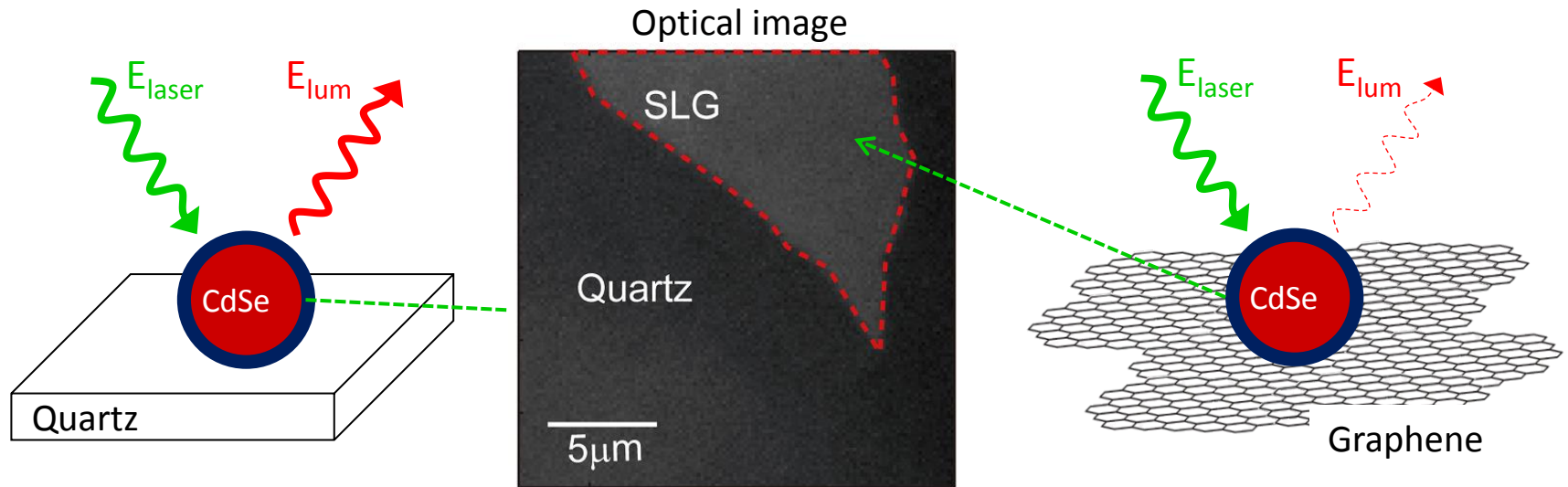


- First theoretical studies: Swathi and Sebastian J. Chem. Phys. 2008 & 2009
- ✓ Single particle studies ?
- ✓ Distance dependence ? Dimensionality effects ?
- ✓ Electrical control ?

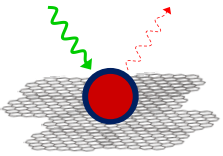


Energy transfer between individual nanocrystals and graphene

- Core/shell nanocrystals on graphene : wide field fluorescence microscopy
- “Proof of concept” experiment: evidence for efficient energy transfer

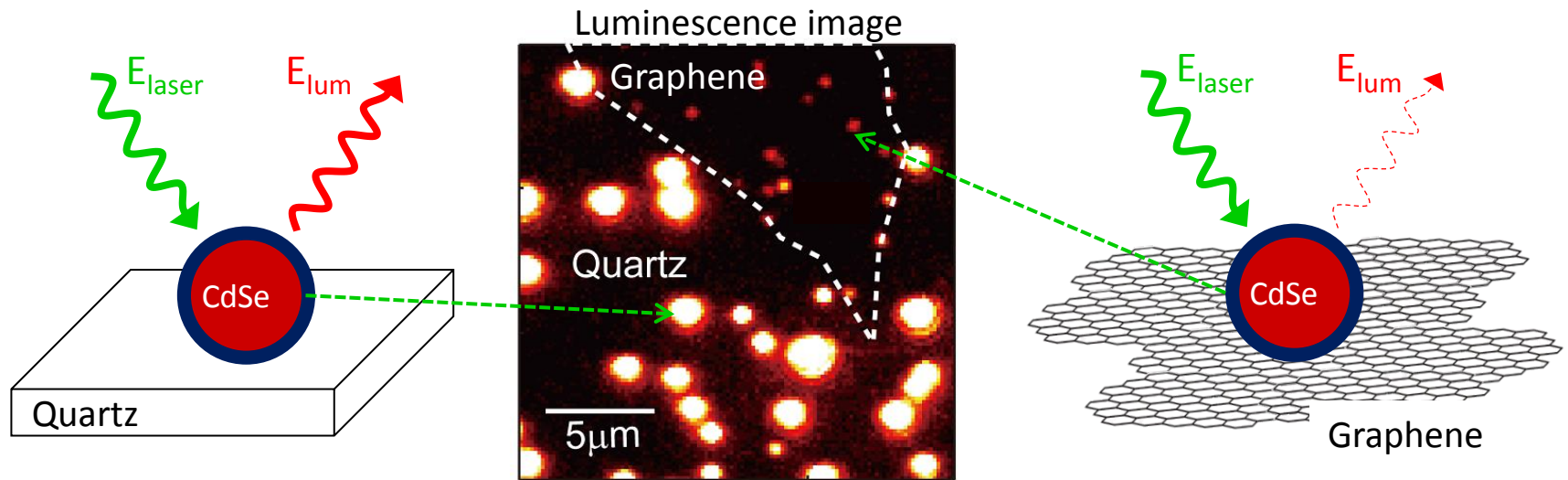


Z. Chen, S. Berciaud *et al.* ACS Nano (2010)

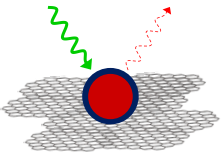


Energy transfer between individual nanocrystals and graphene

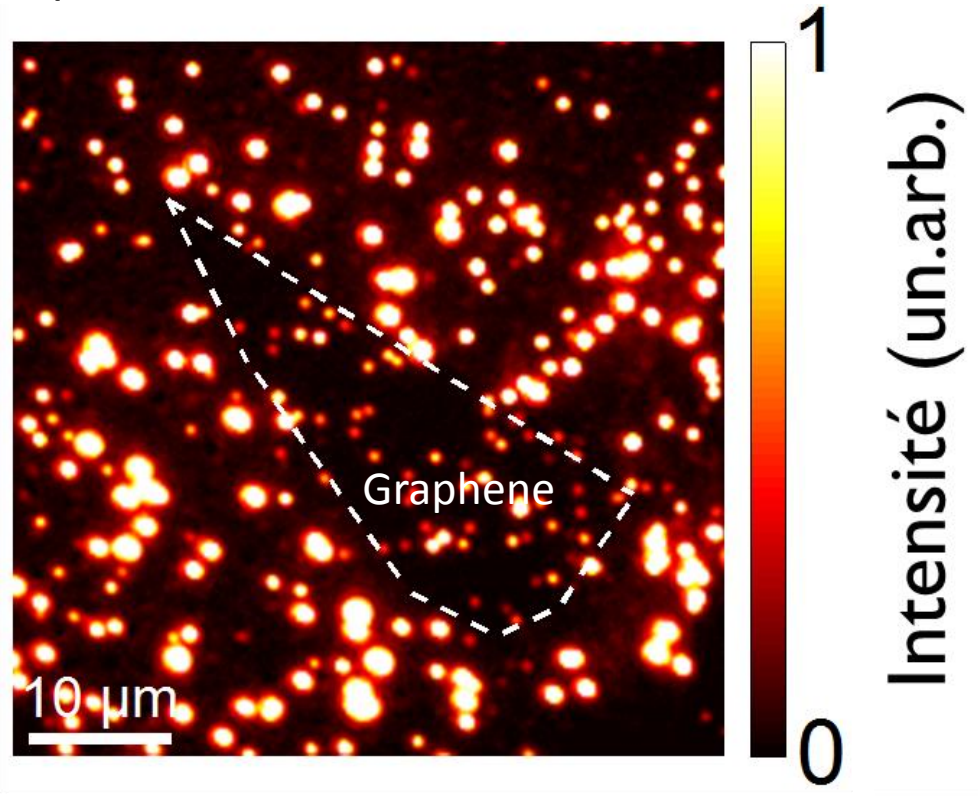
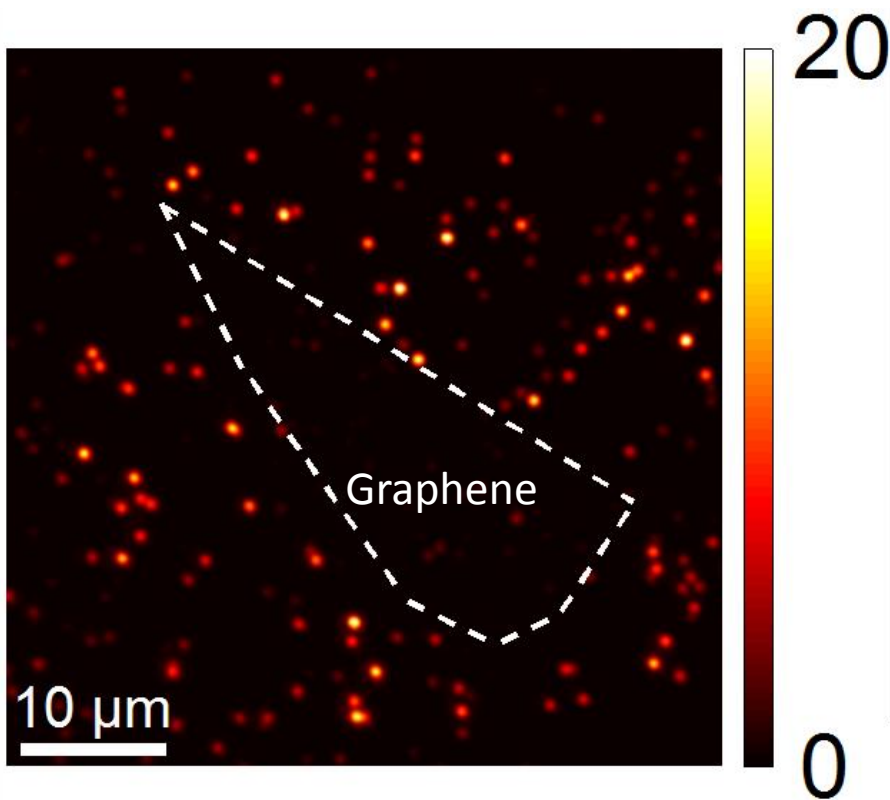
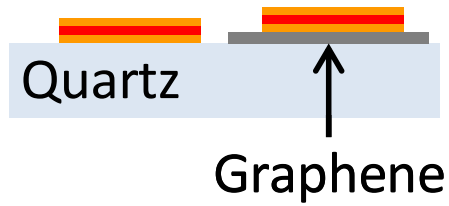
- Core/shell nanocrystals on graphene : wide field fluorescence microscopy
- “Proof of concept” experiment: evidence for efficient energy transfer

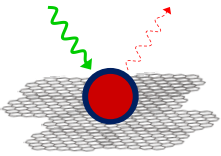


Z. Chen, S. Berciaud *et al.* ACS Nano (2010)

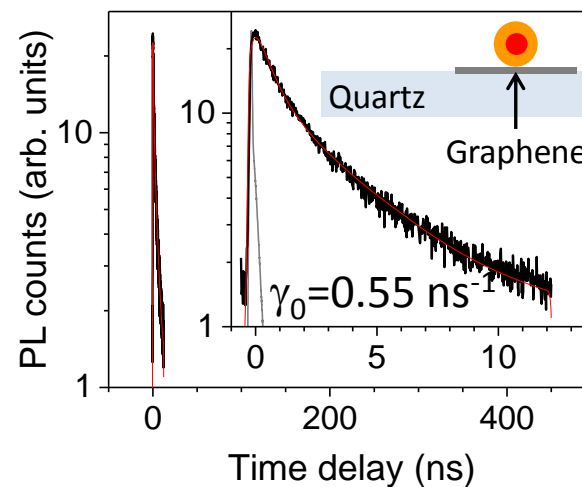
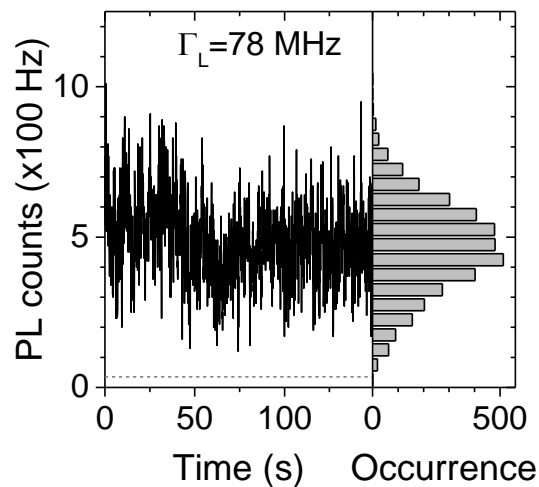
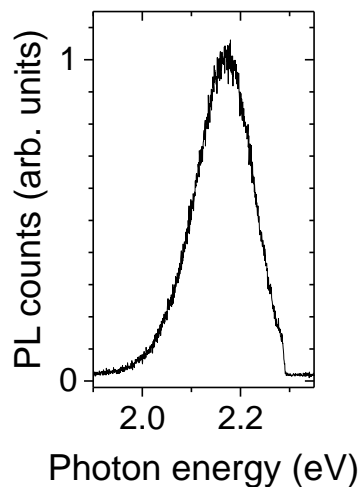
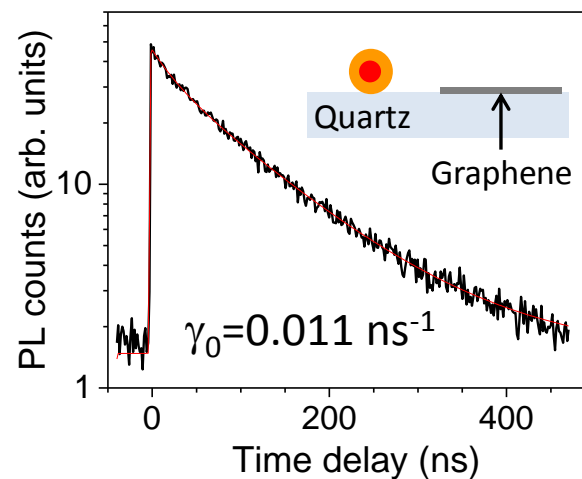
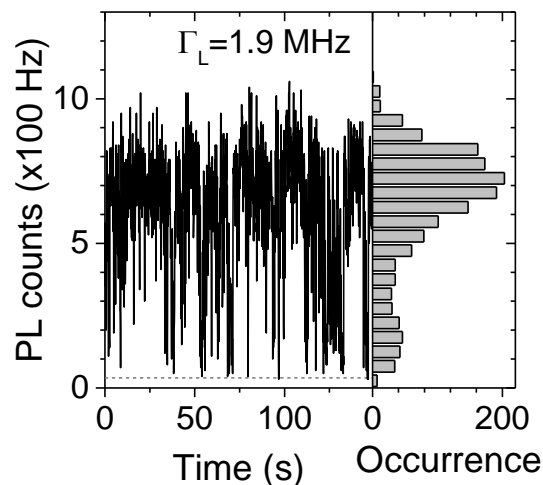
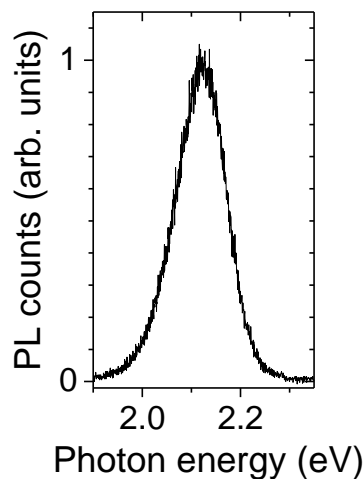


Energy transfer between individual nanocrystals and graphene





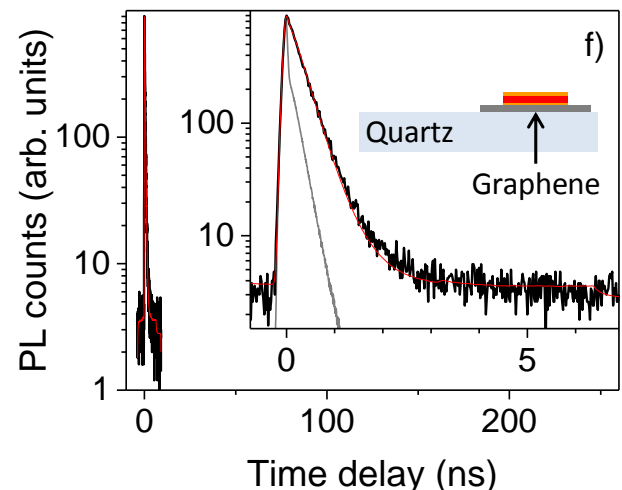
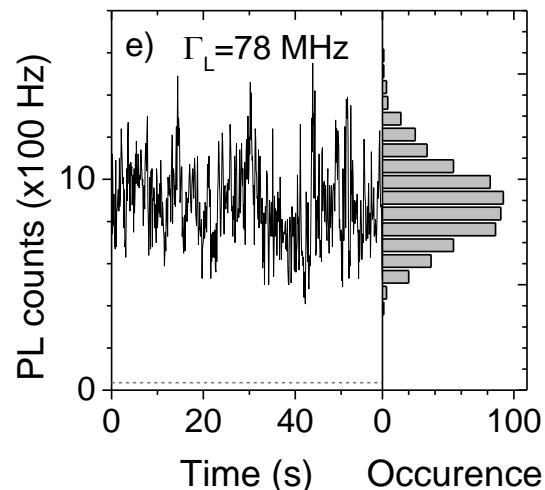
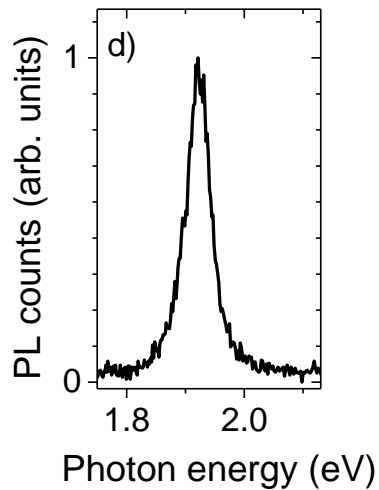
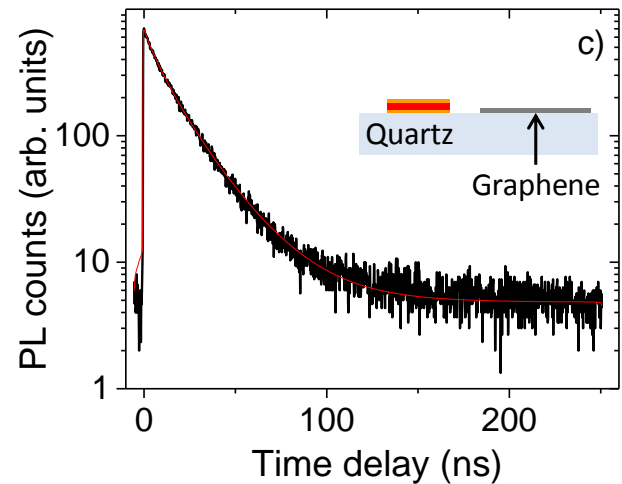
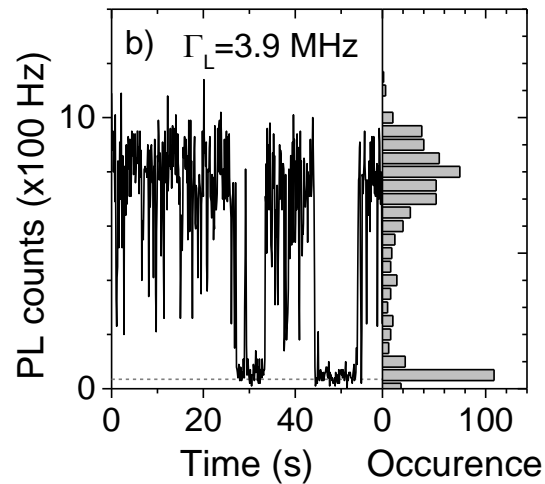
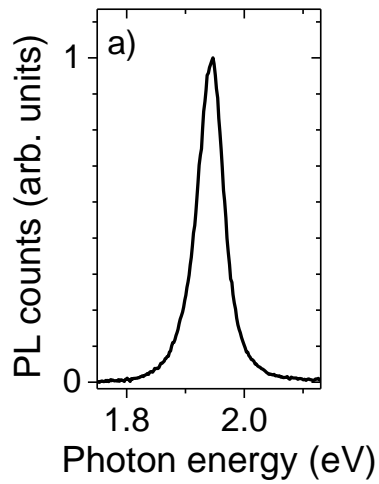
Energy transfer between individual **nanocrystals** and graphene



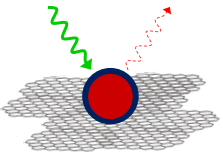
- Much faster decay on graphene and Reduced photoinduced blinking
- Energy transfer efficiency > 95%

Quartz ↑ Graphene

Energy transfer between individual **nanoplatelets** and graphene

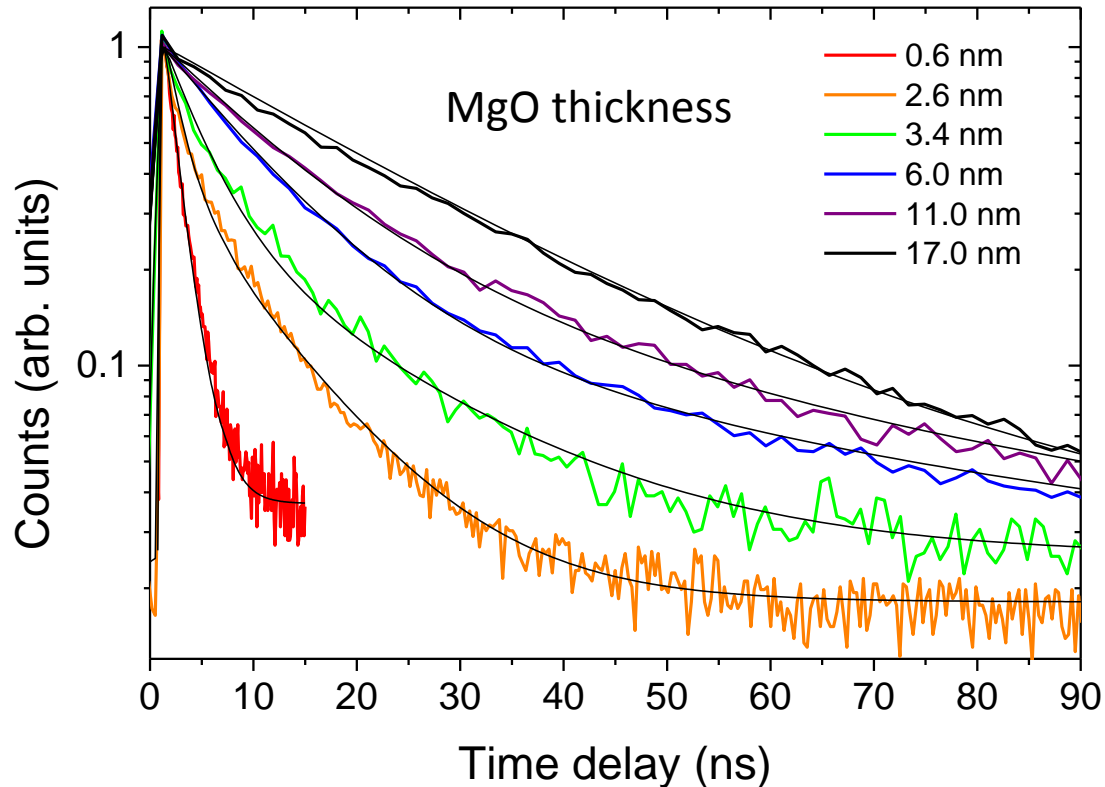
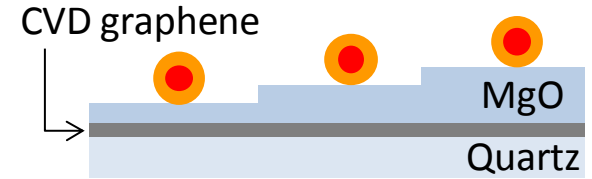


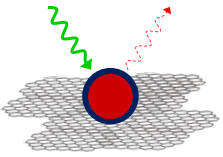
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Distance scaling of the energy transfer rate

- Mechanically exfoliated graphene monolayers on quartz
- CdSe/CdS nanocrystals (B. Dubertret, ESPCI)
- Smooth MgO films grown by MBE (D. Halley, IPCMS)
- Characterization by Raman spectroscopy and AFM





Distance scaling of the energy transfer rate

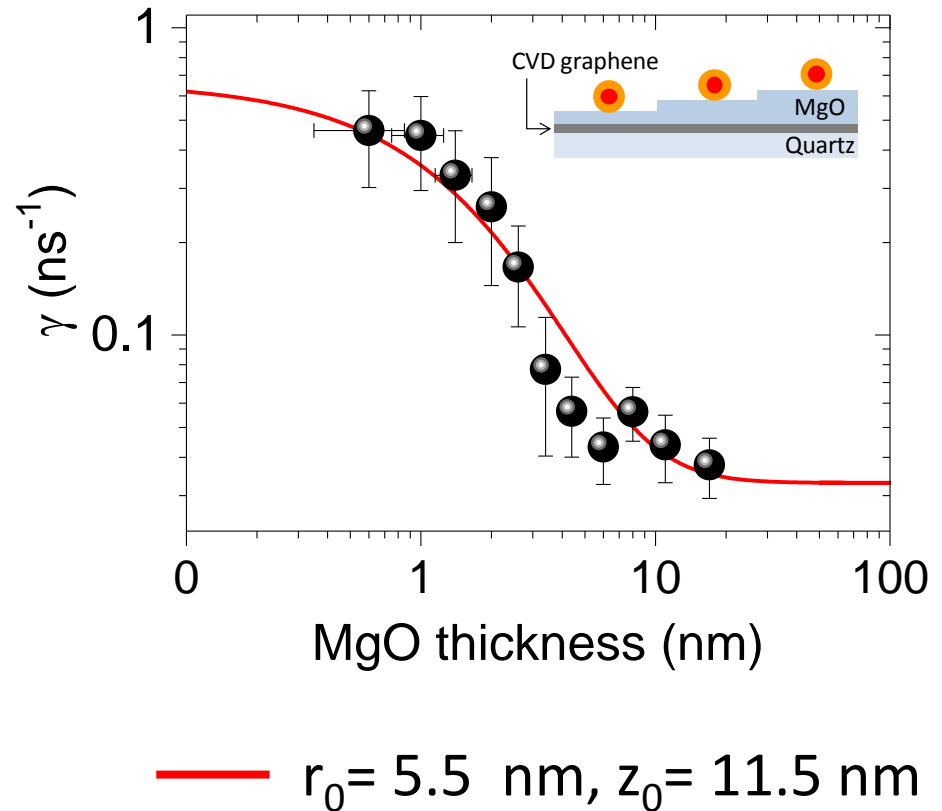
0D-2D Förster Energy Transfer*

$$\gamma = \gamma_0 \left[1 + \left(\frac{z_0}{z + r_0} \right)^4 \right]$$

$$r_0 \text{ (TEM)} = 4.75 \pm 1 \text{ nm}$$
$$z_0 \text{ (theory)} \sim 12 \text{ nm}$$

$$N_{em} = \frac{\gamma_0}{\gamma} N_{abs}$$

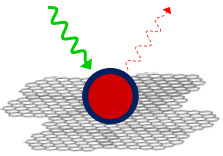
$$\Rightarrow N_{em} \gamma = \text{const.}$$



Demonstration of a graphene-based molecular ruler (1/d⁴ scaling)

*Kühn J. Chem Phys 1970
Chance, Prock, Silbey Adv. Chem. Phys. **37** 65 (1978)

F. Federspiel *et al.* Nano Letters **15**, 1252 (2015)



Distance scaling of the energy transfer rate

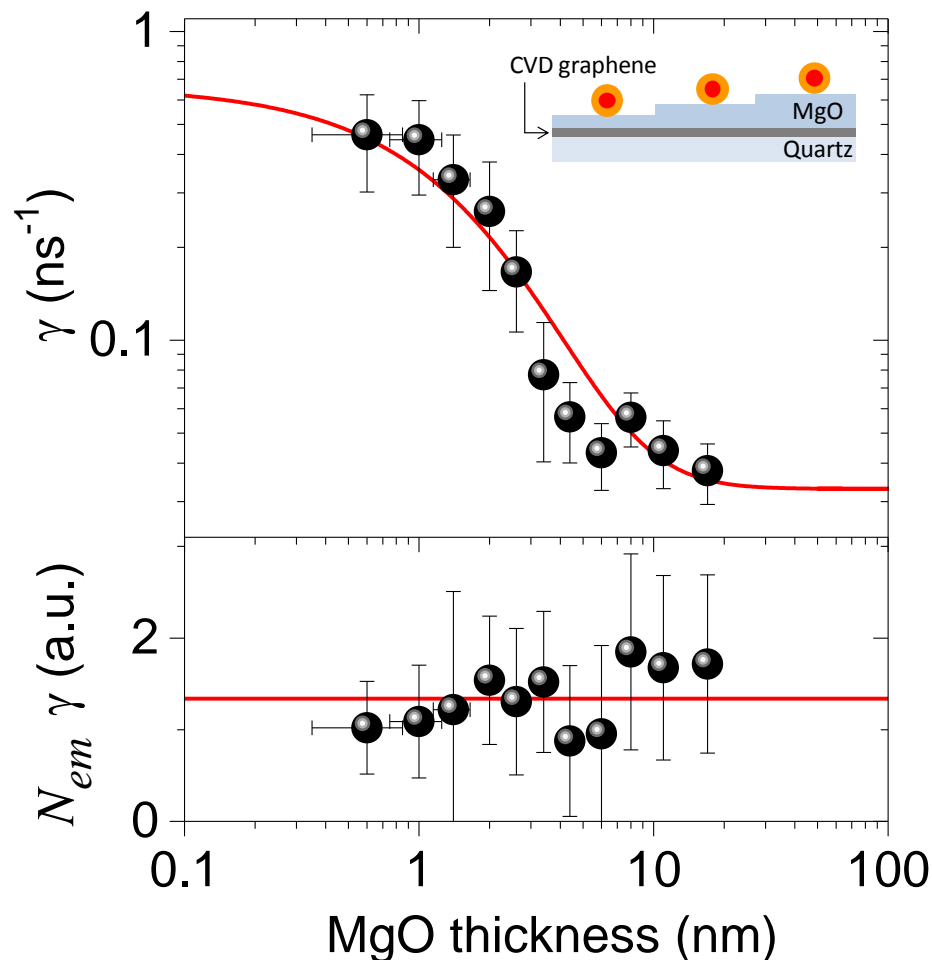
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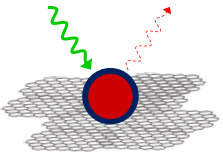
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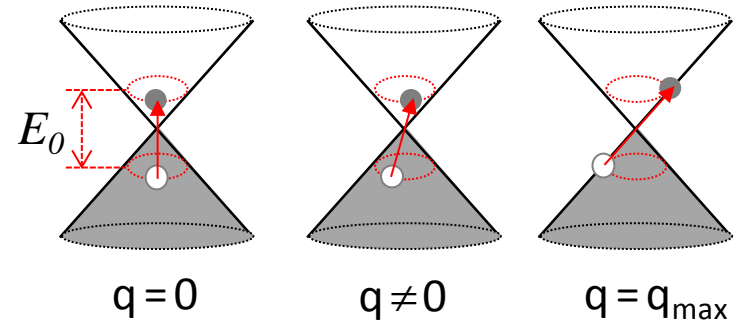
Dimensionality matters: platelets vs. dots

0D - Graphene

$$\gamma_T \propto \int_0^{q_{max}} dq \frac{q^3 e^{-2qd}}{\sqrt{q_{max}^2 - q^2}}$$

$$q_{max} = \frac{E_0}{\hbar v_F}$$

For $d \gg 1/q_{max} \approx 0.3 \text{ nm} \rightarrow \gamma_T \propto \frac{1}{d^4}$

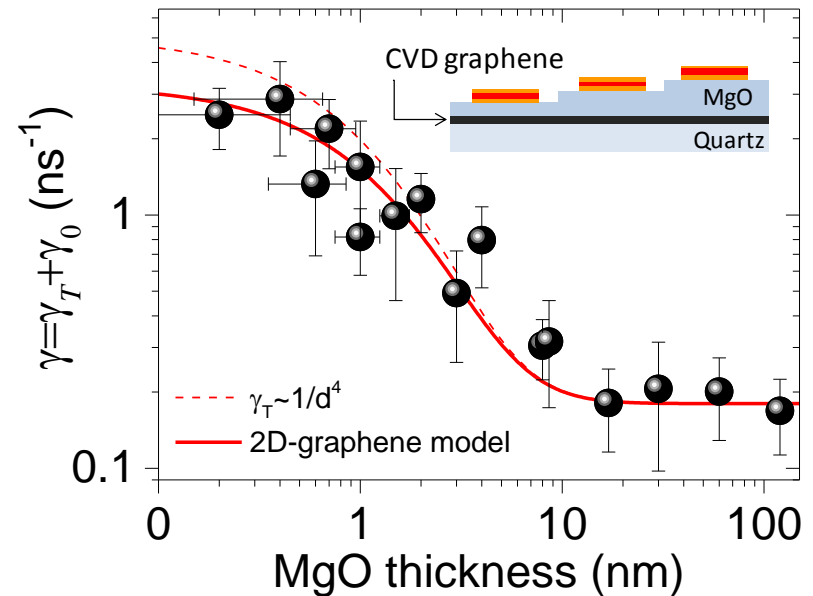


2D - Graphene

$$\Lambda = \frac{h}{\sqrt{2m_x k_B T}} \approx 7.5 \text{ nm} \quad d \gg 1/q_{max}$$

$L_x, L_y > \Lambda$ and $L_z \ll d$

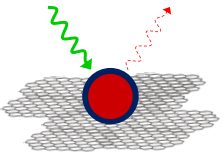
$$\gamma_T \propto \int_0^\infty dq q^3 e^{-2qd} e^{-\left(\frac{\Lambda q}{2\pi}\right)^2}$$



Swathi & Sebastian JCP 2008 & 2009
 Gomez-Santos & Stauber PRB 2011
 Gaudreau *et al.* Nano Lett 2013

D. M. Basko *et al.* EPJB 1999
 Kos *et al.* PRB 2005

F. Federspiel *et al.* Nano Letters 15, 1252 (2015)
 see also arXiv:1501.03401



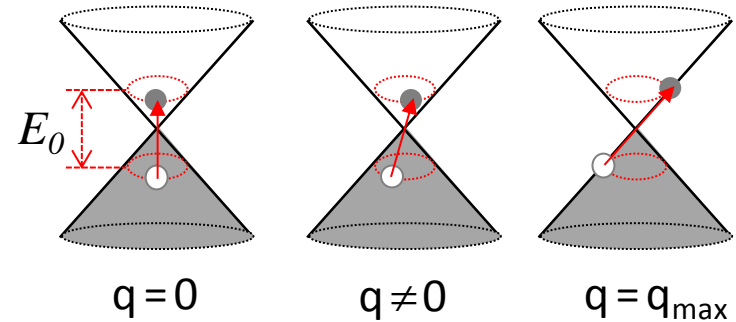
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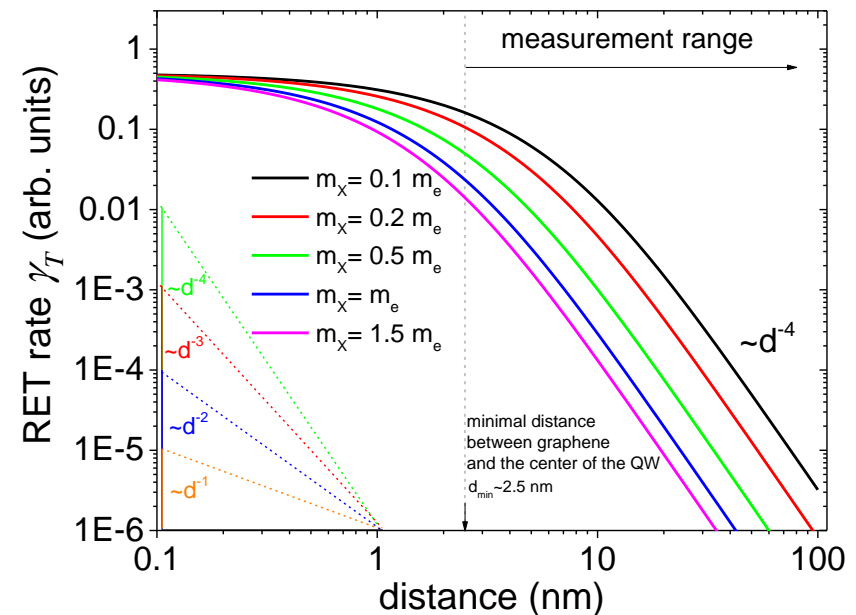


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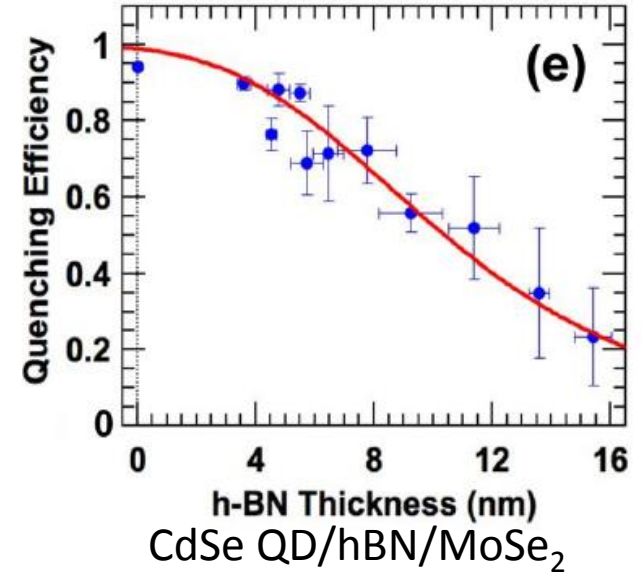
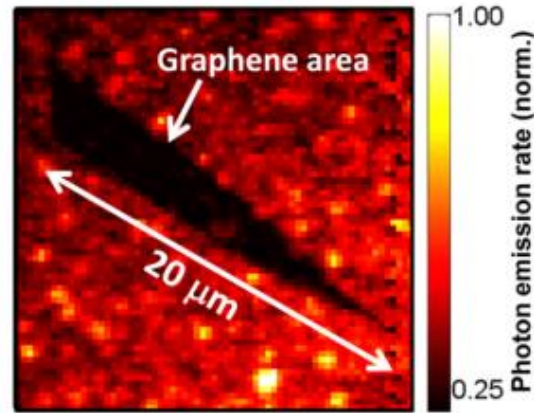
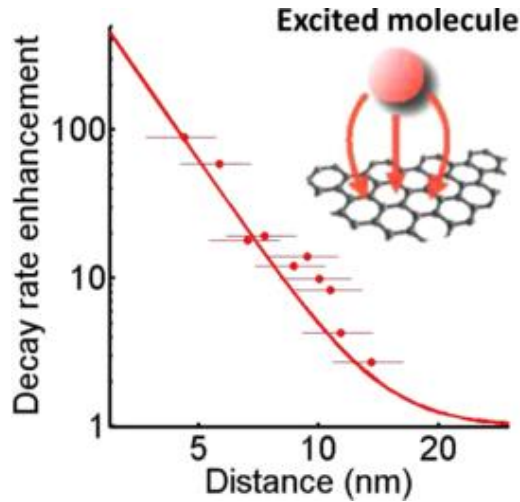


Swathi & Sebastian JCP 2008 & 2009
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 Gaudreau *et al.* Nano Lett 2013

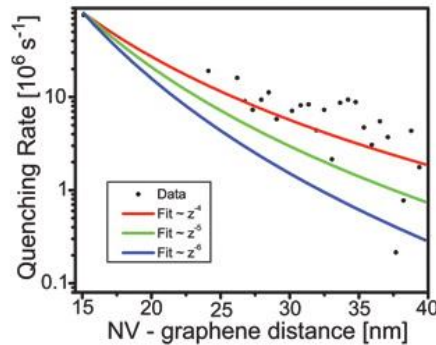
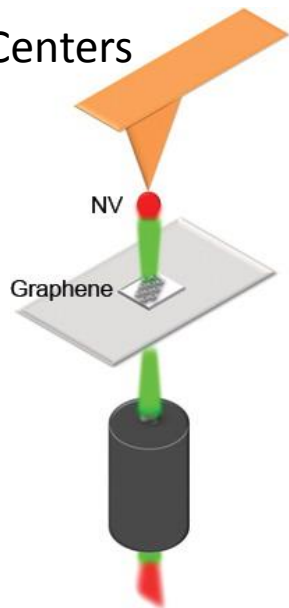
D. M. Basko *et al.* EPJB 1999
 Kos *et al.* PRB 2005

F. Federspiel *et al.* Nano Letters 15, 1252 (2015)
 see also arXiv:1501.03401

Related Results with other materials



NV Centers



Distance dependence of FRET to graphene
 Gaudreau *et al.* Nano Lett. **13**, 2030 (2013)
 Tisler *et al.* Nano Lett. **13**, 3152 (2013)

Single Qdots on graphene

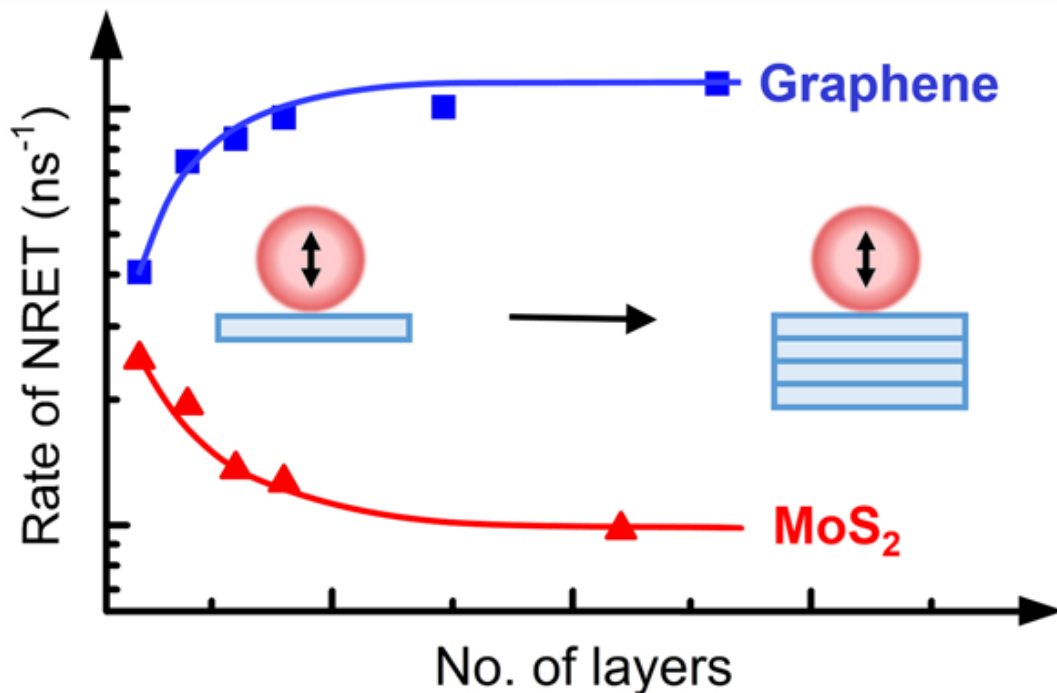
B. Rogez *et al.* JPCC 118, 18445 (2014)
 O. Ajayi *et al.* APL 104 171101 (2014)

Distance dependence of FRET to TMDs
 Goodfellow *et al.* APL 2015 (MoSe₂)

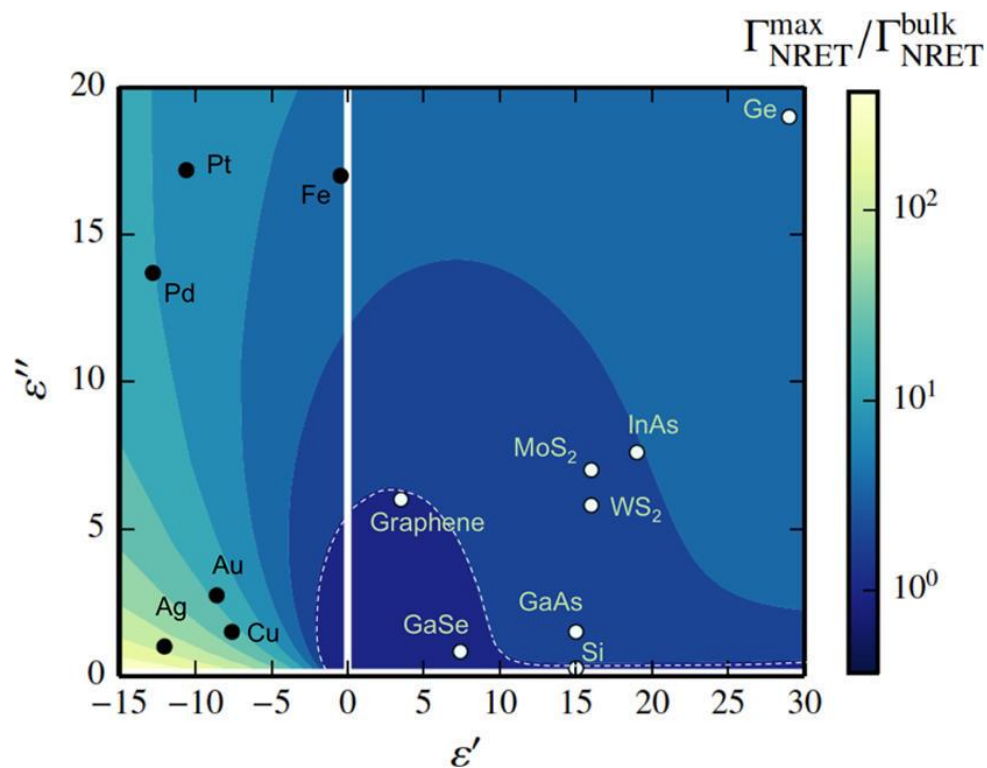
TMD vs Graphene: Dielectric screening matters (1)

$$P_{D \rightarrow A} = -\frac{1}{2} \int_{V_A} \text{Re}\{\mathbf{j}_A^* \cdot \mathbf{E}_D\} dV \approx \frac{\omega_0}{2} \text{Im}\{\alpha_A\} \left| \mathbf{n}_A \cdot \mathbf{E}_D(\mathbf{r}_A) \right|^2$$

- ✓ Imaginary part of the dielectric constant (A)
- ✓ $\mathbf{E}_D(\mathbf{r}_A)$ depends also on epsilon and its anisotropy



TMD vs Graphene: Dielectric screening matters (2)



FRET to monolayer TMD is more efficient than FRET to bulk TMD

- Dielectric screening (ϵ')
- Optical absorption (ϵ'')
- Anisotropy (ϵ_{\perp} vs $\epsilon_{//}$)



FRET Engineering

Theoretical prediction(s):

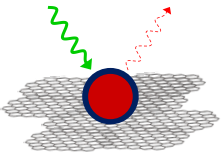
Chance, Prock, Silbey 1970's

Gordon, Gartstein J. Phys Cond. Matter 2013

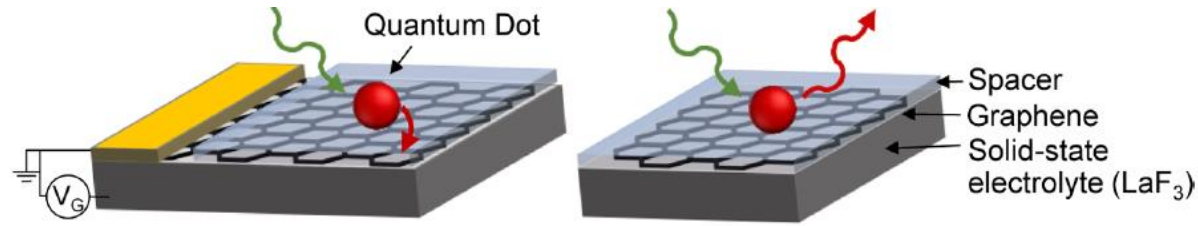
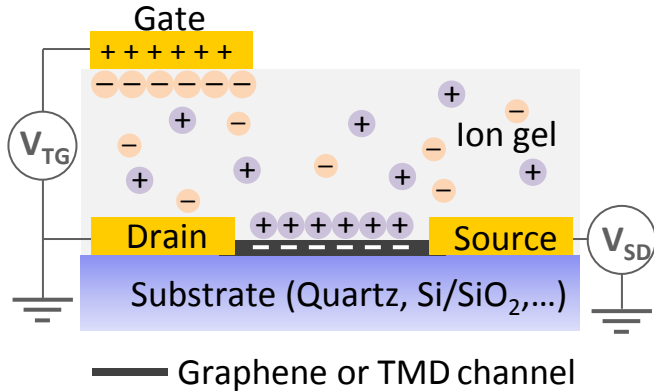
Experiments: QDs on MoS₂ layers

Prins *et al.*, Nano Letters 2014

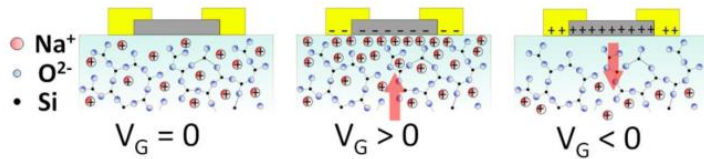
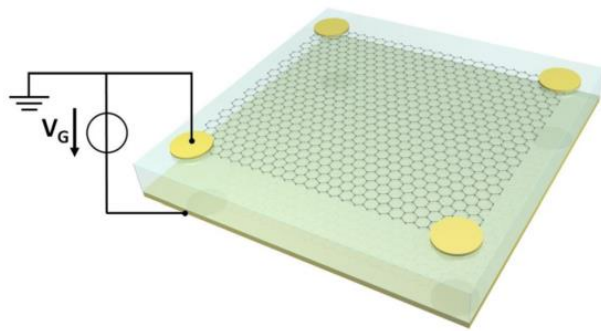
Raja *et al.*, Nano Letters 2016



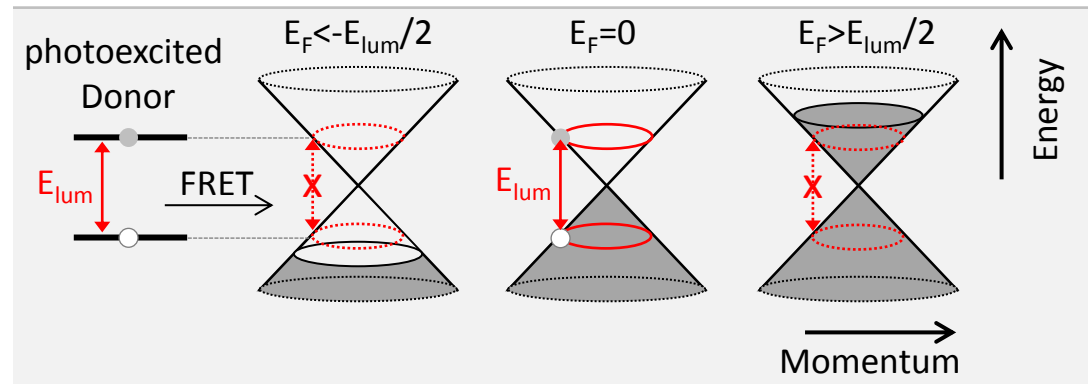
Hybrid phototransistors: electrical Control of FRET



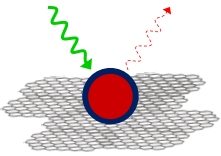
Lee *et al.* Nano Letters **14**, 7115 (2014)



Paradisi *et al.* APL 2015

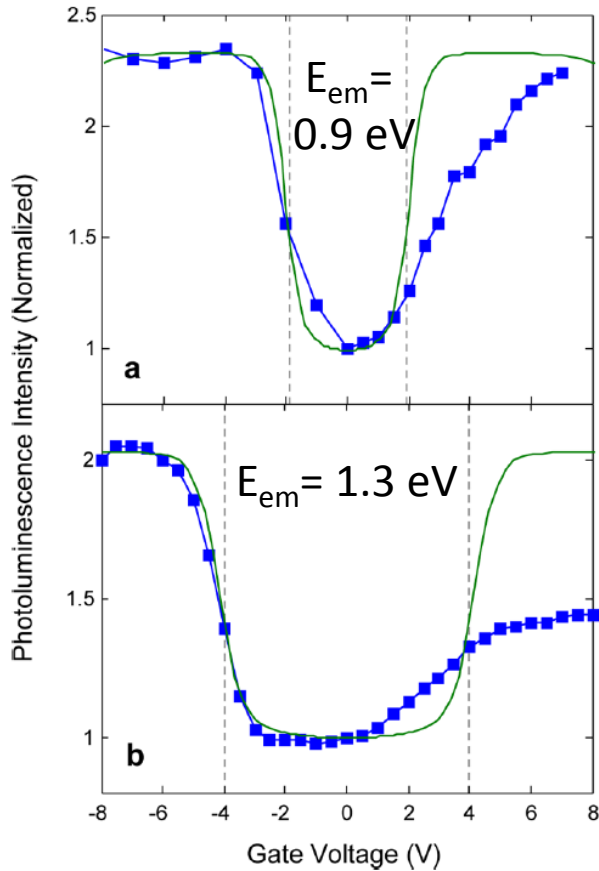
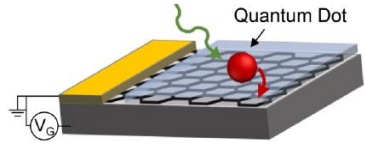


Fermi Energy shifts ~ 1 eV
Need for efficient gating methods



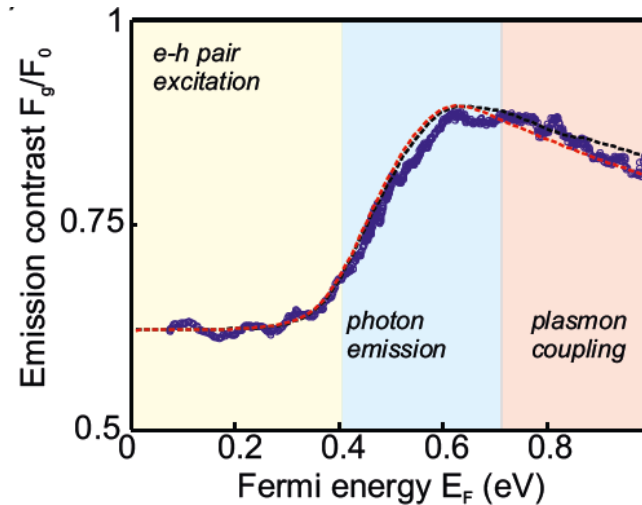
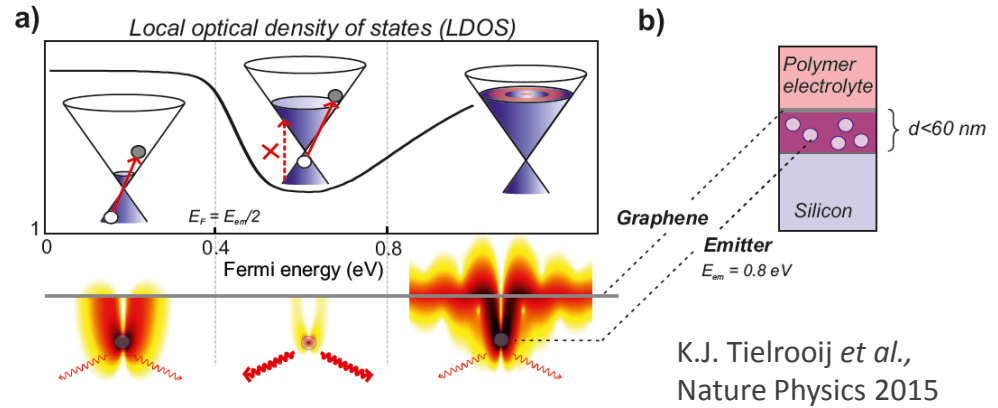
Electrical Control of FRET

PbS nanocrystals on graphene

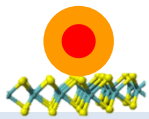


Lee *et al.* Nano Letters **14**, 7115 (2014)

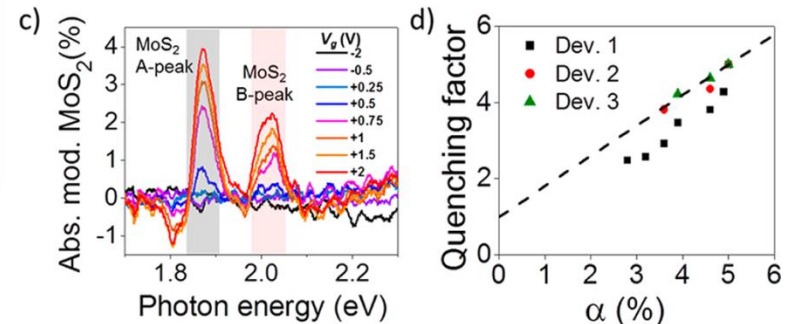
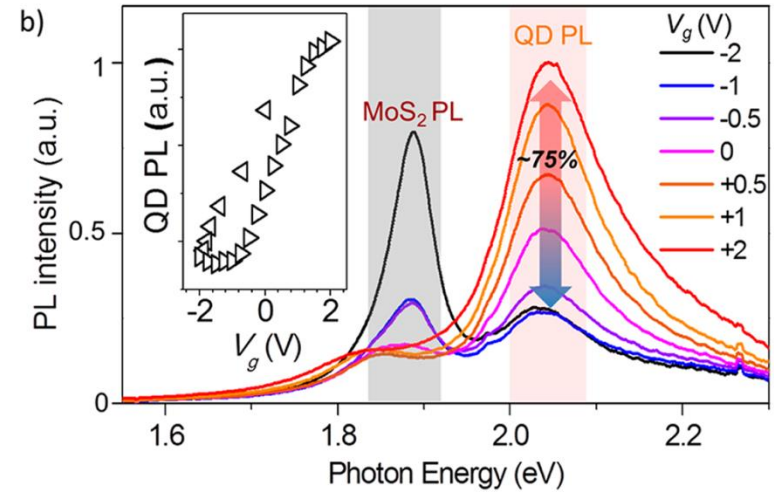
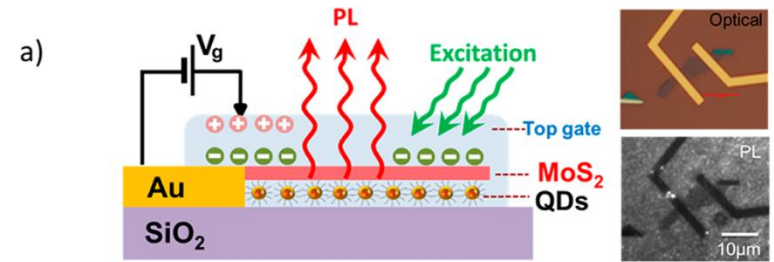
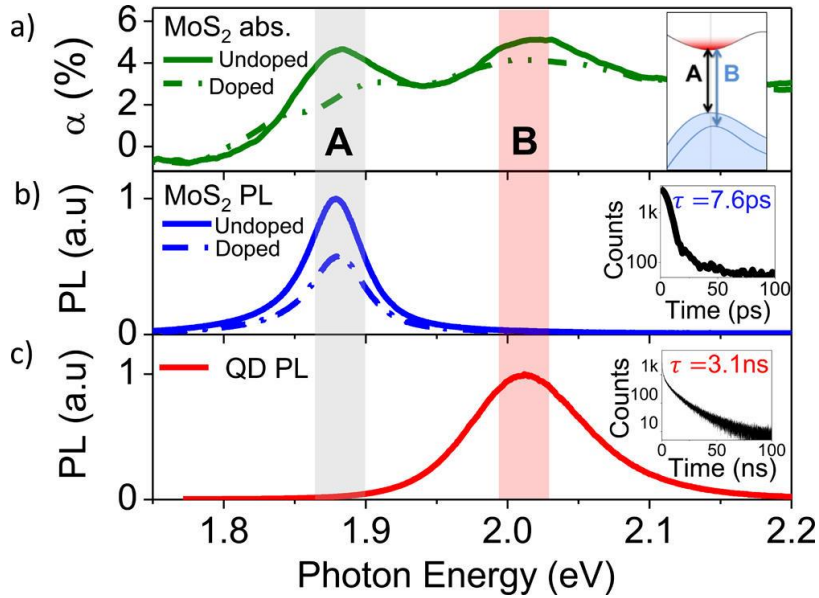
Erbium ions on graphene



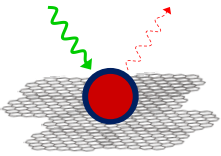
Coupling to graphene plasmons at high doping ($E_F \sim E_{em}$)



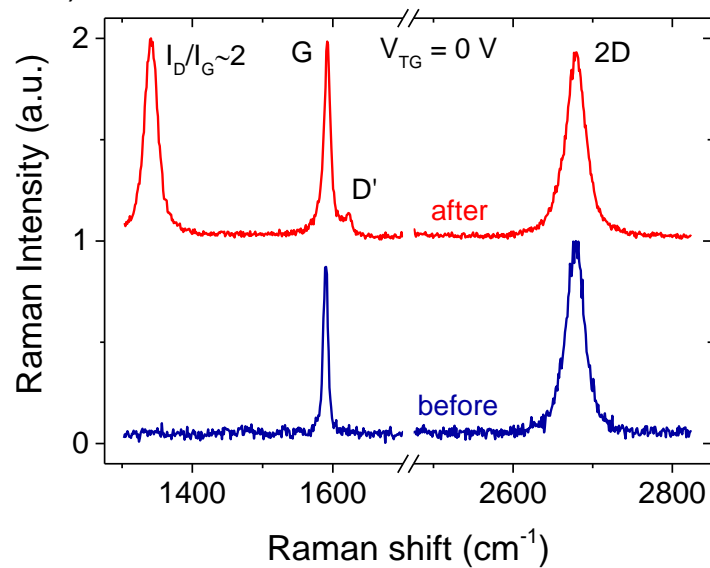
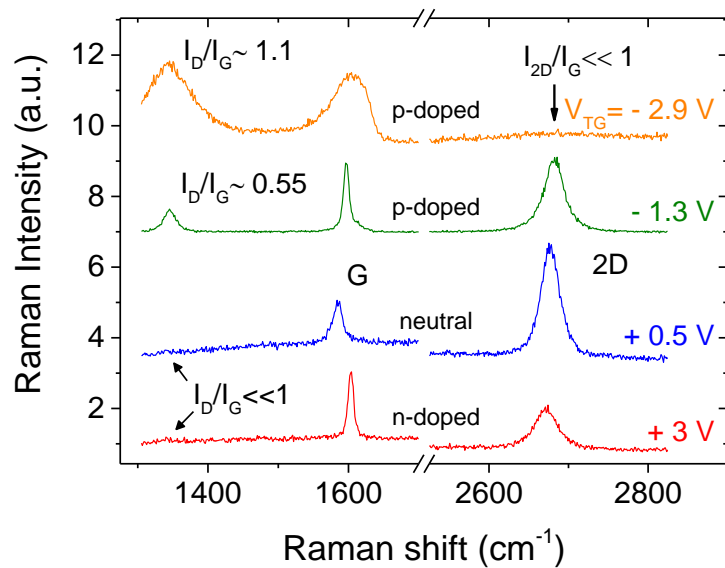
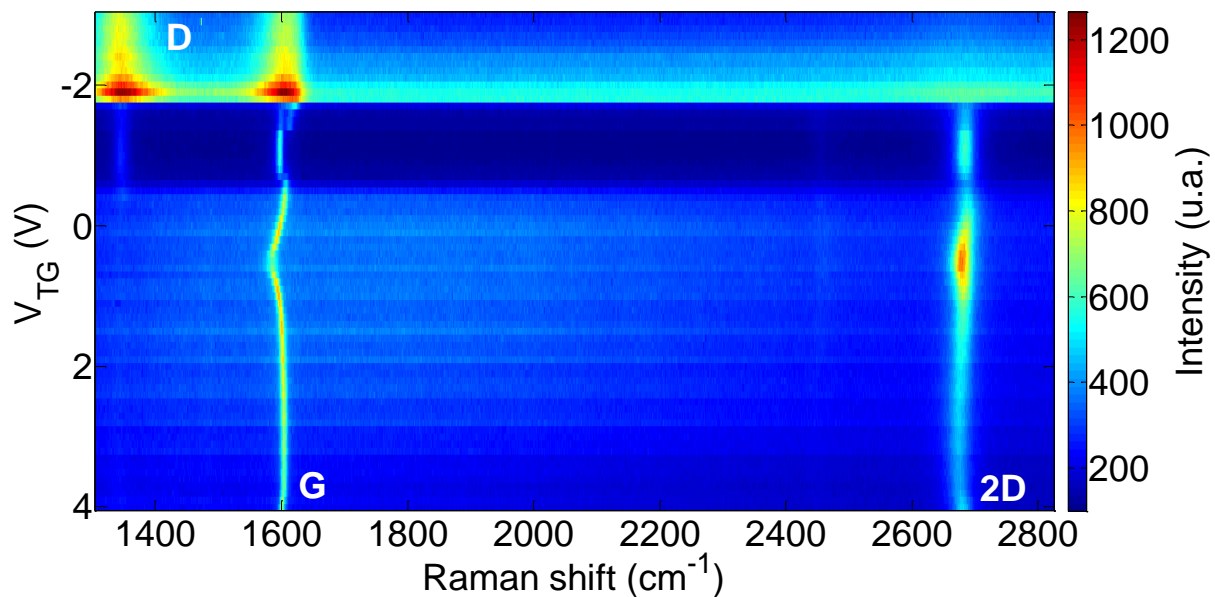
Electrical Control of FRET in QD-TMD devices

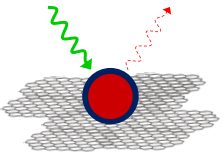


- QD PL resonant with B exciton in MoS₂
- Gate-induced absorption modulation in MoS₂
→ Gate-induced modulation of the FRET Rate



Beware of Polymer Electrolytes



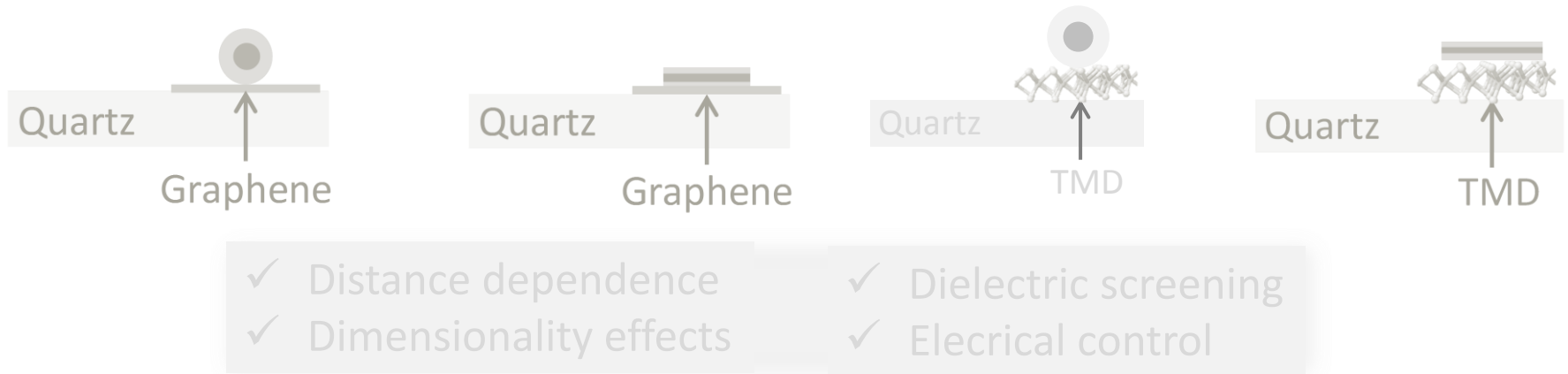


Partial conclusion

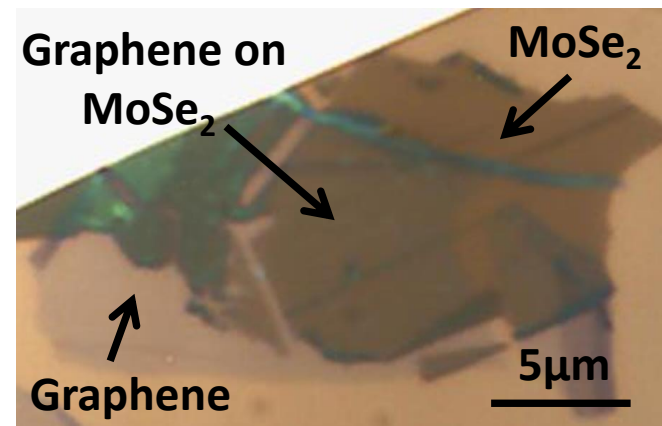
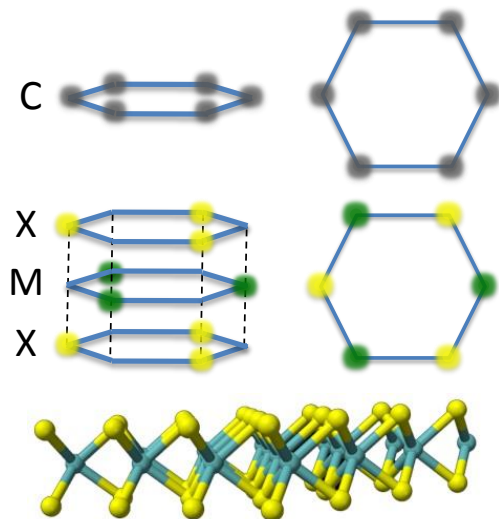
- Highly efficient « Förster-type » energy transfer (up to $\sim 95\%$)
- Graphene-based molecular ruler at the single particle level
- Important role of dimensionality
- Electrical control : PL modulation by $\sim 2x$ (graphene) up to $5x$ (MoS_2)
- Charge transfer \rightarrow Photogating in Hybrid photodetectors
- Outlook:
 - Probing exciton dimensionality with FRET?
 - Performance improvements with device engineering?

Outline

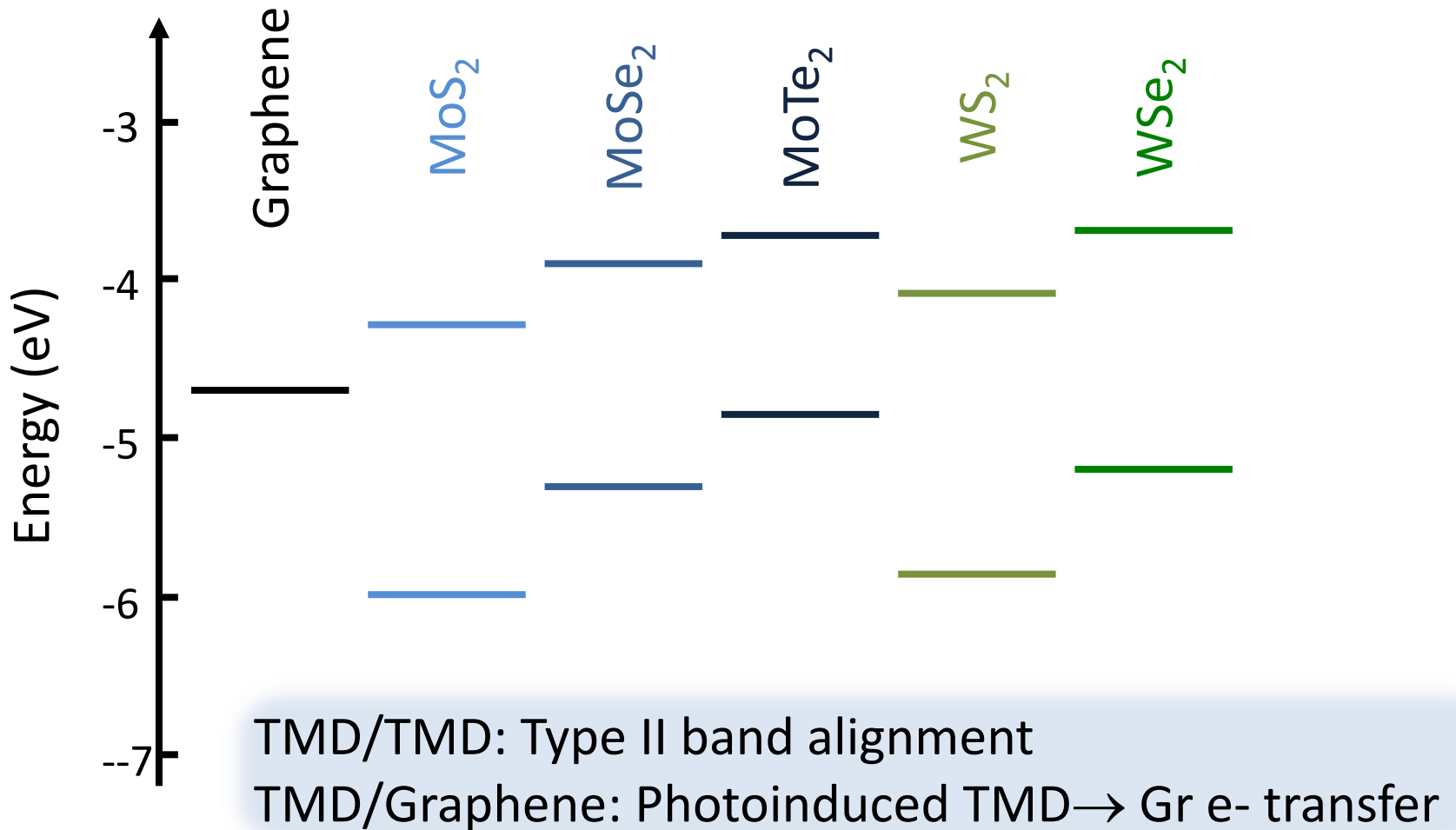
- *Near-field coupling in hybrid heterostructures*



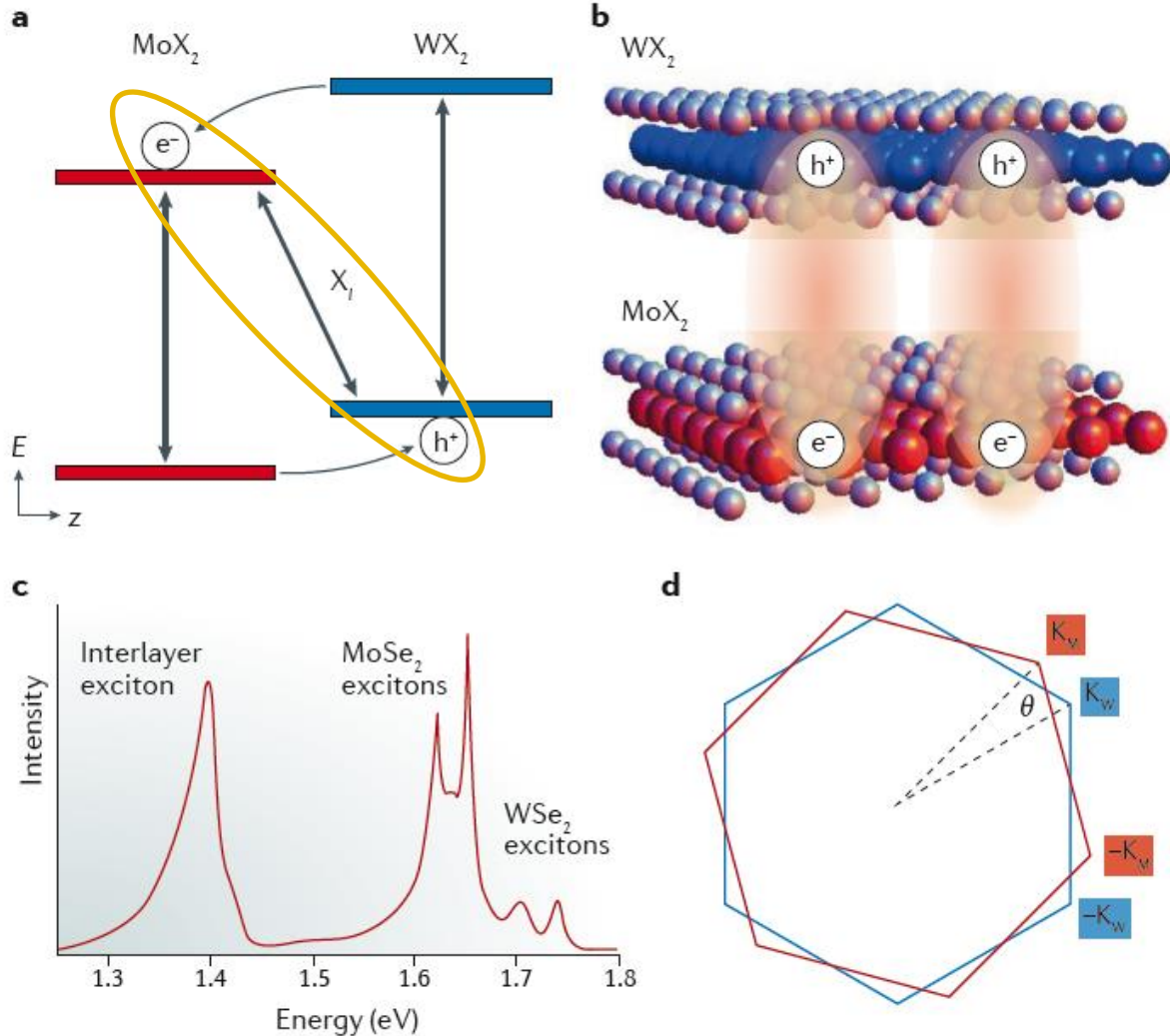
- *Charge and energy transfer in van der Waals heterostructures*



Band alignments



Interlayer excitons in TMD/TMD heterostructures

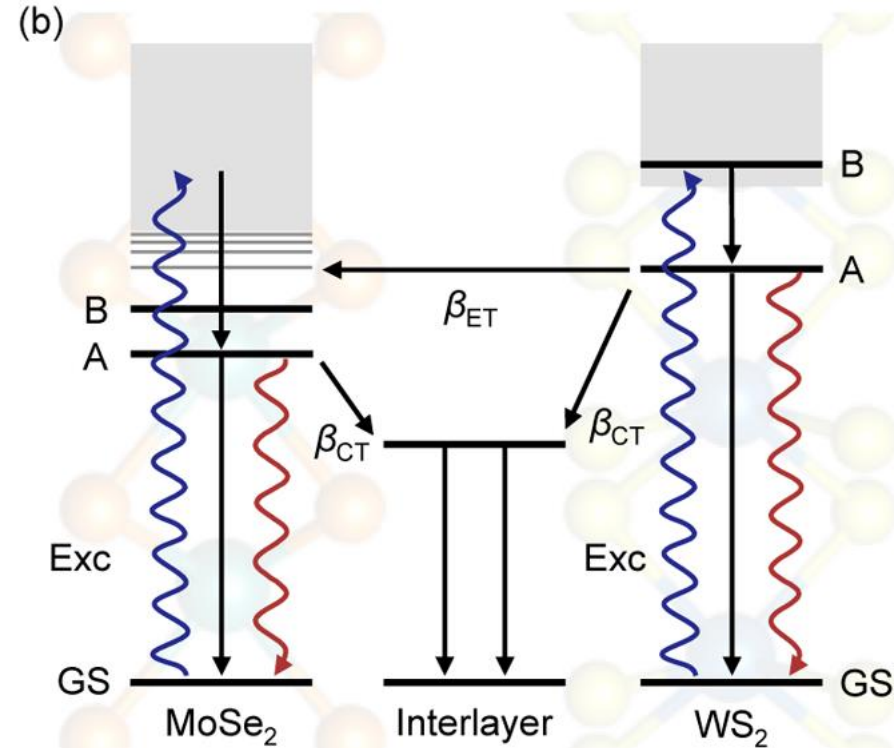
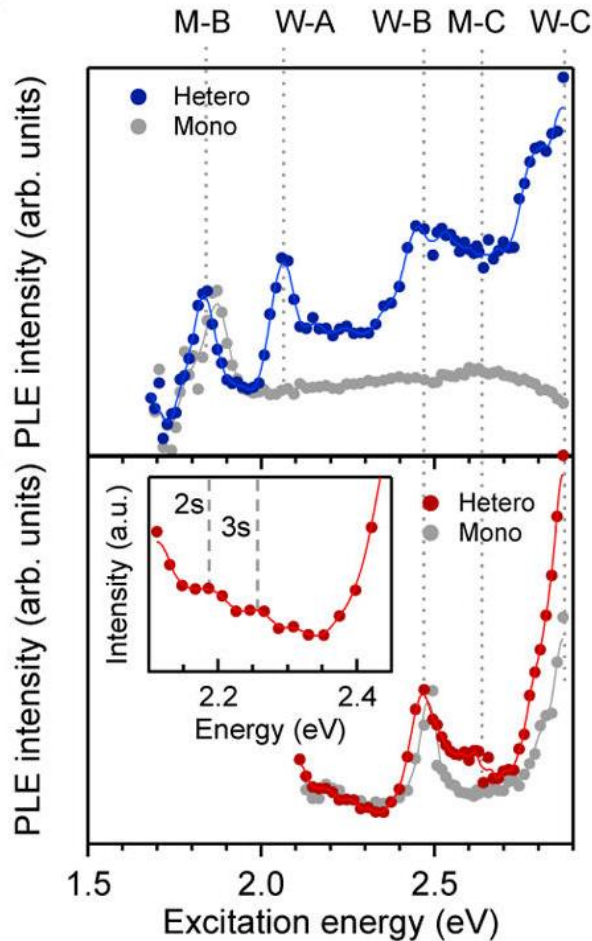
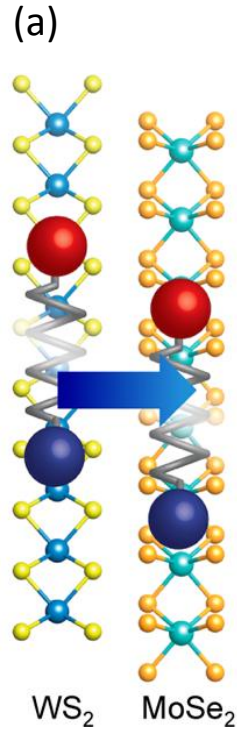


Ultrafast (<ps) formation
Long lived (>ns)
Valley polarized
Direct or indirect (θ)
PN Junctions

Fang *et al.*, PNAS 2014
Hong *et al.*, Nat Nano 2014
Lee *et al.*, Nat Nano 2014
Rivera *et al.*, Nat Comm 2015
Rivera *et al.*, Science 2016
Ceballos *et al.*, ACS Nano 2014
Ross *et al.*, Nano Lett 2017

...

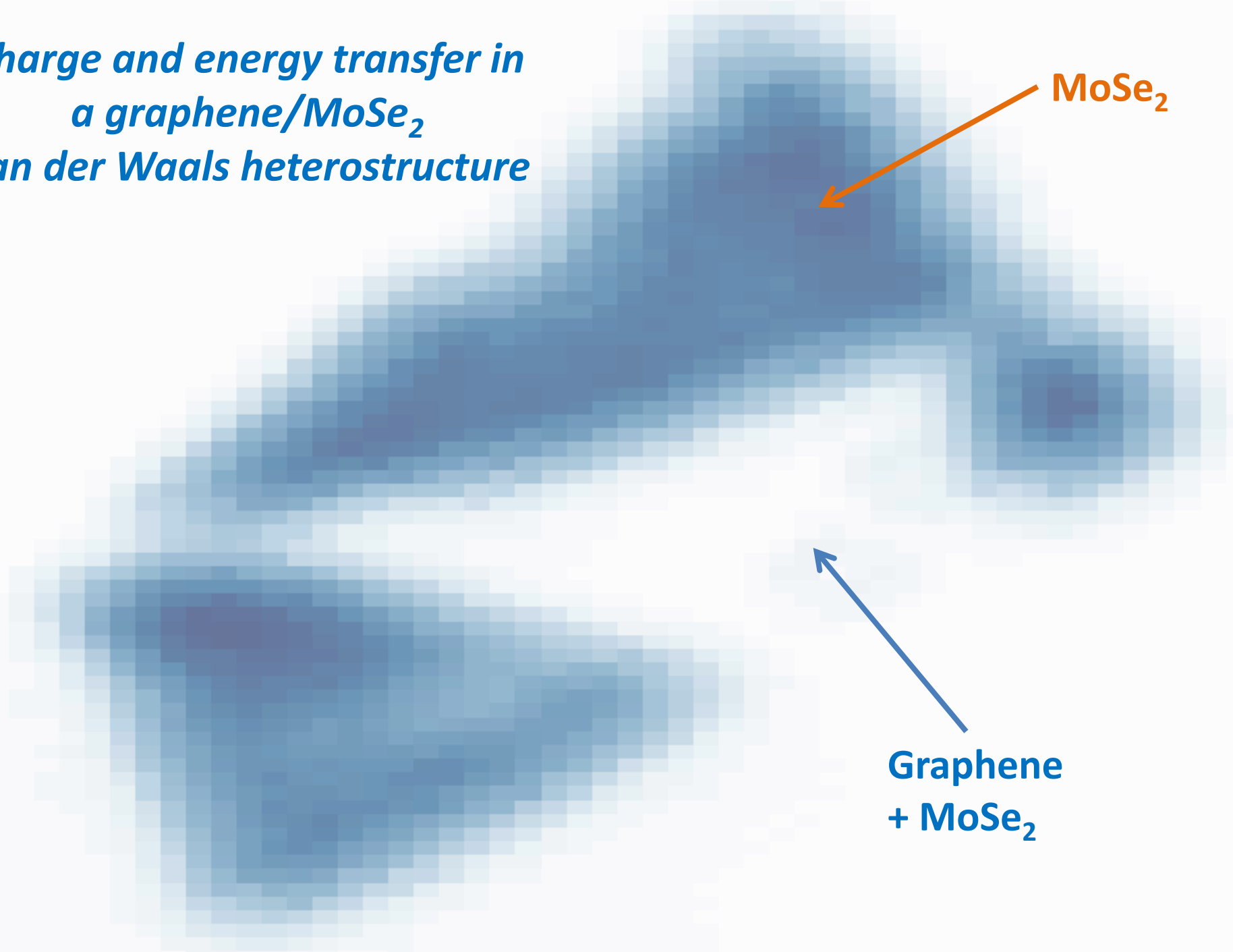
Energy Transfer in TMD/TMD heterostructures



D. Kozawa *et al.*, Nano Lett. 2016

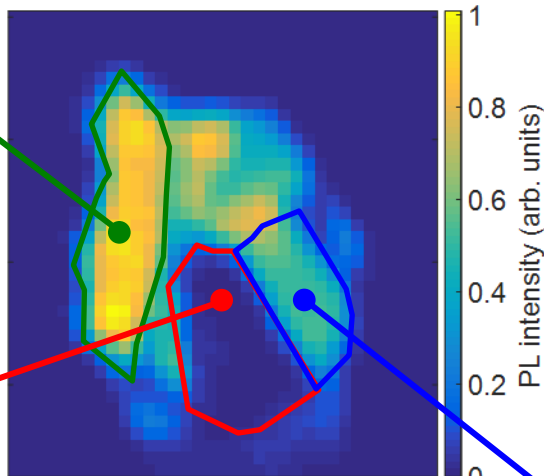
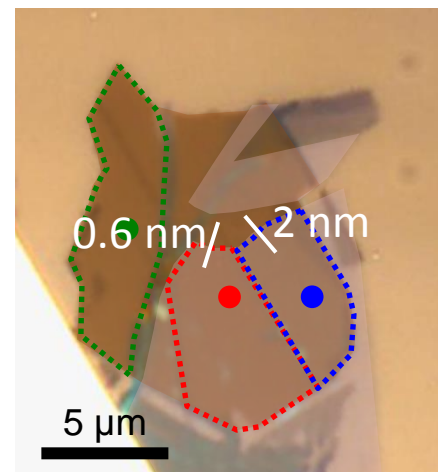
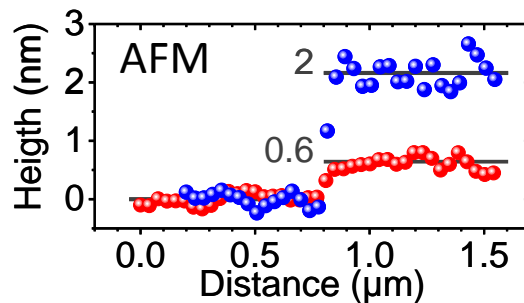
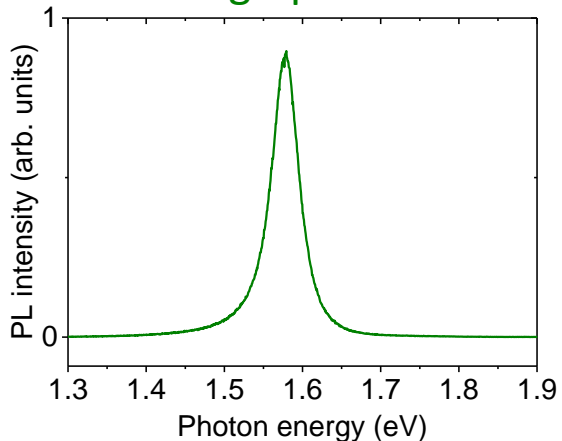
Open debate: competition between interlayer charge and energy transfer

*Charge and energy transfer in
a graphene/MoSe₂
van der Waals heterostructure*

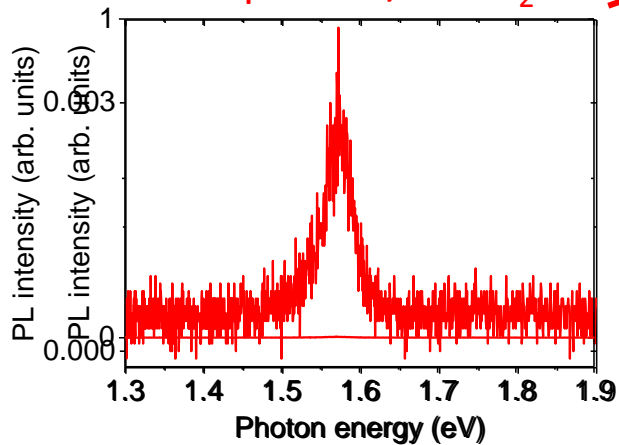


Photoluminescence mapping

No graphene

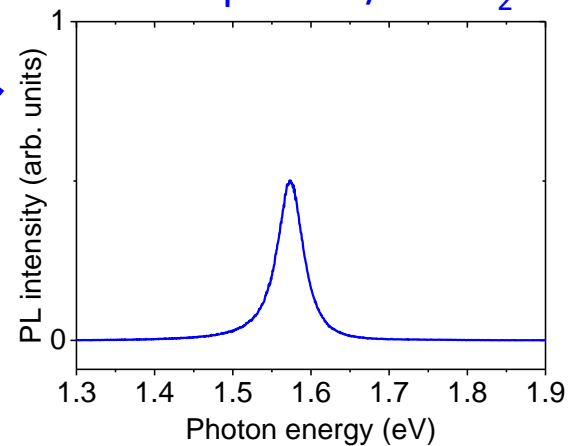


Coupled Gr/MoSe₂



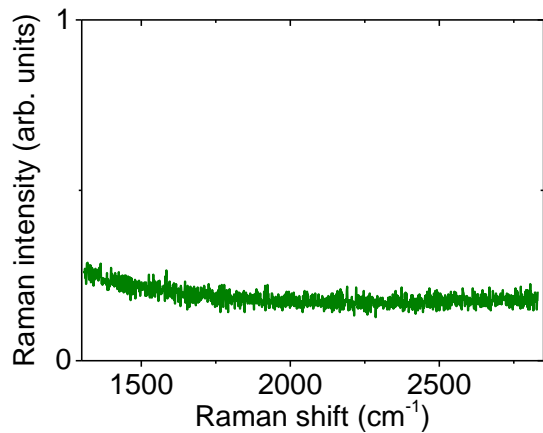
➔ Strong PL Quenching ~ 300

Decoupled Gr/MoSe₂

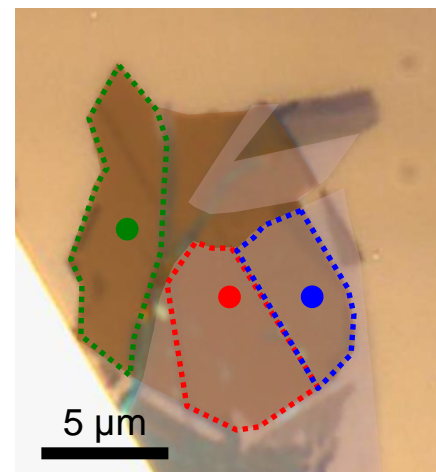
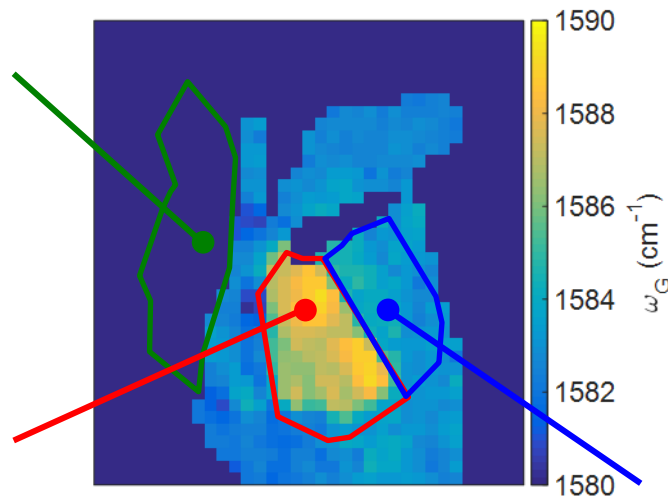


Raman mapping

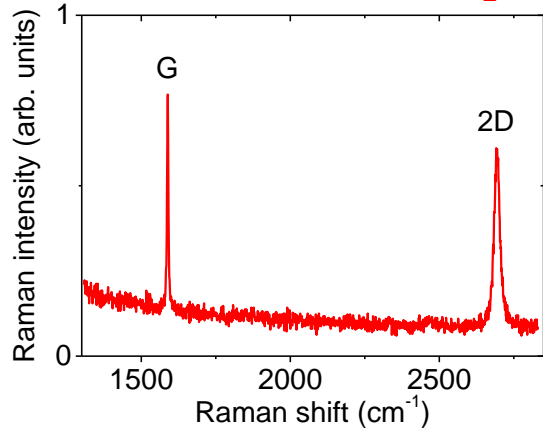
No graphene



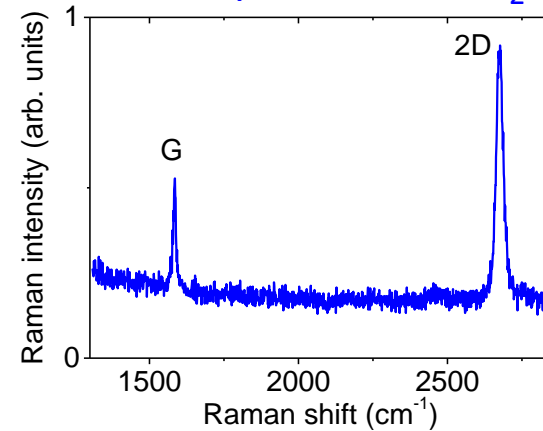
G-mode frequency



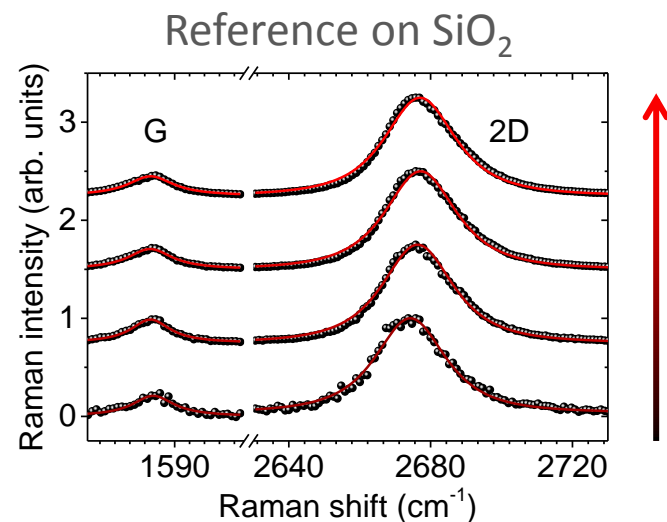
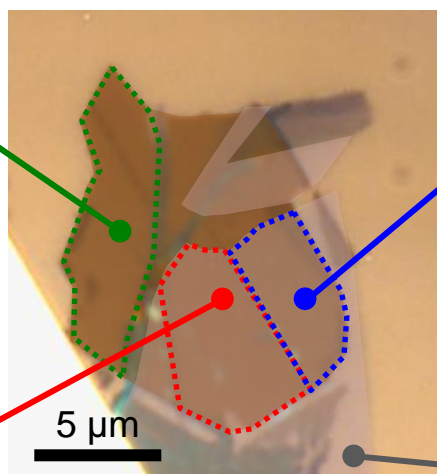
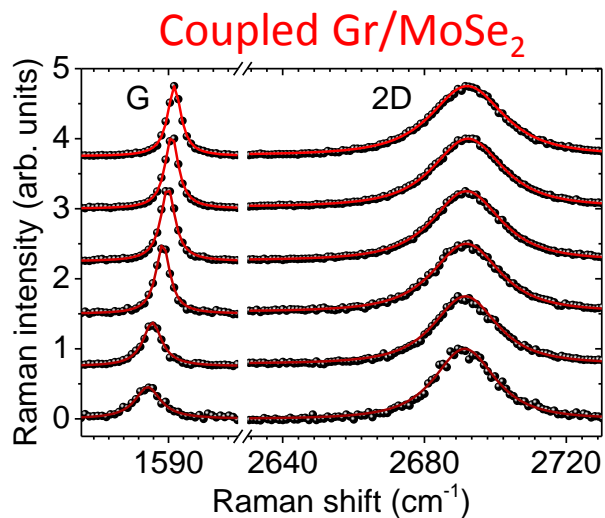
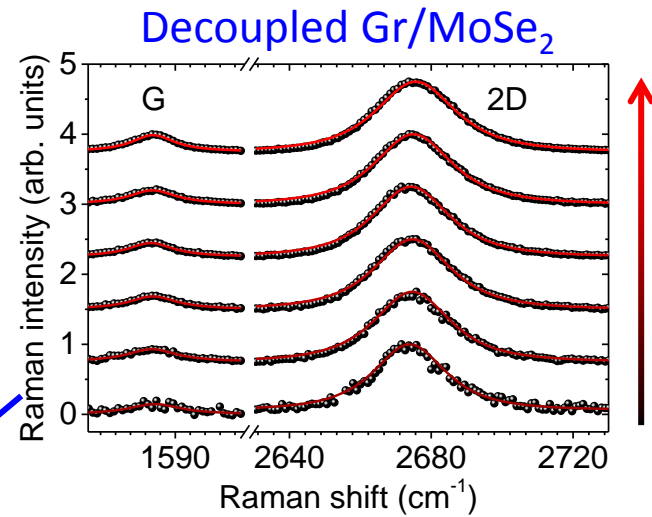
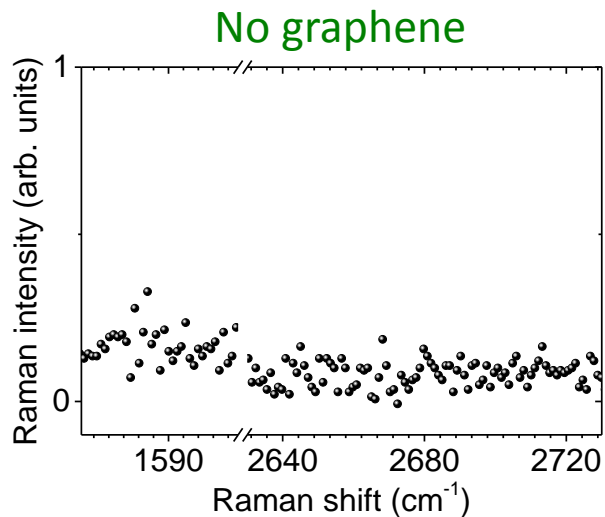
Coupled Gr/MoSe₂



Decoupled Gr/MoSe₂



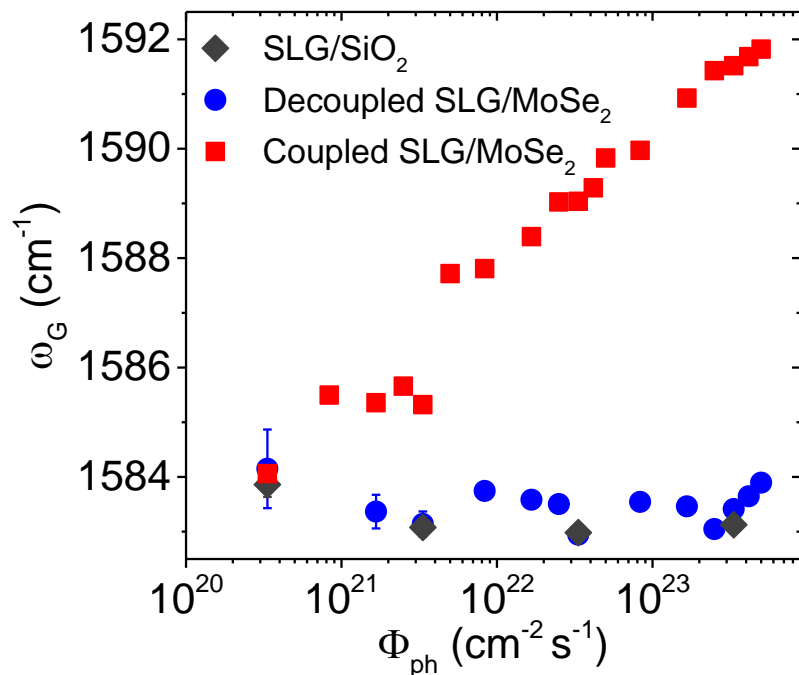
Raman response vs photon flux (2)



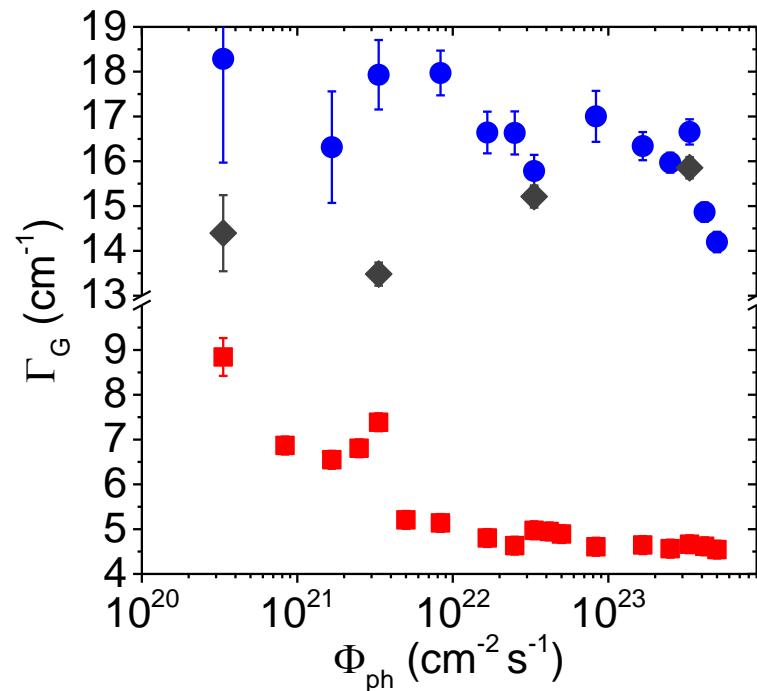
Φ_{ph} increases

Raman response vs photon flux (2)

G-mode frequency



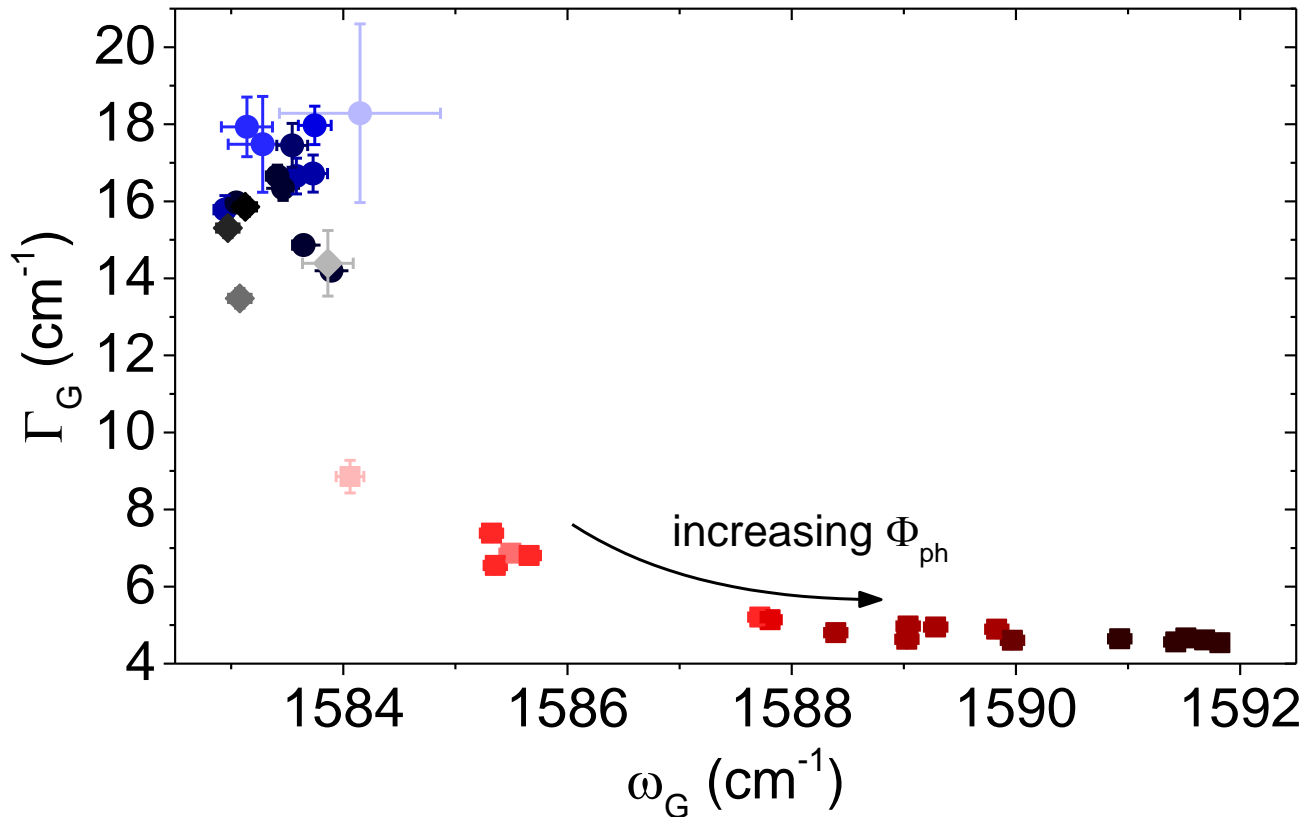
G-mode FWHM



➔ Clear signatures of photoinduced charge transfer

Raman response vs photon flux (2)

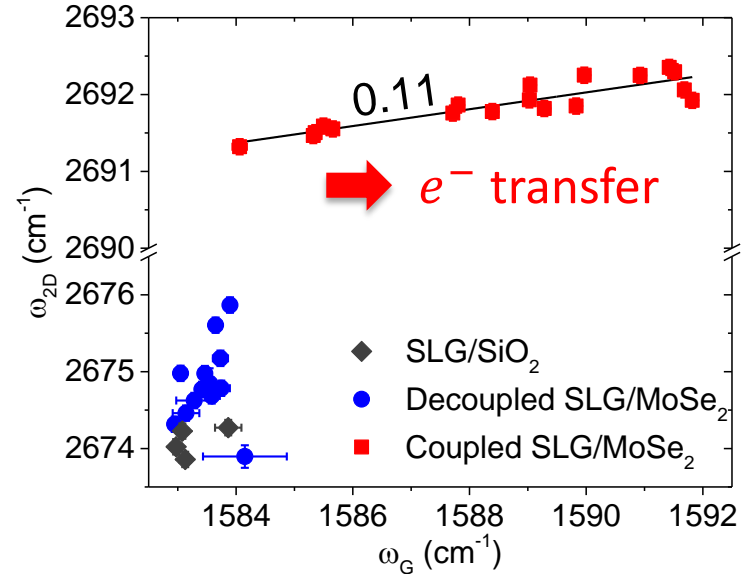
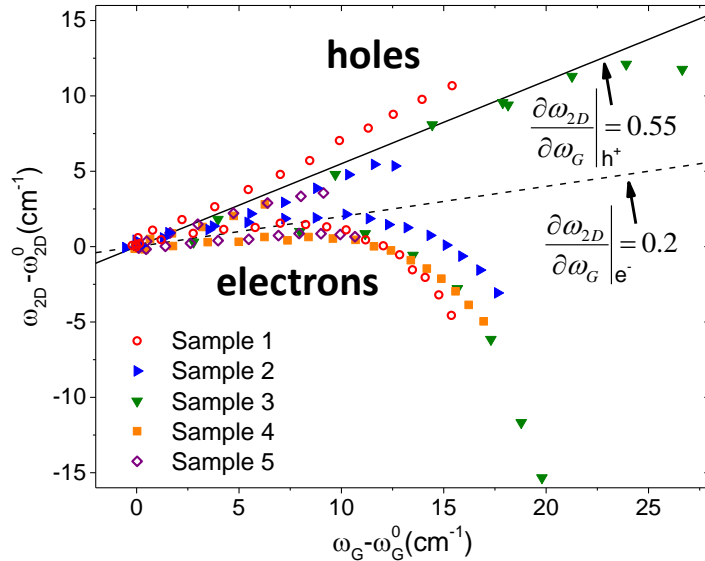
Width-Frequency Correlation



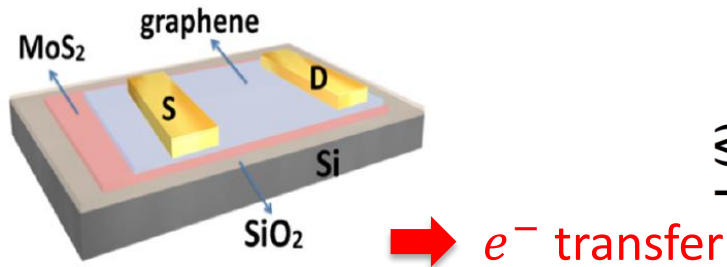
➡ Clear signatures of photoinduced charge transfer

Evidence for TMD → Gr electron transfer

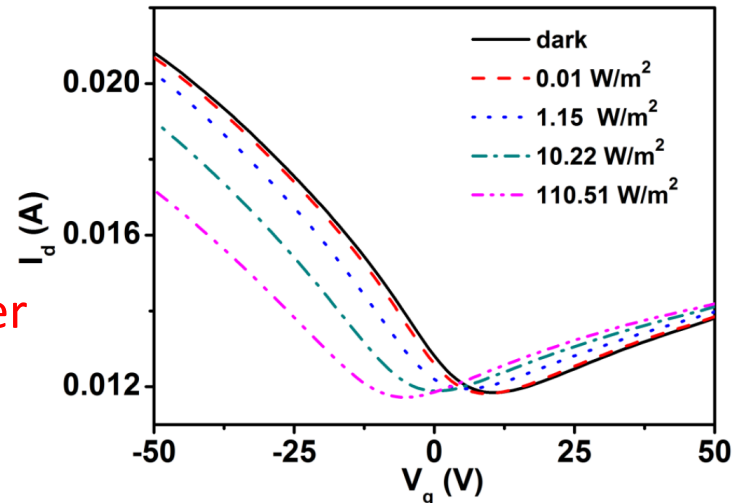
- 2D and G mode correlations: separation of strain and e^-/h^+ doping



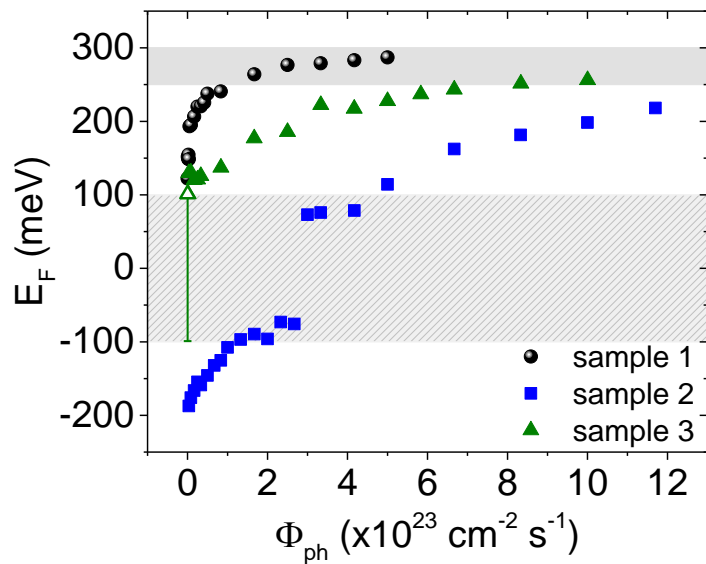
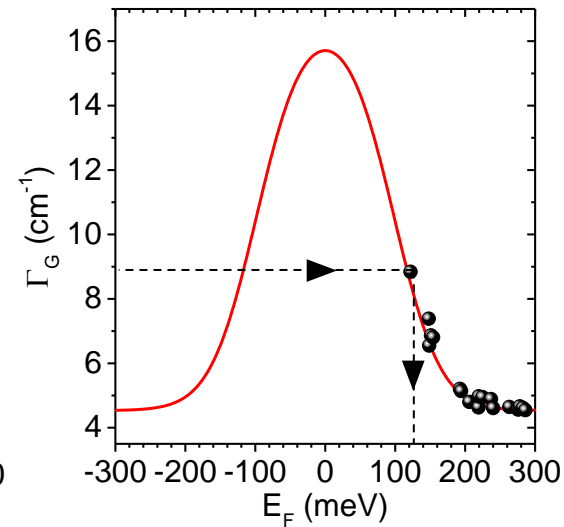
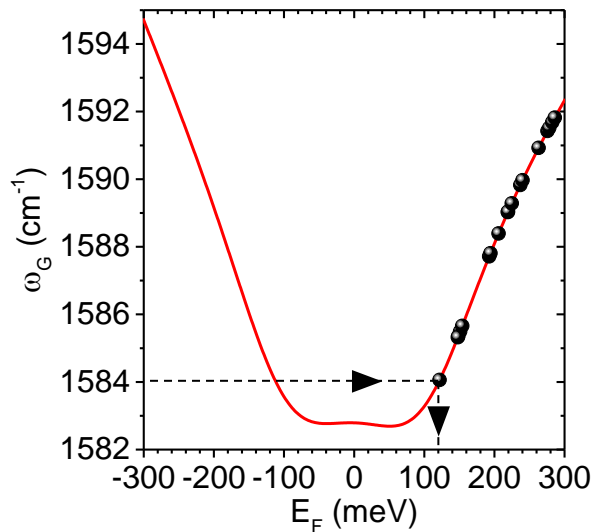
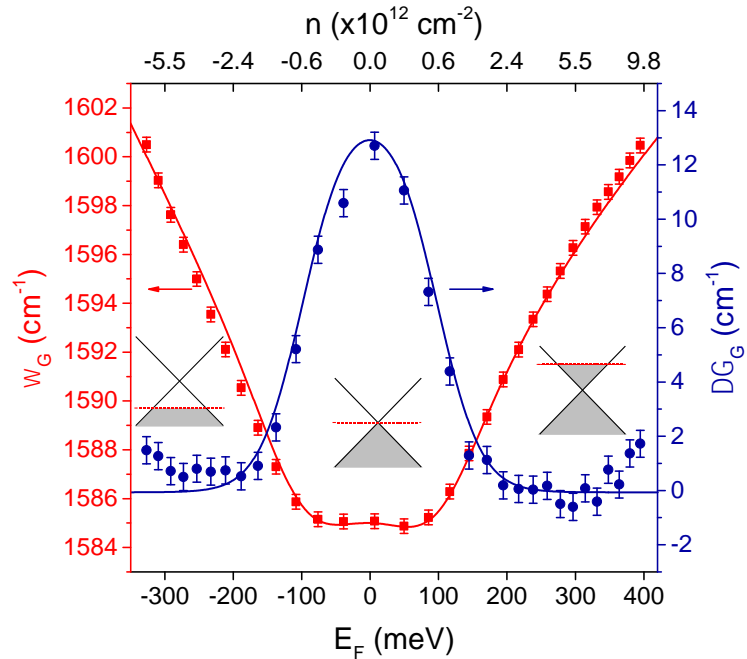
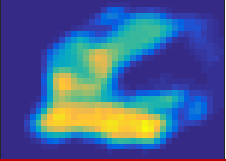
- Comparison with Gr/MoS₂



electrical measurements



Quantifying photoinduced doping

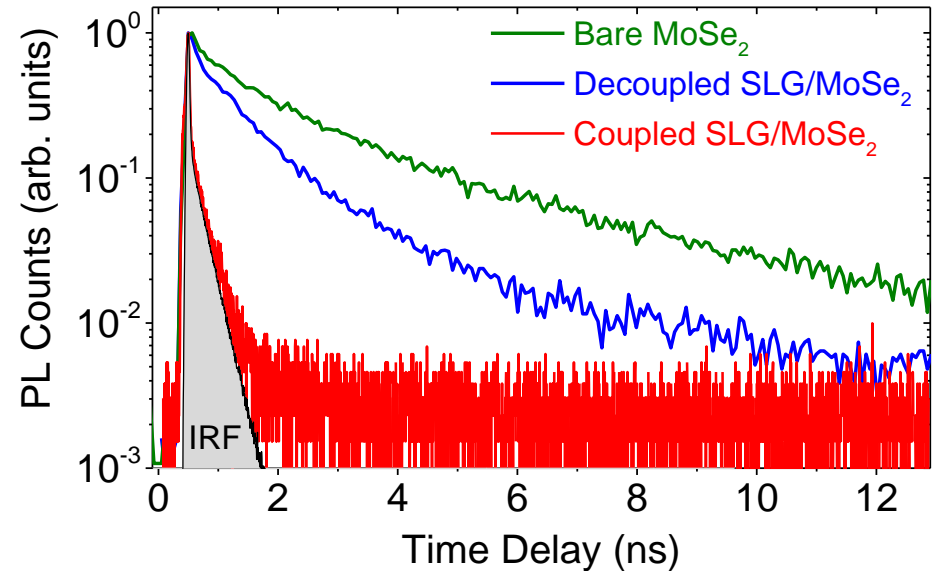
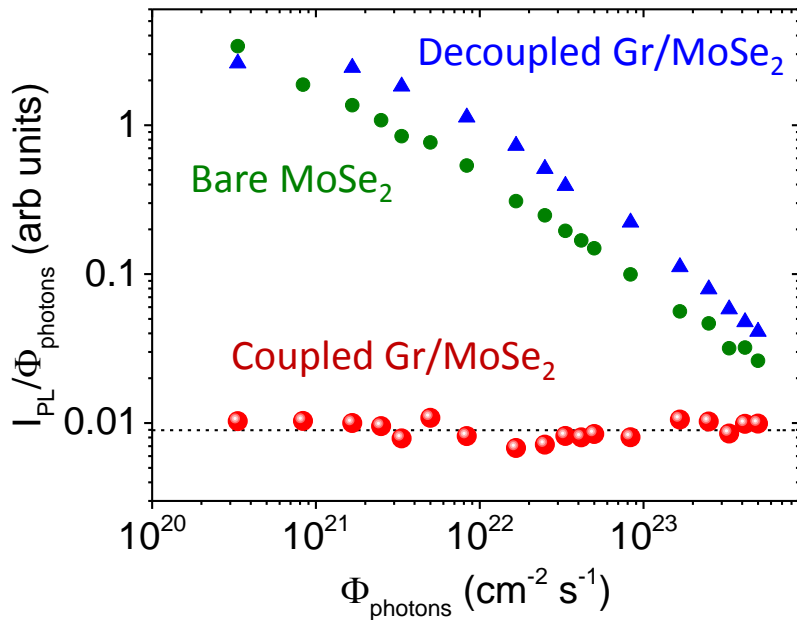


Saturation at $E_F \sim 250$ -300 meV
Does the ICT efficiency depend on E_F ?

G. Froehlicher and SB, PRB **91**, 205413 (2015)

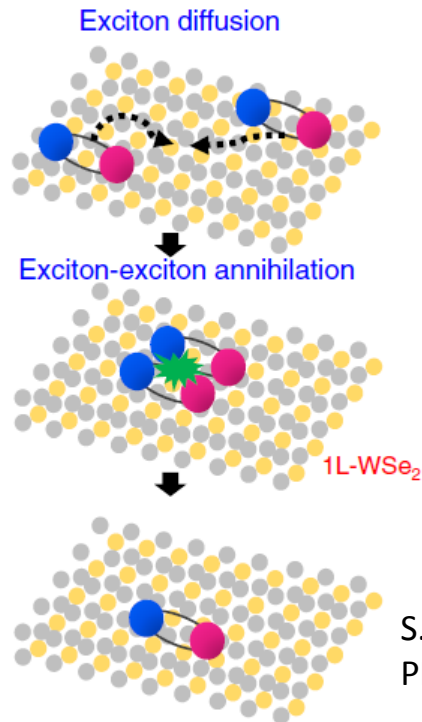
G. Froehlicher *et al.*, (in preparation, 2016)

PL vs Φ_{photons}

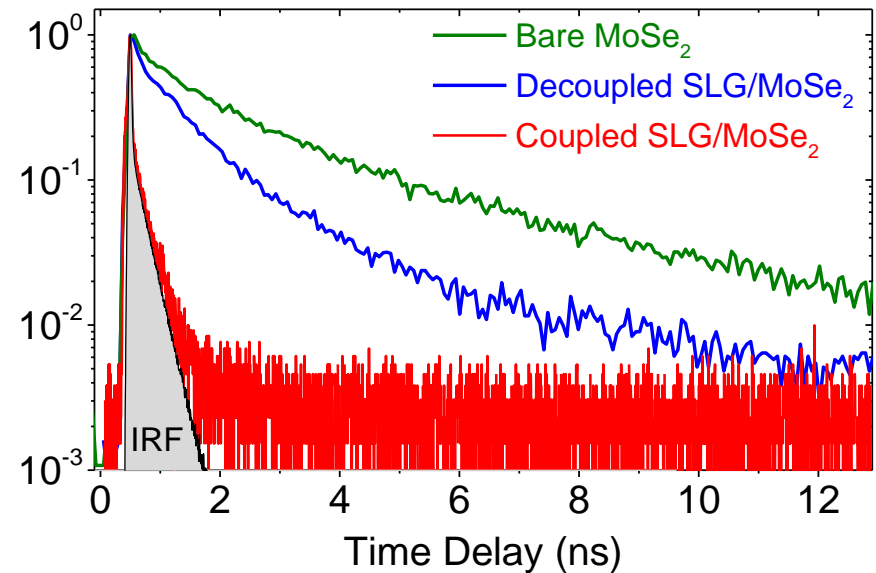


- **PL saturation on bare and decoupled MoSe₂:**
→ Exciton-Exciton Annihilation (EEA)
- **No PL saturation on Gr/MoSe₂**
→ Drastic reduction of the excitonic lifetime (~ 1 ps)
→ **Charge and Energy Transfer?**

PL vs Φ_{photons}



S. Mouri *et al.*,
PRB 2014

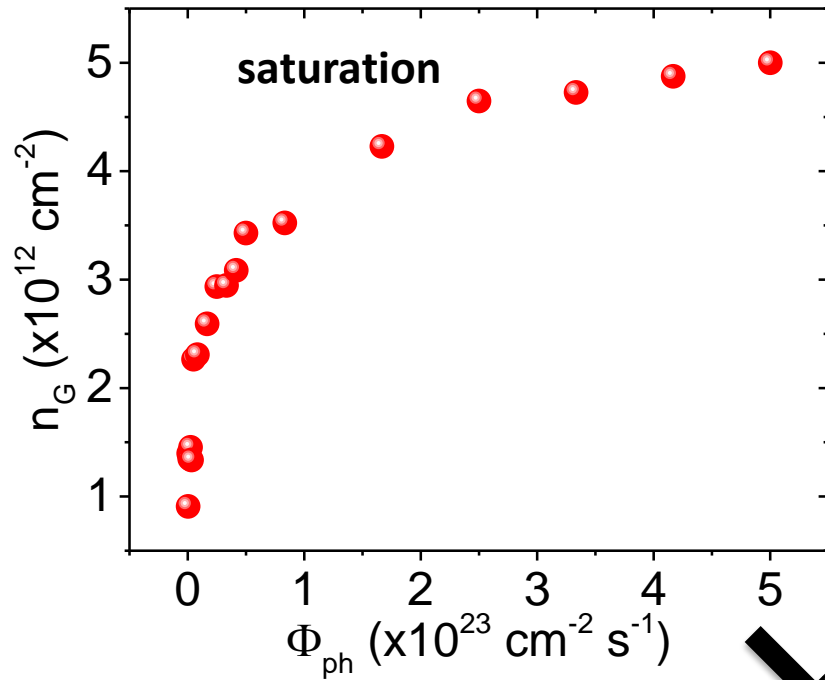


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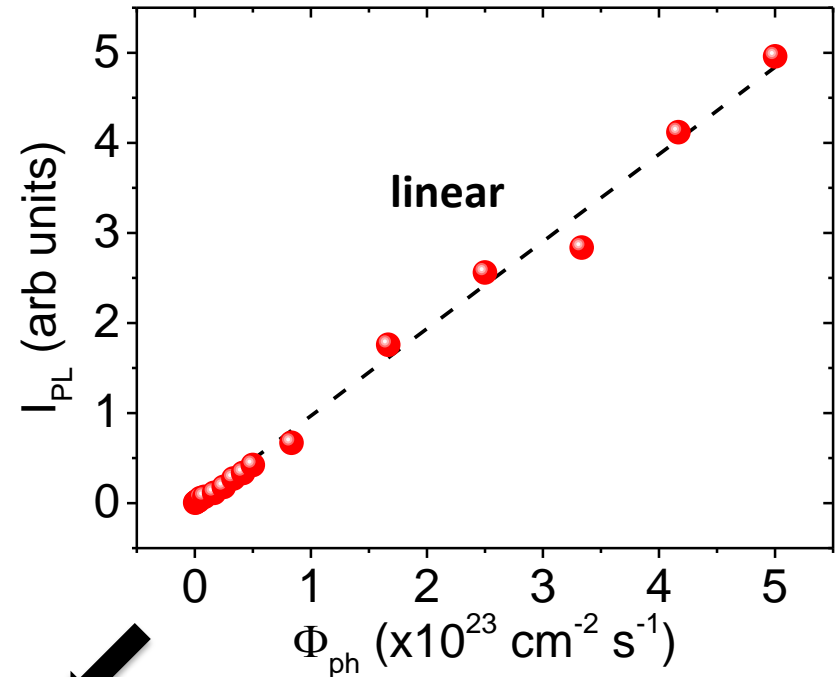
Photoluminescence vs Raman



Graphene's doping level

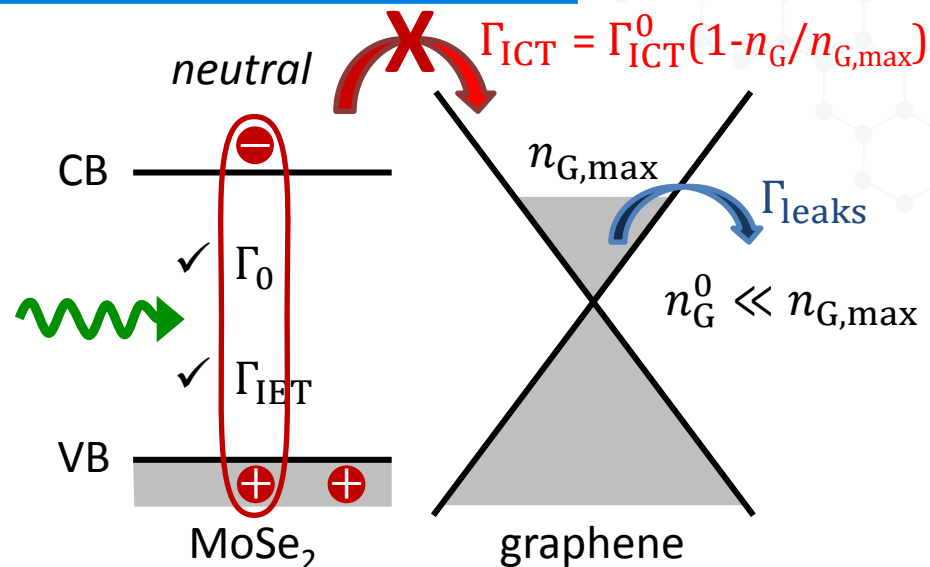
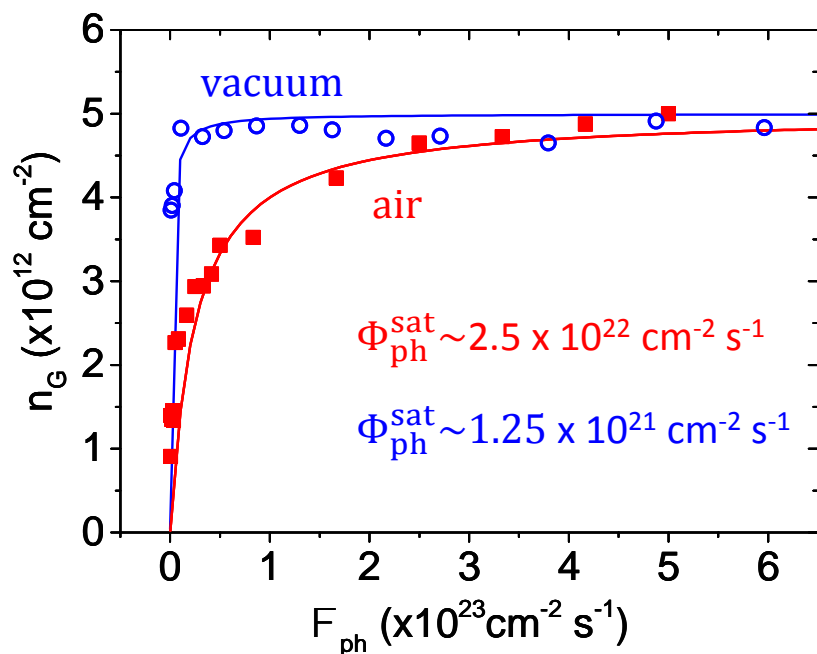


MoSe₂ PL

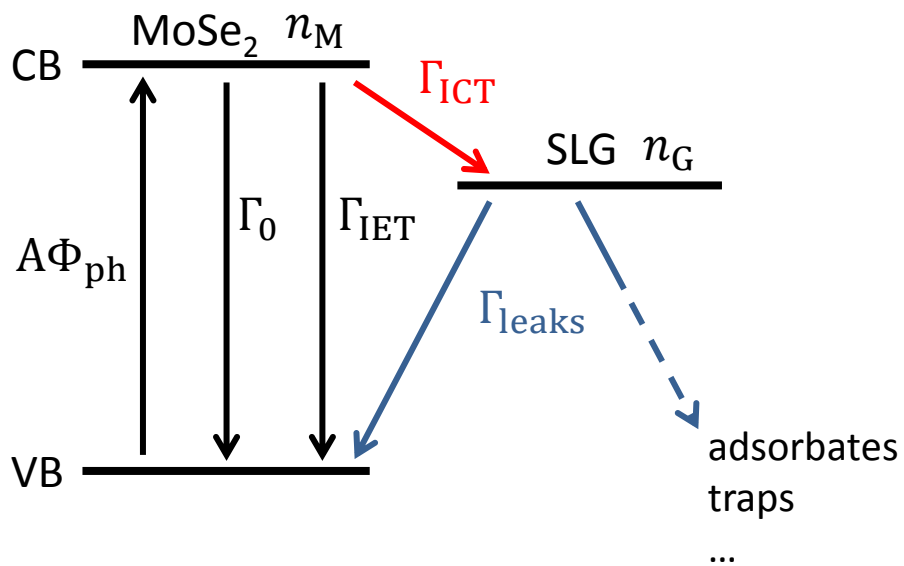


Cannot be explained
using ICT only

Toy model



- At $\Phi_{\text{ph}} = 0$, $n_M = 0$ and $n_G = 0$
- $\Gamma_{\text{IET}} \gg \Gamma_{\text{ICT}}, \Gamma_0$



$$\langle n_M \rangle \approx \frac{A\Phi_{\text{ph}}}{\Gamma_{\text{IET}}} \quad \checkmark$$

$$\langle n_G \rangle \approx \frac{n_{G,\text{max}}}{1 + \Phi_{\text{ph}}^{\text{sat}}/\Phi_{\text{ph}}} \quad \checkmark$$

$$\Phi_{\text{ph}}^{\text{sat}} = \frac{\Gamma_{\text{leaks}} \Gamma_{\text{IET}}}{\Gamma_{\text{ICT}}^0} \frac{n_{G,\text{max}}}{A} \quad \sim 10^{12} \text{ s}^{-1}$$

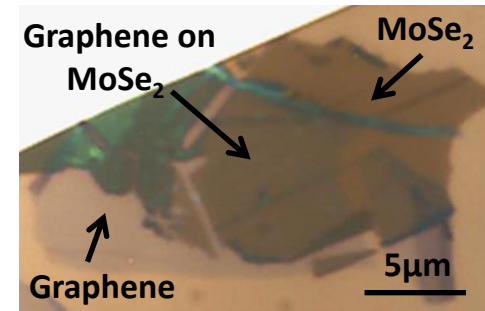
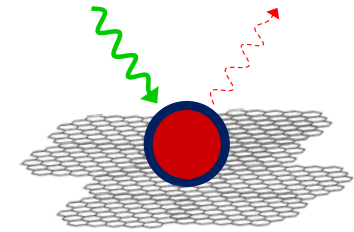
Conclusion

- ✓ **Efficient energy transfer from semiconductor nanostructures to 2D materials**
- ✓ Molecular rulers
- ✓ FRET as a probe of exciton dimensionality
- ✓ FRET engineering

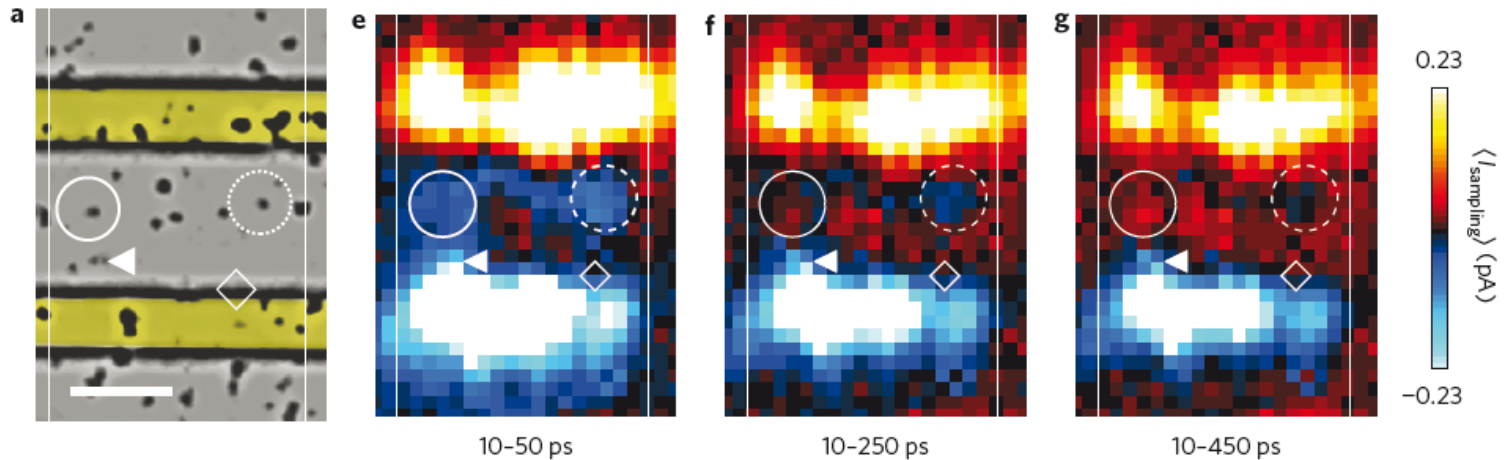
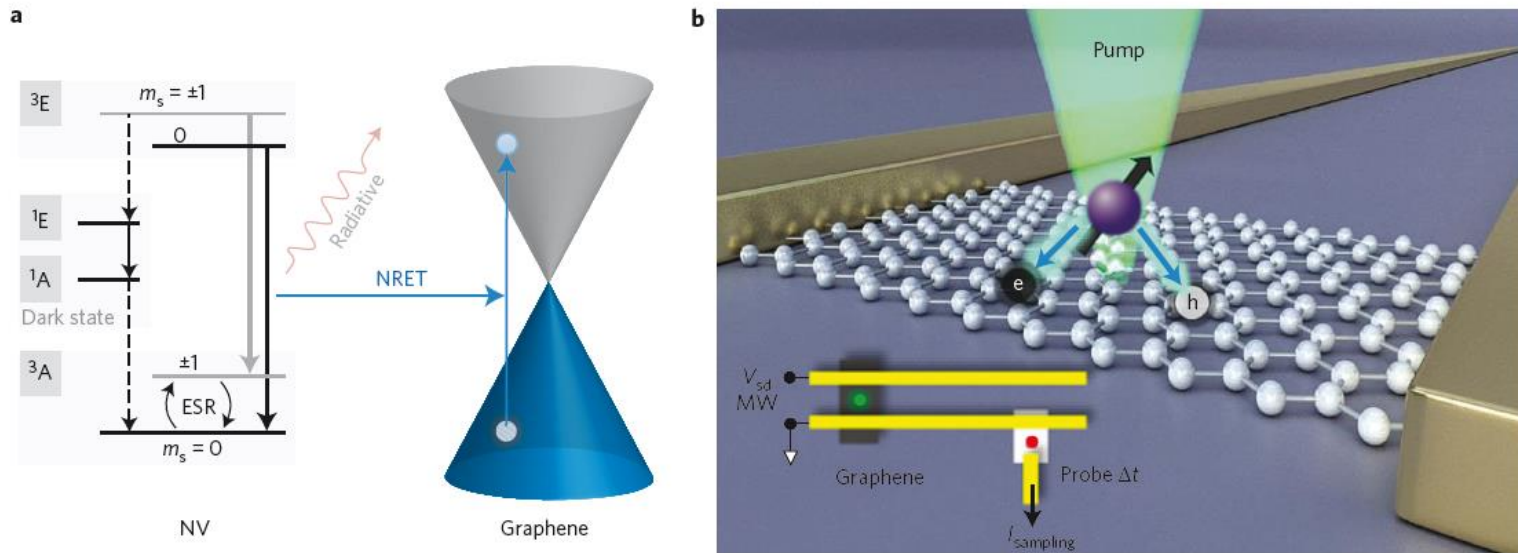
- ✓ **Photoinduced e^- transfer from TMD to graphene**
→ Towards local photogating of graphene
- ✓ **Fast IET is responsible for PL quenching**
- ✓ **IET is more efficient than ICT**

- **Open questions**

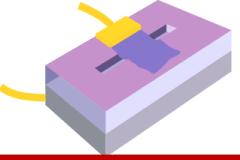
- ✓ Energy transfer mechanism in Gr-TMD? In TMD-TMD?
- ✓ Band alignment and excitonic effects?
- ✓ ...



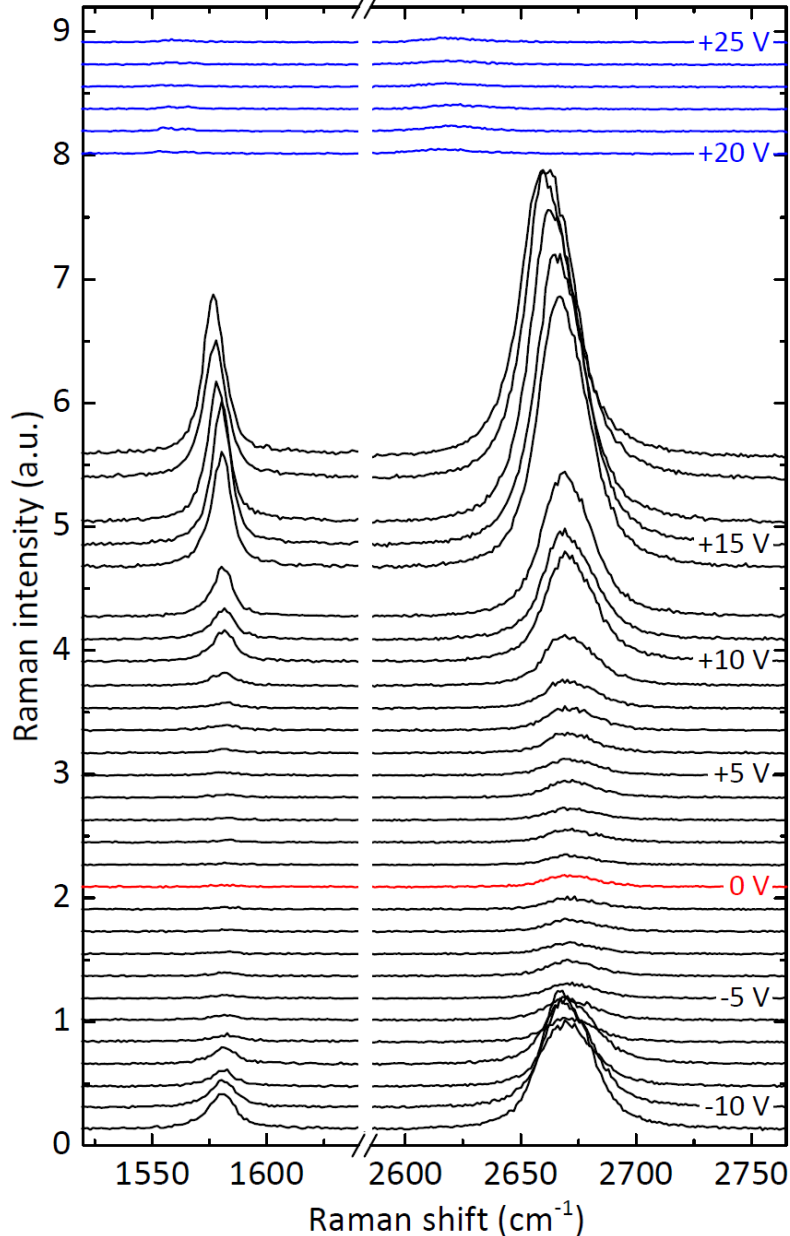
Outlook 1: FRET-induced electrical currents



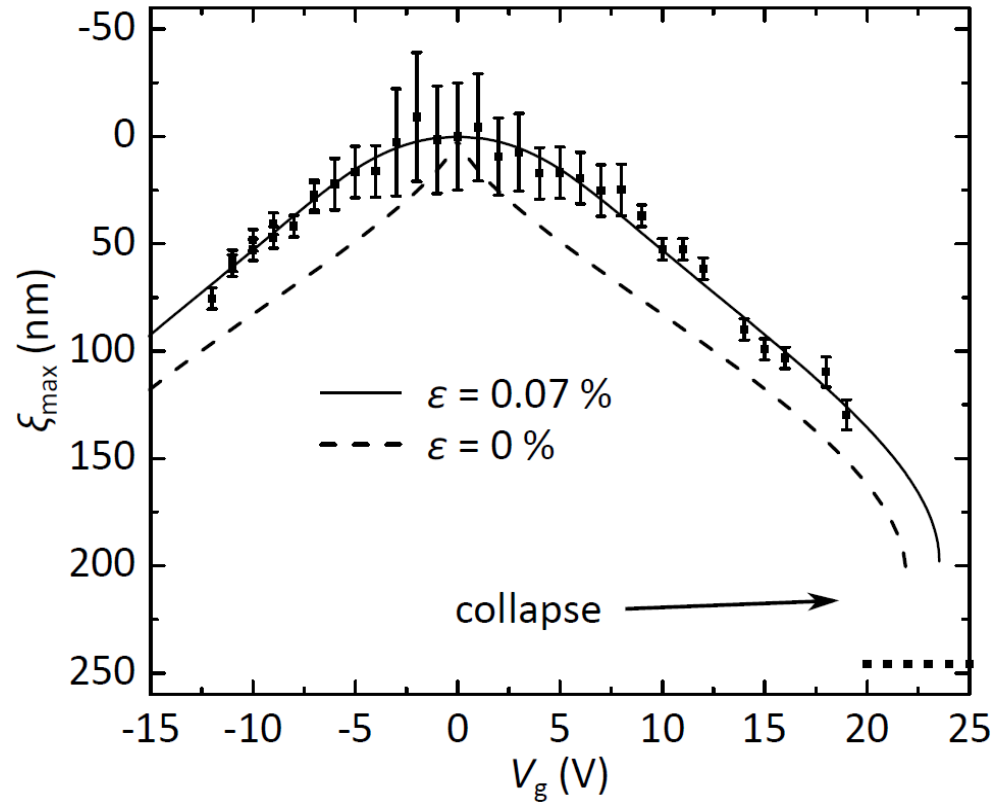
A. Brenneis *et al.* Nat. Nano 2015. (Holleitner group with Koppens group)



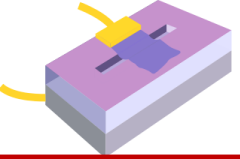
Outlook2: opto-electromechanics in 2DM



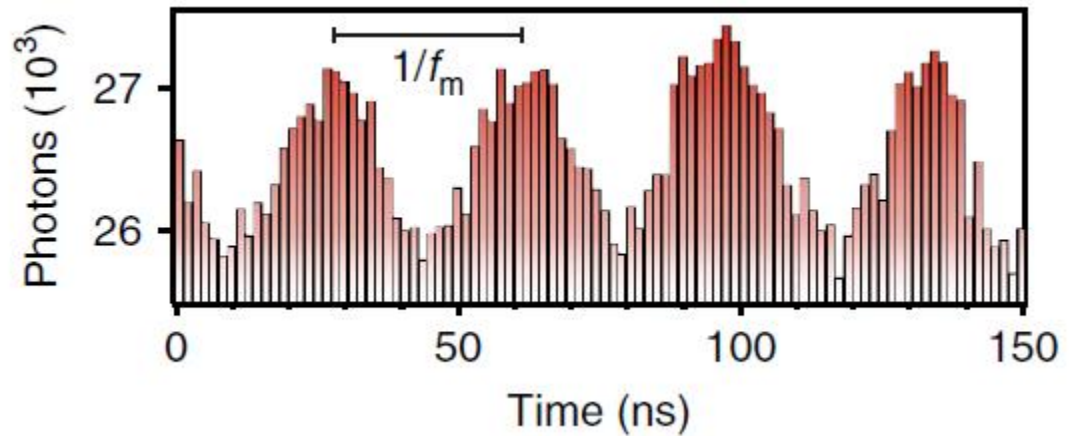
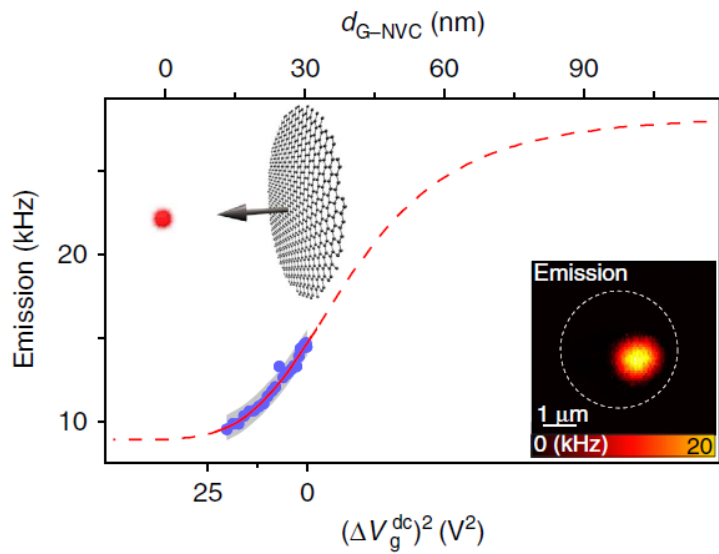
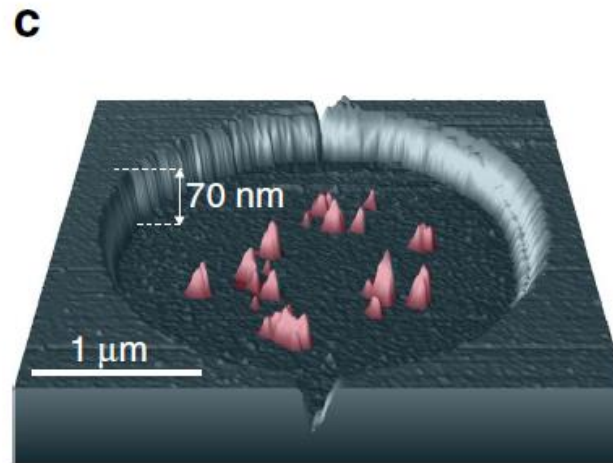
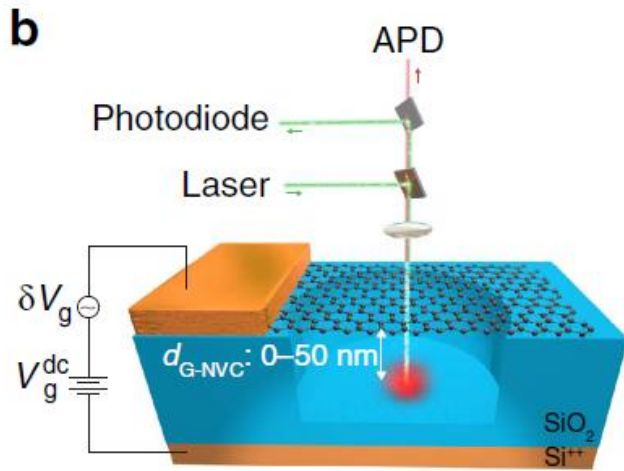
*Deflection, strain, doping
Transport? Optomechanics?*



D. Metten, G. Froehlicher and SB, 2D Materials 4 014004 (2017)



Optoelectromechanical control of FRET



Acknowledgements



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